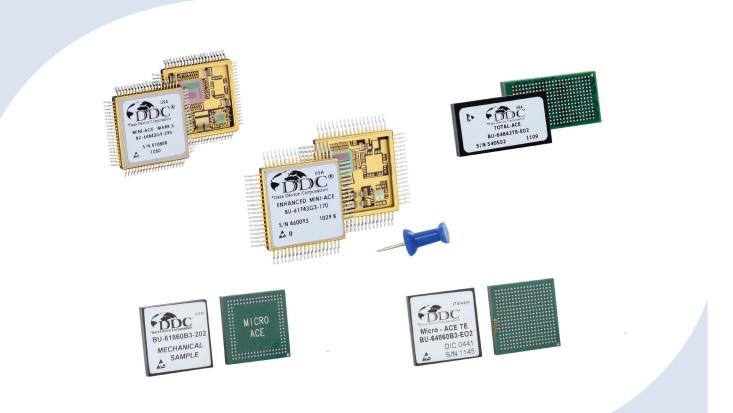
Enhanced Miniature Advanced Communications Engine User's Guide



Model: BU-6186X



Volume 2 - Hardware Reference

DDC's Enhanced Mini-ACE family of MIL-STD-1553 terminals provide complete interfaces between a host processor and 1553 bus. These terminals integrate a dual transceiver, protocol logic, and 4K or 64K words of RAM.

Enhanced Mini-ACE Family:

- Enhanced Mini-ACE^{\tiny (B)}
- Micro-ACE[®]
- Mini-ACE[®] Mark3
- Micro-ACE[®]-TE
- Total-ACE®



For more information: www.ddc-web.com/EMA

DDC's Data Networking Solutions

MIL-STD-1553 | ARINC 429 | Fibre Channel

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_ MIL-STD-1553 _

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_ ARINC 429

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ENHANCED MINIATURE ADVANCED COMMUNICATIONS ENGINE (ENHANCED MINI-ACE[®] SERIES) USER'S GUIDE VOLUME 2 – HARDWARE REFERENCE

MN-6186X-002

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В	8/2004	All	Major Revision, See MarCom for Markup
A	8/2005	All	Major Revision, Volume 2 now a stand alone Manual returning to an A revision.
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E	2/2008	156 – 182	Removed outline drawings, pinouts, and ordering information, as these details are maintained in the datasheet.
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1 PREFACE

This manual uses typographical conventions to assist the reader in understanding the content. This section will define the text formatting used in the rest of the manual

1.1 Text Usage

- **BOLD**–indicates important information and table, figure, and chapter references.
- **BOLD ITALIC**-designates DDC Part Numbers.
- Courier New-indicates code examples.
- <...> indicates user-entered text or commands.

1.2 Special Handling and Cautions

The *Enhanced Mini-ACE Series* uses state-of-the-art components, and proper care should be used to ensure that the device will not be damaged by Electrical Static Discharge (ESD), physical shock, or improper power surges and that precautions are taken to avoid electrocution.



Warnings: Turn off power to the computer hardware and unplug from wall.

NEVER insert or remove card with power turned on.

Ensure that standard ESD precautions are followed. As a minimum, one hand should be grounded to the power supply in order to equalize the static potential.

Do not store disks in environments exposed to excessive heat, magnetic fields or radiation.

1.3 Trademarks

All trademarks are the property of their respective owners.

1.4 What is included in this manual?

This manual contains a complete description of hardware installation and use.

1.5 Technical Support

In the event that problems arise beyond the scope of this manual, you can contact DDC by the following:

US Toll Free Technical Support: 1-800-DDC-5757, ext. 7771

Outside of the US Technical Support: 1-631-567-5600, ext. 7771

Fax: 1-631-567-5758 to the attention of DATA BUS Applications

DDC Website: www.ddc-web.com/ContactUs/TechSupport.aspx

Please note that the latest revisions of Software and Documentation are available for download at DDC's Web Site, <u>www.ddc-web.com</u>.

2 OVERVIEW

All references throughout this document to the "Enhanced Mini-ACE" shall be interpreted to include Enhanced Mini-ACE, Micro-ACE, Mini-ACE Mark3, Micro-ACE TE, and Total-ACE products. Any specific references to a unique series of components (i.e. Micro-ACE only) will utilize the component part number (i.e. BU-61740B, BU-61840B/61860B etc.).

The Enhanced Mini-ACE family (Enhanced Mini-ACE, Micro-ACE, Mini-ACE Mark 3, Micro-ACE TE, Total-ACE) of MIL-STD-1553 terminals provides complete interfaces between a host processor and a 1553 bus. All these terminals integrate dual transceiver, protocol logic, and 4K words or 64K words of RAM. Additionally, the Total-ACE integrates the isolation transformer(s) as well. The BC/RT/MT versions with 64K words of RAM include built-in RAM parity checking.

The Enhanced Mini-ACE is packaged in a choice of a 1.0-inch square Flat Pack or Gull Wing package, or a 0.815-inch square BGA package (Micro-ACE). The Mini-ACE Mark 3 is packaged in a choice of a 0.890-inch Flat Pack or Gull Wing package, or a 0.815-inch square BGA package (Micro-ACE-TE). The Total-ACE is packaged in a 1.100-inch x 0.600-inch rectangular, plastic BGA.

The Flat Pack or Gull Wing packaged Enhanced Mini-ACE provides footprint compatibility with the previous generation Mini-ACE (Plus) terminal.

All members of the Enhanced Mini-ACE series (Enhanced Mini-ACE, Micro-ACE, Mini-ACE Mark3, Micro-ACE-TE, and Total-ACE) provide software compatibility with the previous generation Mini-ACE (Plus) terminals, and the older ACE series.

The Enhanced Mini-ACE and Micro-ACE are powered by a choice 5V, or 5V/3.3V (3.3V logic). Multiprotocol support of MIL-STD-1553A/B and STANAG 3838, including versions incorporating McAir compatible transmitters, is provided. There is a choice of 10, 12, 16, or 20 MHz clocks.

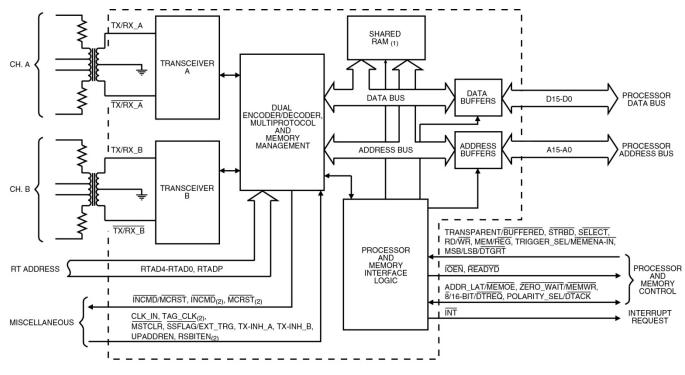
The Mini-ACE Mark3 and Micro-ACE-TE are powered by a choice of 3.3V/5V (logic), and 3.3V/5V (transceivers). (Certain combination restrictions apply. See datasheet for full ordering information). Multiprotocol support of MIL-STD-1553A/B and STANAG 3838, including versions incorporating McAir compatible transmitters, is provided. There is a choice of 10, 12, 16, or 20 MHz clocks.

The Total-ACE is an all 3.3V device (logic & transceivers) with integrated isolation transformers. (Certain combination restrictions apply. See datasheet for full ordering information). Multiprotocol support of MIL-STD-1553A/B and STANAG 3838, is provided. There is a choice of 10, 12, 16, or 20 MHz clocks.

BC features include a built-in engine, with a set of 20 instructions. This provides an autonomous means of implementing multi-frame message scheduling, message retry schemes, data double buffering, asynchronous message insertion, and reporting to the host CPU. The Enhanced Mini-ACE incorporates a fully autonomous built-in selftest, which provides comprehensive testing of the internal protocol logic and/or RAM.

The Enhanced Mini-ACE RT offers the same choices of subaddress buffering as ACE and Mini-ACE (Plus), along with a global circular buffering option, 50% rollover interrupt for circular buffers, an interrupt status queue, and an "Auto-boot" option to support MIL-STD-1760.

The Enhanced Mini-ACE terminals provide the same flexibility in host interface configurations as the Mini-ACE (Plus) terminals, and the older ACE series along with a reduction in the host processor's worst-case holdoff time.



NOTE 1: See Ordering Information for Available Memory Options. NOTE 2: Indicates signals brought out only on µ-ACE (BGA package) version.

Figure 1. Enhanced Mini-ACE/Micro-ACE Series Block Diagram

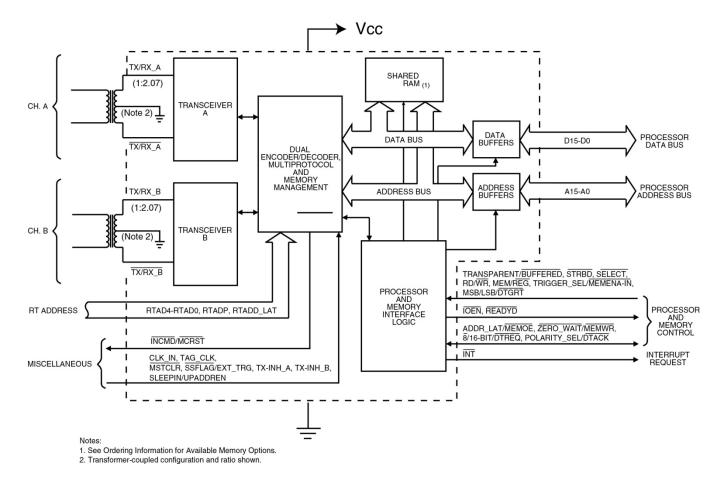


Figure 2. Mini-ACE Mark3 and Micro-ACE-TE Block Diagram (shown with X8/9 Transceiver Option)

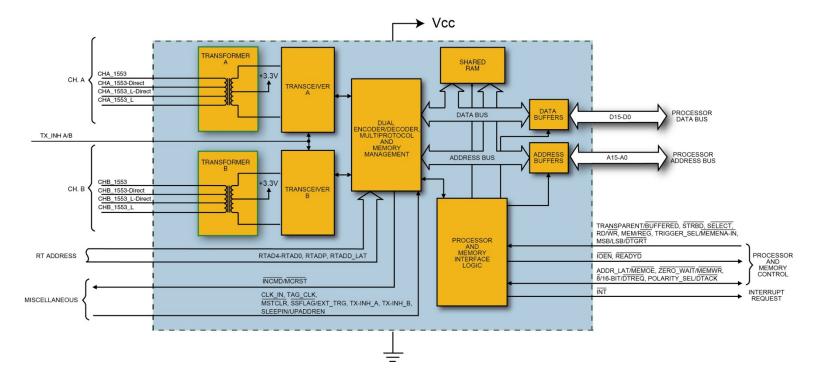


Figure 3. Total-ACE Block Diagram

3 DEVICE SPECIFICATIONS

The Latest Device Specifications for the Enhanced Mini-Ace/Micro-Ace and Mini-ACE Mark3/Micro-ACE TE, and Total-ACE are available at http://www.ddc-web.com:

For the latest Enhanced Mini-ACE/Micro-ACE information see BU-6174X/6184X/6186X Data Sheet

For the latest Mini-ACE Mark3/Micro-ACE-TE information see BU-6474X/6484X/6486X Data Sheet

For the latest Total-ACE information see BU-64843T Data Sheet

4 FUNCTIONAL OVERVIEW

The BU-61743/61745 RT, and BU-61843/61845/61864/61865 BC/RT/MT Enhanced Mini-ACE (BU-61740B RT, and BU-61840B/61860B BC/RT/MT Micro-ACE), BU-64743/64745 RT, and BU-64843/64845/64863 BC/RT/MT Mini-ACE Mark3 (BU-64840B/64843B/64860B/64863B BC/RT/MT Micro-ACE-TE) family of MIL-STD-1553 terminals comprise a complete integrated interface between a host processor and a MIL-STD-1553 bus.

The BU-61743/61745 RT, and BU-61843/61845/61864/61865 BC/RT/MT Enhanced Mini-ACE are packaged in a 1.0 inch square ceramic flat-pack package providing footprint (with four pin differences) compatibility with previous generation Mini-ACE terminals. The BU-64743/64745 RT, and BU-64843/64845/64863 BC/RT/MT Mini-ACE Mark3 are packaged in a 0.890 inch square ceramic flat-pack package.

The BU-61740B RT, and BU-61840B/61860B BC/RT/MT Micro-ACE and BU-64840B/64843B/64860B/64863B BC/RT/MT Micro-ACE-TE are packaged in a 0.815 inch square BGA package.

The Enhanced Mini-ACE series of hybrids provides software compatibility with the previous generation Mini-ACE terminals, as well as software compatibility with the older ACE series.

The Enhanced Mini-ACE RT provides complete multi-protocol support of MIL-STD-1553A/B/McAir and STANAG 3838. All versions integrate dual transceiver; along with protocol, host interface, memory management logic; and a minimum of 4K words of RAM. In addition, the BU-61864/61865/61860B/64863/64860B/64863B BC/RT/MT terminals include 64K words of internal RAM, with built-in parity checking.

The Enhanced Mini-ACE series includes 5V or 3.3V, voltage source transceivers for improved line driving capability, with options for MIL-STD-1760 and McAir compatibility. As a means of reducing power consumption, there are versions for which the logic is powered by 3.3V, rather than 5V. To provide further flexibility, the Enhanced Mini-ACE may operate with a choice of 10, 12, 16, or 20 MHz clock inputs.

One of the salient new features of the Enhanced Mini-ACE is its enhanced bus controller architecture. The Enhanced BC's highly autonomous message sequence control engine provides a means for offloading the host processor for implementing minor and major frame timing control; asynchronous message insertion; data block double buffering; bulk data transfers; and retry and bus switching strategy. For the purpose of performing messaging to the host processor, the Enhanced BC mode includes a General Purpose Queue, along with user-defined interrupts.

The Enhanced Mini-ACE is the latest device group in the ACE family. The term "enhanced" has also been used in earlier versions of the family to describe new features introduced at each stage. For backward compatibility reasons, the same terms and options have been maintained in the Enhanced Mini-ACE. The user will be aware of Enhanced Mode, set by bit 15 of Configuration Register (CR) # 3 along with the following optional features from earlier families:

Enhanced RT Memory Management	CR#2 Bit #1
Enhanced RT Interrupt Handling	CR#2 Bit #15
Enhanced Mode Code Handling	CR#3 Bit #0
Enhanced Mode Enable	CR#3 Bit #15
Expanded BC Control Word Enable	CR#4 Bit #12
Plus for the latest devices:	
Enhanced BC	CR#6 Bit #15
Enhanced Time Tag Synchronization	CR#7 Bit #2
Enhanced BC Watchdog Timer Enable	CR#7 Bit #1

In many cases, the user may wish to enable most of these bits at initialization to have all available features active

A second major new feature of the Enhanced Mini-ACE is the incorporation of a fully autonomous built-in self-test. This test provides comprehensive testing of the internal protocol logic. A separate test verifies the operation of the internal RAM. Since the self-tests are fully autonomous, they eliminate the need for the host to write and read stimulus and response vectors.

The Enhanced Mini-ACE RT offers the same choices of single, double, and circular buffering for individual subaddresses as the ACE and Mini-ACE (Plus). New enhancements to the RT architecture include a global circular buffering option for multiple (or all) receive subaddresses, a 50% rollover interrupt for circular buffers, an interrupt status queue for logging up to 32 interrupt events, and an option to automatically initialize to RT mode with the busy bit set. The interrupt status queue and 50% rollover interrupt features are also included as improvements to the Enhanced Mini-ACE's monitor architecture.

To minimize board space and "glue" logic, the Enhanced Mini-ACE terminals provide the same wide choice of host interface configurations as the ACE and Mini-ACE (Plus). This includes support of shared RAM interfaces to 16-bit or 8-bit processors, memory or port type interfaces, and multiplexed or non-multiplexed address/data buses; plus a DMA interface configuration.

Hermetic, ceramic packaged, Enhanced Mini-ACE series terminals are available in versions operating over the full military temperature range of -55 to +125°C. Available screened to MIL-PRF-38534C, these terminals are ideal for military and industrial processor-to-1553 applications.

4.1 Transceivers

The transceivers in the Enhanced Mini-ACE series of terminals are fully monolithic, requiring only a +5 or +3.3 volt power input. The transmitters are voltage sources, which provide improved line driving capability over current sources. This serves to improve performance on long buses with many taps. The transmitters also offer an option that satisfies the MIL-STD-1760 requirement for a minimum of 20 volts peak-to-peak, transformer coupled output.

Besides eliminating the demand for an additional power supply, the use of a +5V or +3.3V-only transceivers requires the use of a step-up, rather than a step-down, isolation transformer. This provides the advantage of higher terminal input impedance than is possible for a 15 volt or 12 volt transmitter. As a result, there is a greater margin for the input impedance test, mandated for the 1553 validation test. This characteristic allows for longer cable lengths between a system connector and the isolation transformers of an embedded 1553 terminal.

To provide compatibility to McAir specs, the Enhanced Mini-ACE is available with an option for transmitters with increased rise and fall times.

The receiver sections of the Enhanced Mini-ACE are fully compliant with MIL-STD-1553B Notice 2 in terms of front end over voltage protection, threshold, common mode rejection, and word error rate.

5 SIGNAL DESCRIPTIONS BY FUNCTIONAL GROUPS

For the latest Enhanced Mini-ACE/Micro-ACE information see BU-6174X/6184X/6186X Data Sheet

For the latest Mini-ACE Mark3/Micro-ACE-TE information see BU-6474X/6484X/6486X Data Sheet

For the latest Total-ACE information see BU-64843T Data Sheet

6 +5.0V TRANSCEIVER INTERFACE TO A MIL-STD-1553 BUS

Figure 4 illustrates the interface between the various +5.0V transceiver versions of the Enhanced Mini-ACE series and a MIL-STD-1553 bus. Connections for both direct (short stub) and transformer (long stub) coupling, as well as the peak-to-peak "Nominal" voltage levels that appear at various points (when transmitting), are as indicated in the figure.

Please see for +5.0V isolation transformer limitations and recommendations.

In accordance with MIL-STD-1553B, the turns ratio of the coupling transformer is required to be 1.0 to 1.4. For both coupling configurations, isolation resistors are required to be in series with each leg connecting to the 1553 bus. In the case of direct coupling, the value of the coupling resister is 55 ohms. For direct coupling, the isolation resistors are located within the 1553 BC, RT, or Monitor terminal. In the case of transformer coupled, the resistors are 0.75 Z_0 in value and are located in the bus coupler, rather than the BC, RT, or Monitor terminal. The isolation resistors protect the bus against short circuit conditions in the transformers, stubs, or terminal components.

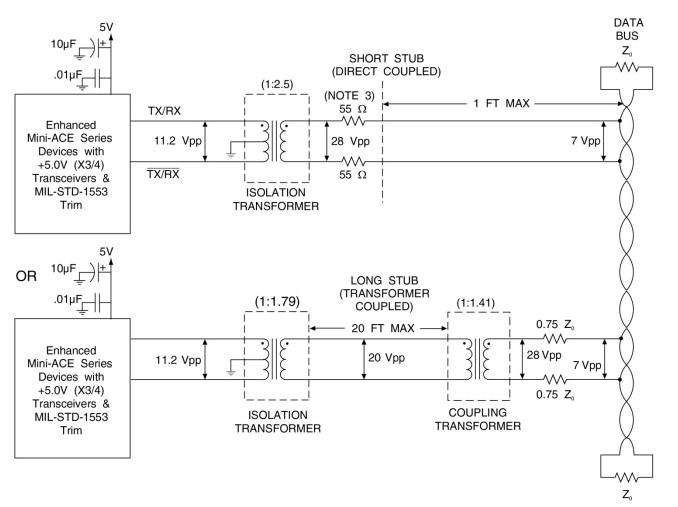
For most system applications, transformer (stub) coupling is preferred over direct coupling. Some of the advantages of transformer coupling are:

(1) Looking from the 1553 bus towards the stub, the effect of the 1.4 to 1.0 stepdown of the coupling transformer will be to **double** the impedance of the stub/terminal combination, as seen by the bus. Since the stub impedance decreases as a function of stub length due to distributed cable capacitance, this doubling effect serves to reduce the amount of impedance loading on the bus by individual terminals. For this reason, stub coupled terminals may be located up to 20 feet from the bus; the distance for direct coupled terminals is limited to 12 inches.

(2) Looking from the isolation transformer down the stub (towards the bus), the impedance seen is Z_0 . Therefore, the characteristic impedance of the stub cabling (78 ohms nominal) matches the stub's load impedance, minimizing reflections back toward the transmitter.

(3) In a direct-coupled terminal, the main bus is not protected against a short circuit in the stub cabling. For the transformer coupled case, the bus is protected against such a fault.

(4) A transformer coupled terminal provides improved DC and common mode isolation over a direct-coupled terminal.



NOTE: $Z_0 = 70$ TO 85 OHMS



Figure 4 Notes:

- 1. Shown for one or two redundant buses that interface to the Enhanced Mini-ACE.
- 2. Transmitted voltage level on 1553 bus is 6 Vp-p min, 7 Vp-p nominal, 9 Vp-p max.
- 3. Required tolerance on isolation resistors is 2%. Instantaneous power dissipation (when transmitted) is approximately 0.5W (typ), 0.8W (max).

6.1 +5.0 Volt Isolation Transformers

Please see MN-6186X-003 Appendix A for +5.0V isolation transformer limitations and recommendations.

7 +3.3V TRANSCEIVER INTERFACE TO A MIL-STD-1553 BUS

Figure 5 and Figure 6 illustrate the interface between the various +3.3V transceiver versions of the Enhanced Mini-ACE series and a MIL-STD-1553 bus. Connections for both direct (short stub) and transformer (long stub) coupling, as well as the peak-to-peak "Nominal" voltage levels that appear at various points (when transmitting), are as indicated in the Figures.

Figure 7 illustrates the interface between the Total-ACE (with integrated isolation transformers) and a MIL-STD-1553 bus. Connections for transformer (long stub) coupling, as well as the peak-to-peak "Nominal" voltage levels that appear at various points (when transmitting), are as indicated in the Figure.

Please see +3.3V isolation transformer limitations and recommendations.

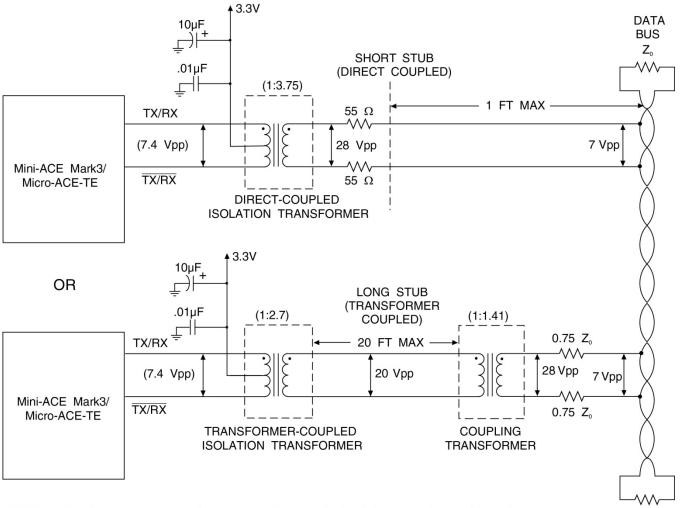
In accordance with MIL-STD-1553B, the turns ratio of the coupling transformer is required to be 1.0 to 1.4. For both coupling configurations, isolation resistors are required to be in series with each leg connecting to the 1553 bus. In the case of direct coupling, the value of the coupling resister is 55 ohms. For direct coupling, the isolation resistors are located within the 1553 BC, RT, or Monitor terminal. In the case of transformer coupled, the resistors are 0.75 Z_0 in value and are located in the bus coupler, rather than the BC, RT, or Monitor terminal. The isolation resistors protect the bus against short circuit conditions in the transformers, stubs, or terminal components.

For most system applications, transformer (stub) coupling is preferred over direct coupling. Some of the advantages of transformer coupling are:

(1) Looking from the 1553 bus towards the stub, the effect of the 1.4 to 1.0 stepdown of the coupling transformer will be to **double** the impedance of the stub/terminal combination, as seen by the bus. Since the stub impedance decreases as a function of stub length due to distributed cable capacitance, this doubling effect serves to reduce the amount of impedance loading on the bus by individual terminals. For this reason, stub coupled terminals may be located up to 20 feet from the bus; the distance for direct coupled terminals is limited to 12 inches.

(2) Looking from the isolation transformer down the stub (towards the bus), the impedance seen is Z_0 . Therefore, the characteristic impedance of the stub cabling (78 ohms nominal) matches the stub's load impedance, minimizing reflections back toward the transmitter.

(3) In a direct-coupled terminal, the main bus is not protected against a short circuit in the stub cabling. For the transformer coupled case, the bus is protected against such a fault.



(4) A transformer coupled terminal provides improved DC and common mode isolation over a direct-coupled terminal.

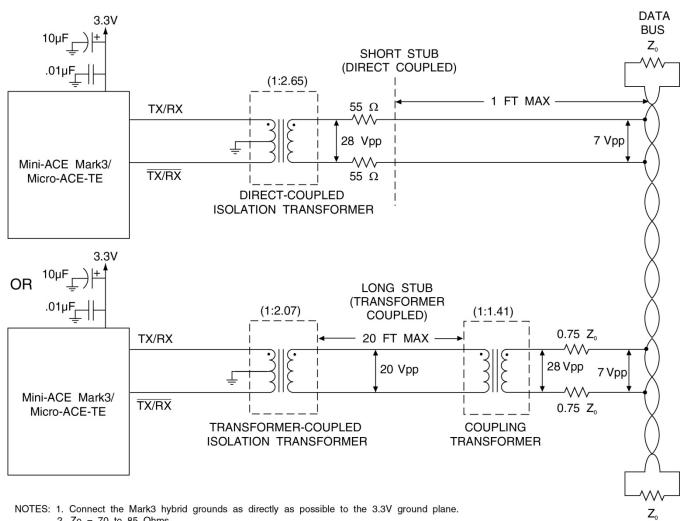
NOTES: 1. Transformer center tap capacitors: use a 10µF tantalum for low inductance, and a 0.01µF ceramic. Both must be mounted as close as possible, and with the shortest leads to the center tap of the transformer(s) and ground.

2. Connect the Mark3 hybrid grounds as directly as possible to the 3.3V ground plane.

3. Zo = 70 to 85 Ohms.

Figure 5. Enhanced Mini-ACE Series Interface to 1553 Bus (+3.3V Transceivers [X8/9] & MIL-STD-1553 Trim shown)

Z₀



2. Zo = 70 to 85 Ohms.

Figure 6. Enhanced Mini-ACE Series Interface to 1553 Bus (+3.3V Transceivers [XC/D] & MIL-STD-1553 Trim shown)

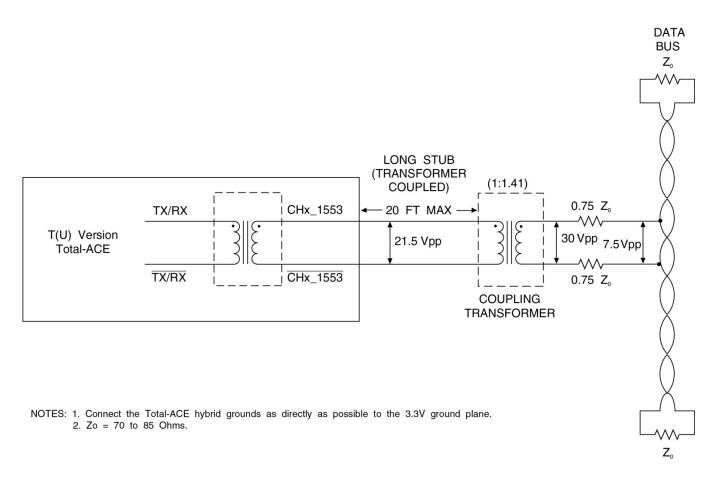


Figure 7. Total-ACE Series Interface to 1553 Bus (+3.3V Transceivers [X8] & MIL-STD-1553 Trim shown)

7.1 +3.3 Volt Isolation Transformers

Please see MN-6186X-003 Appendix A for +3.3V isolation transformer limitations and recommendations.

8 THERMAL MANAGEMENT FOR MICRO-ACE AND MIRCO-ACE-TE (BGA PACKAGE)

Ball Grid Array (BGA) components necessitate that thermal management issues be considered early in the design stage for MIL-STD-1553 terminals. This is especially true if high transmitter duty cycles are expected. The temperature range specified for DDC's Micro-ACE, Micro-ACE-TE, and Total-ACE device refers to the temperature at the ball, not the case.

All Micro-ACE, Micro-ACE-TE, and Total-ACE devices incorporate multiple package connections that perform the dual function of transceiver circuit ground and thermal heat sink. **Refer to datasheet pinout tables for thermal ball connection locations.** It is mandatory that these thermal balls be directly soldered to a circuit ground/thermal plane (a circuit trace is insufficient). Operation without an adequate ground/thermal plane is not recommended and extended exposure to these conditions may affect device reliability.

The purpose of this ground/thermal plane is to conduct the heat being generated by the transceivers within the package and conduct this heat away from the Micro-ACE, Micro-ACE-TE, and Total-ACE. In general, the circuit ground and thermal (chassis) ground are not the same ground plane. It is acceptable for these balls to be directly soldered to a ground plane but it must be located in close physical and thermal proximity (0.003" pre-preg layer recommended) to the thermal plane.

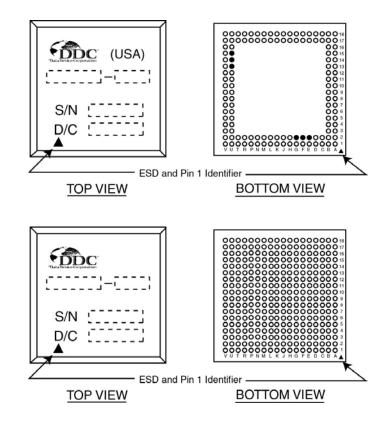


Figure 8. Ball Locations for Micro-ACE-TE and Micro-ACE (BGA Packages)

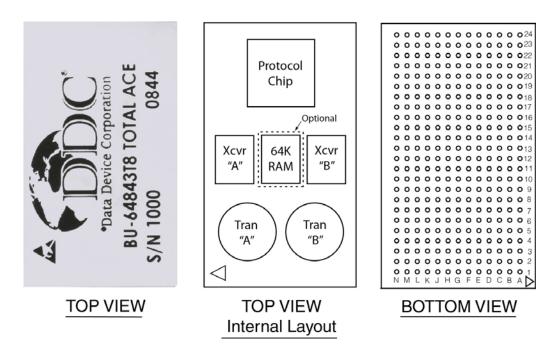


Figure 9. Ball Locations for Total-ACE (BGA Package)

8.1 Power Supply and PC Board Considerations

With regard to the Enhanced Mini-ACE terminal and the associated isolation Transformers (Note: Total-ACE features integral isolation transformers), there are a number of important factors to consider relating to component placement, circuit routing, and power distribution. Some of these factors include:

(1) Power and Ground Distribution:

Any resistance will result in power supply input voltage drops, which can lower the transmitter output voltage below the minimum level required by MIL-STD-1553. It is important to minimize the power distribution impedance along the transceivers high current path.

For devices with X3/4 (+5V) or XC/D (+3.3V) transceivers, the high current path (while transmitting) is from the positive voltage supply into the device, through the transmitter output stage, through one leg of the isolation transformer to the grounded transformer primary winding center tap (see Figure 10).

For devices with X8/9 (+3.3V) transceivers, the high current path (while transmitting) is from the +3.3 volt supply into the transformer primary winding center tap, through one leg of the isolation transformer, through the transmitter output stage and the device GROUND pins (see Figure 11).

It is important to realize that in both cases the high current path is through (and includes) the transformer primary winding center tap. A worst-case analysis should ensure that with minimum supply voltage (and calculated voltage drops), the voltage delivered between device power supply pins (Vcc or Gnd) and the center tap of the respective transformer will be no less than the specified minimum voltage of 4.75V (X3/4 option) or 3.15V (X8/9/C/D option).

In some cases, excessive transmitting voltage drops can be reduced by means of larger decoupling capacitors, but it is best to minimize these voltage drops at the PCB design stage with low resistance conductors.

(2) Component & Signal Spacing:

Avoid running 1553 analog signal traces in close proximity to other analog or digital signals on the board (especially those running in parallel) as severe crosstalk can increase the receiver's bit error rate, zero-crossing distortion, or common mode rejection beyond that allowed by MIL-STD-1553.

Isolation transformers should be placed as close as is physically possible to the respective TX/RX pins on the device. This serves to minimize crosstalk from other signals in addition to minimizing the voltage drop in the traces. The trace lengths of the complementary, input/output signal pairs should also be minimized and closely matched in length as well.

(3) Power & Ground Planes:

As is the rule in all high-speed digital circuits, it is good practice to incorporate ground and power supply planes under the MIL-STD-1553 device, Bi-Phase data output lines (out of device transceivers) and Isolation transformers.

Isolation transformer secondary output traces to the bus (or stub) should not have ground or power planes under them.

Distributed capacitance tends to lower the input impedance of the terminal as seen from the 1553 bus. MIL-STD-1553 requires there be a minimum input impedance of $2k_{\Omega}$ for direct-coupled and $1k_{\Omega}$ for transformer-coupled (stub) terminals. It is likely that the terminal will not meet this requirement if there are ground or power planes under the isolation transformer secondary output traces to the bus (or stub).

IMPORTANT NOTE:

It is very important that there be ground and/or power supply planes underneath the MIL-STD-1553 device, the Bi-Phase data output lines (out of device transceivers) and Isolation transformers.

There <u>should NOT</u> be any ground or power planes beneath the TX/RX signals emanating from the isolation transformer secondary output winding to any connector or cables leaving the board.

(4) Analog and Digital Grounds:

The BU-61743/61745 RT, and BU-61843/61845/61864/61865 BC/RT/MT Enhanced Mini-ACE (BU-61740B RT, and BU-61840B/61860B BC/RT/MT Micro-ACE) logic and transceiver grounds ARE connected together inside the hybrid.

The BU-64743/64745 RT, and BU-64843/64845/64863 BC/RT/MT Mini-ACE Mark3 (BU-64840B/64843B/64860B/64863B BC/RT/MT Micro-ACE-TE) and BU-64843T Total-ACE, logic and transceiver grounds are NOT connected together inside the hybrid.

(5) Decoupling Capacitors:

Two relatively small ceramic capacitors $(0.1\mu f)$, with both low Effective Series Resistance (ESR) and low Effective Series Inductance (ESL), are generally necessary for the LOGIC & RAM power inputs as well as the transceiver power inputs on the device. These reduce the high-frequency power supply noise that may result from the 1MHz and 2MHz current pulses drawn by the transceivers.

A 10µf tantalum capacitor located at the device transceiver power inputs is usually sufficient to compensate for voltage drops due to the increased current requirement (100s of mA) while transmitting.

If the voltage at the device transceiver power inputs is greater than the required minimum when not transmitting, but less than the minimum when transmitting, then a larger tantalum capacitor may be necessary to sustain the power input voltage above the minimum level while transmitting. This capacitor could be sized by a process of trial and error while the transceiver is transmitting 32 data word (worst case) messages at duty cycles representing typical system operation.

(6) Location of the Clock Oscillator:

The Clock Oscillator should be located as close as physically possible to the clock input pin on the device.

(7) In Summary:

For all devices, two, 0.1µf ceramic decoupling capacitor on both LOGIC & RAM power inputs.

For devices, with X3/4/C/D transceivers, DDC recommends a 10µf tantalum capacitor in parallel with a 0.1µf ceramic capacitor (see Figure 10).

For devices with X8/9 transceivers, DDC recommends a $1.0\mu f$ tantalum capacitor in parallel with a $0.1\mu f$ ceramic capacitor (see Figure 11).

These capacitors should be located as close as possible to the Vcc input pads and should be sufficient for most applications.

Additionally, for devices with X8/9 transceivers, a 10μ f tantalum capacitor in parallel with a $.01\mu$ f ceramic capacitor must be located as close as possible to the center tap of the transceiver isolation transformer.

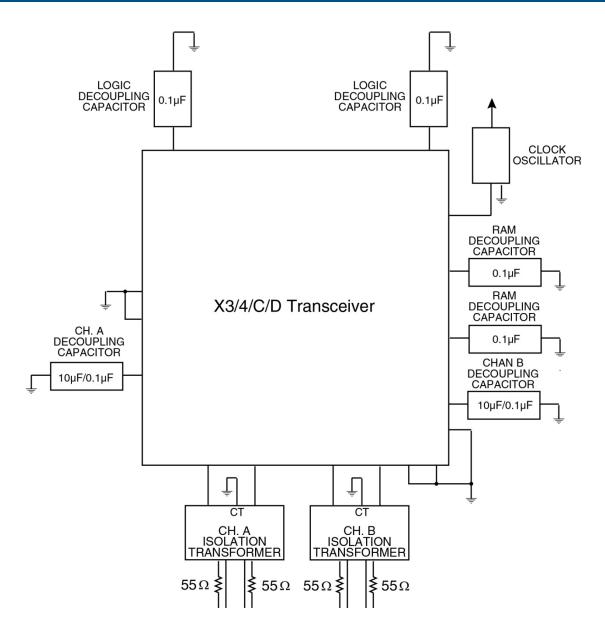


Figure 10. P.C. Board Layout Example: X3/4/C/D Transceiver

Figure 10 Notes:

- 1. Physical spacing between Enhanced Mini-ACE® and isolation transformers must be kept to a minimum.
- 2. There must be ground and/or power supply planes underneath the device, the Bi-Phase data output lines (out of device transceivers) and isolation transformers.
- 3. There should not be any ground or power supply planes underneath the TX/RX signals emanating from the isolation transformers secondary output winding to any connector or cables leaving the board.

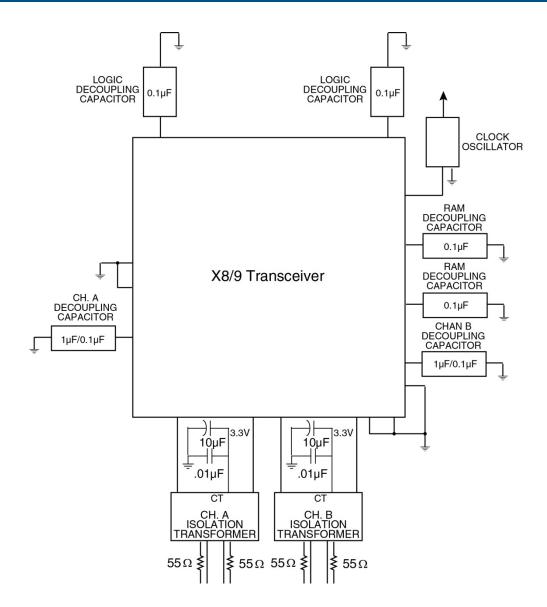


Figure 11. P.C. Board Layout Example: X8/9 Transceiver

Figure 11Notes:

- 1. Physical spacing between Enhanced Mini-ACE[®] and isolation transformers must be kept to a minimum.
- 2. There must be ground and/or power supply planes underneath the device, the Bi-Phase data output lines (out of device transceivers) and isolation transformers.
- 3. There should not be any ground or power planes beneath the TX/RX signals emanating from the isolation transformers secondary output winding to any connector or cables leaving the board.
- 4. The two isolation transformers are an integral part of the Total-ACE[®].

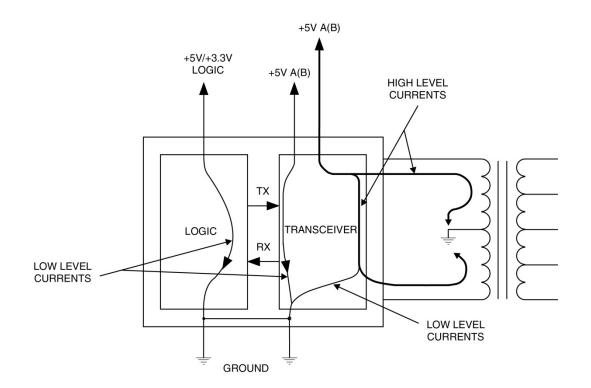


Figure 12. Power/Ground Current Distribution for +5V Transceivers (X3/4 Option)

8.2 Simplified Equivalent Circuit of Transceiver

Refer to the circuit illustrated in Figure 13. V_{in} is defined to be the rated minimum output voltage from the power supply. R_d is the series resistance of the power distribution path to the transceiver power inputs. This includes resistance in the power supply return path, from the transformer center tap, as well as the power input path.

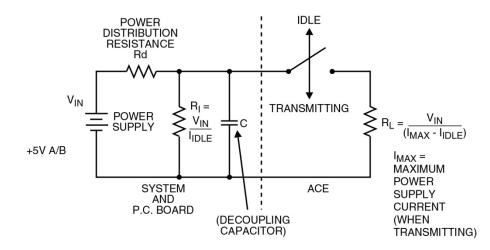


Figure 13. Simplified Equivalent Circuit of Enhanced Mini-ACE Terminal

8.3 Isolation Transformer Interface to System Connector

The general practice in connecting the stub side of a transformer (or direct) coupled terminal to an external system connector is to make use of 78 ohm twisted-pair shielded cable. This minimizes impedance discontinuities. The decision of whether to isolate or make connections between the center tap of the isolation transformer's secondary, the stub shield, the bus shield, and/or chassis ground must be made on a system basis, as determined by an analysis of EMI/RFI and lightning considerations. In most systems, the secondary center tap is **not** grounded. In some systems, it is specified that the 1553 terminal's input impedance must be measured at the system connector. This is despite the fact that the MIL-STD-1553B requirement is for it to be measured looking directly in from the bus side of the isolation transformer. The effect of a relatively long stub cable will be to reduce the measured impedance. If this reduces the impedance below the required level of 1000 ohms (for transformercoupled stubs), it is sometimes possible to increase the impedance somewhat by using a pair of coax wires (with the shields ungrounded), rather than a single twisted/shielded pair, for the stub connections. The effect on the rest of the system performance of the bus signals coupled from the ungrounded shielded cables must be considered as a tradeoff against the increased terminal impedance.

8.4 Simulated Bus (Lab Bench) Interconnections

For purposes of software development and system integration, it is generally not necessary to integrate the required couplers, terminators, etc., that comprise a complete MIL-STD-1553B bus. In most instances, a simplified electrical configuration will suffice. The interconnection methods illustrated in Figure 14 allows the device to be interfaced over a "simulated bus" to simulation and test equipment. The length of this "simulated bus" should not exceed 5 feet. It is important to note that the termination resistors indicated are necessary (if not already present within the test/simulation equipment) in order to ensure reliable communications between the device and the simulation/test equipment. As illustrated In Figure 14, the 78 Ω and 39 Ω termination resistors should be physically located as close as possible to the test/simulation equipment.

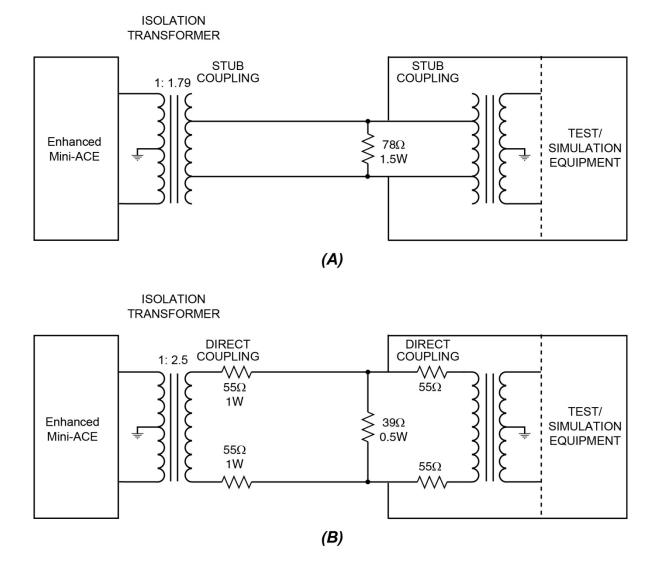
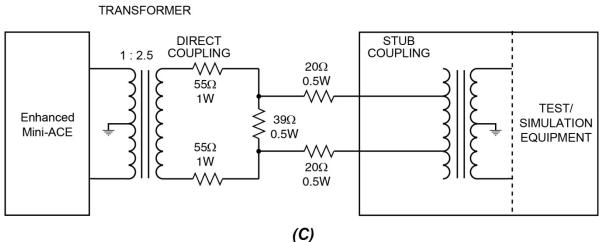


Figure 14. Simulated Bus Interconnections

Figure 14 Note:

- (A) Transformer Coupled Enhanced Mini-ACE-to-Transformer Coupled Equipment
- (B) Direct Coupled Enhanced Mini-ACE-to-Direct Coupled Equipment



ISOLATION



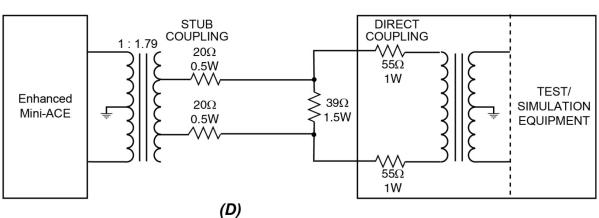


Figure 14. Simulated Bus Interconnections

Figure 14 Note:

(C) Direct Coupled Enhanced Mini-ACE-to-Transformer Coupled Equipment

(D) Transformer Coupled Enhanced Mini-ACE-to-Transformer Coupled Equipment

8.5 Logic Compatibility

The Enhanced Mini-ACE's logic signals provide compatibility with both TTL and CMOS type systems. In addition, the BU-61XX**3(4)** versions of the Enhanced Mini-ACE, which operates from a 3.3V logic supply, provides tolerance to external 5 volt logic. That is, the absolute maximum rating for "Logic Input Voltage" for versions of Enhanced Mini-ACE operating from either +5V or +3.3V logic power is 6.0V. To enable this, the Enhanced Mini-ACE's input and I/O pad cells include clamping diodes to LOGIC GROUND, but do **not** include clamping diodes to V_{cc}-LOGIC.

The output and I/O signals are capable of sourcing and sinking up to 3.4 mA.

There are active "pull-up" type current sources from V_{cc} on all of the inputs and I/O signals except for the clock input, CLK_IN. The value of these current sources is specified for a range of 50 to 350 μ A.

There are Schmidt triggers on all digital input signals (including I/Os), including the clock input. All input signals (and the inputs on I/O signals) except for CLK_IN are TTL type, with V_{IL} = 0.7V max, V_{IH} = 2.1V min, and a minimum Schmidt hysteresis window of 0.4V. CLK_IN is a CMOS type input signal, with a V_{IL} of 0.2• V_{CC} max, a V_{IH} of 0.8• V_{CC} min, and a minimum Schmidt hysteresis window of 1 volt.

9 HOST PROCESSOR AND MEMORY INTERFACE

The Enhanced Mini-ACE provides a great deal of flexibility for interfacing to a host processor and optional external memory. As shown in Figure 15, there are 14 control signals (13 for the Mini-ACE series terminals), 6 of which are dual purpose, for the processor/memory interface. Figure 15 through Figure 20 illustrate six of the configurations that may be used for interfacing an Enhanced Mini-ACE to a host processor bus. The various possible configurations serve to reduce to an absolute minimum the amount of "glue" logic required to interface to 8-, 16-, and 32_bit processor buses. In addition, features are included to facilitate interfacing to processors that do not have a "wait state" type of handshake acknowledgment. Finally, the Enhanced Mini-ACE supports a reliable interface to an external dual port RAM. This type of interface minimizes the portion of the available processor bandwidth required to access its internal 1553 RAM.

9.1 Address Mapping: Words vs. Bytes

It is important to note that with respect to the Enhanced Mini-ACE's address bus, A15 through A0, all address mapping is **word oriented**, rather than byte oriented. Although there are a few exceptions, inherent address mapping for most standard 8-, 16-, and 32-bit microprocessors is **byte oriented**. This difference in mapping convention must be taken into account when assigning pointer values and making CPU accesses to the Enhanced Mini-ACE's internal data structures (stack, lookup tables, data tables, etc.) in the Enhanced Mini-ACE's shared RAM address space. That is, in terms of the CPU's memory map, the address of these data structures, relative to the Enhanced Mini-ACE's base memory address, will be **double** the value of the pointer that is stored in the Enhanced Mini-ACE's shared RAM.

For interfacing to most 16-bit microprocessors, the processor's A1 signal connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A1 pin, etc. For interfacing to an 8-bit microprocessor, the processor A0 output connects to the Enhanced Mini-ACE's MSB/LSB input, the processor's A1 output connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A0 pin, processor A2 connects to the Enhanced Mini-ACE's A1 pin, etc.

While the Enhanced Mini-ACE's internal shared RAM is intended primarily for the buffering of 1553 messages and related pointer data, it is important to noted that there is **no restriction** prohibiting the use of this RAM for general purpose program memory or "scratchpad" data memory.

9.2 16-Bit Buffered Mode

The 16-bit buffered mode (Figure 15) is the most common interface configuration used. It provides a direct, shared RAM interface to a 16-bit or 32-bit microprocessor.

In this mode, the Enhanced Mini-ACE's internal address and data buffers provide the necessary isolation between the host processor's address and data buses and the corresponding internal memory buses.

Depending on which version of Enhanced Mini-ACE, Mini-ACE Mark3, Micro-ACE(TE), or Total-ACE is used, there may be either 4K X 16 or RAM or 64X 16 of RAM. For a version with 4K X 16 of RAM, the upper address signals A15-A12 may be either connected to the host address bus, hardwired to logic '0' or '1', or left disconnected. For a version with 64K X 16 of RAM, all 16 address signals A15-A0 should be connected to the host address bus.

In the shared RAM configuration, the processor **always** has access to its own buses. That is, the Enhanced Mini-ACE will **never** request the use of the CPU buses. This provides the advantage of allowing the Enhanced Mini-ACE to access its buffer RAM while the CPU is able to **simultaneously** use its buses to access its memory or I/O. In this way, a shared RAM interface utilizes less of the CPU's bandwidth than does a DMA interface.

In the 16-bit buffered mode, note that TRANSPARENT/BUFFERED* is strapped to logic "0," while 16/8*-BIT is connected to logic "1." The input signal ADDR_LAT may be used to demultiplex the address bus. For examples, for some Intel microprocessors (i.e., Intel 80186), the CPU's ALE output should be connected to ADDR_LAT. If not used, ADDR_LAT should be connected to logic "1."The logic sense of the RD/WR* control input is selectable by means of the POLARITY SEL input. For example, POLARITY_SEL should be connected to logic "1" to write on RD/WR* low for Motorola 680X0 processors; POLARITY SEL should be connected to logic "0" to write on RD/WR* high for Intel i960 series processors. By strapping the input signal ZERO WAIT* to logic "1," the Enhanced Mini-ACE may be interfaced to processors that have an acknowledge type of handshake input to accommodate hardware controlled wait states; most current processor chips have such an input. For this type of processor, the Enhanced Mini-ACE will assert its READYD* output low only after it has latched data to be written or has presented data to be read on D15-D0. In the nonzero wait mode, the host processor terminates the transfer cycle by releasing STRBD* high after the Enhanced Mini-ACE has asserted READYD* low.

By strapping ZERO_WAIT* to logic "0," it is possible to easily interface the Enhanced Mini-ACE to processors that **do not** have an acknowledge type of handshake input. An example of such a processor is Analog Device's ADSP2101 DSP chip. In this configuration, the processor can clear its strobe output (the Enhanced Mini-ACE's STRBD* input) before the access to the Enhanced Mini-ACE has been completed (before READYD* goes low).

In the buffered configuration, the host initiates an access to the Enhanced Mini-ACE's internal RAM or registers by asserting the signals SELECT*, STRBD*, MEM/REG*, and RD/WR*. SELECT* and MEM/REG* are generally the outputs of an address

decoder. SELECT* must be asserted low to access the Enhanced Mini-ACE's RAM or registers. MEM/REG* must be presented high for memory access and low for register access. If POLARITY_SEL is logic "1," RD/WR* must be presented high to read and low to write; if POLARITY_SEL is logic "0," RD/WR* must be presented low to read and high to write. STRBD* is the main processor control input to the Enhanced Mini-ACE to control the length of an access cycle.

9.3 Zero Wait Configuration

Some microprocessors **do not** have a "strobe/acknowledge" type of handshake mechanism. In this case, the Enhanced Mini-ACE's "zero wait" interface configuration may be used by strapping ZERO_WAIT* to logic "0." In this mode, the CPU is able to release STRBD* high **before** the Enhanced Mini-ACE's READYD* output transitions from high to low and back to high. The low-to-high transition of READYD* indicates the end of the Enhanced Mini-ACE's internal transfer cycle. This mode takes advantage of the Enhanced Mini-ACE's internal address and data latches and added control logic and serves to minimize the amount of "glue" logic required.

In the 16-bit zero wait mode, the CPU writes a word by presenting the address and data for the word to be written on A15-A0 and D15-D0 respectively. To implement a single zero wait read operation, the host processor must perform **two** read accesses to the Enhanced Mini-ACE. During the first access, the address and transfer type indication (memory or register) of the location to be read must be asserted on A15-A0 and MEM/REG*, respectively. The data read on D15-D0 during this cycle **should be ignored ("thrown away")**. During the **second** read access, the Enhanced Mini-ACE presents the data corresponding to the address presented on the **first** access on D15-D0. If the CPU performs a multi-word read burst, the address for the **next** word should be presented on A15-A0 on the same cycle that data is read from D15-D0. That is, for a multi-word read transfer, the address presented should always be **one location ahead** of that of the data being read.

In the zero wait mode, STRBD* must be asserted low for a minimum of 20 ns. Reference Figure 35 and Figure 40. If STRBD* is not sampled low for two rising edges of the clock input CLK_IN, READYD* will go low within 40 ns after the rising edge of STRBD*. If STRBD* is sampled low for two rising edges of CLK_IN, READYD* will go low within 40 ns after the second rising clock edge. In either case, the Enhanced Mini-ACE's internal transfer cycle will not begin until after the second rising edge of CLK_IN and STRBD* is returned to logic "1." When the Enhanced Mini-ACE initiates the internal transfer, it asserts the output signal IOEN* low for four clock cycles. When the Enhanced Mini-ACE completes the internal transfer cycle, IOEN* clears high. One-half clock cycle after IOEN* goes high, the Enhanced Mini-ACE acknowledges completion of the transfer by re-asserting READYD* high. In the zero wait mode, the CPU can determine if the Enhanced Mini-ACE has completed its transfer cycle by polling the value of the READYD* output.

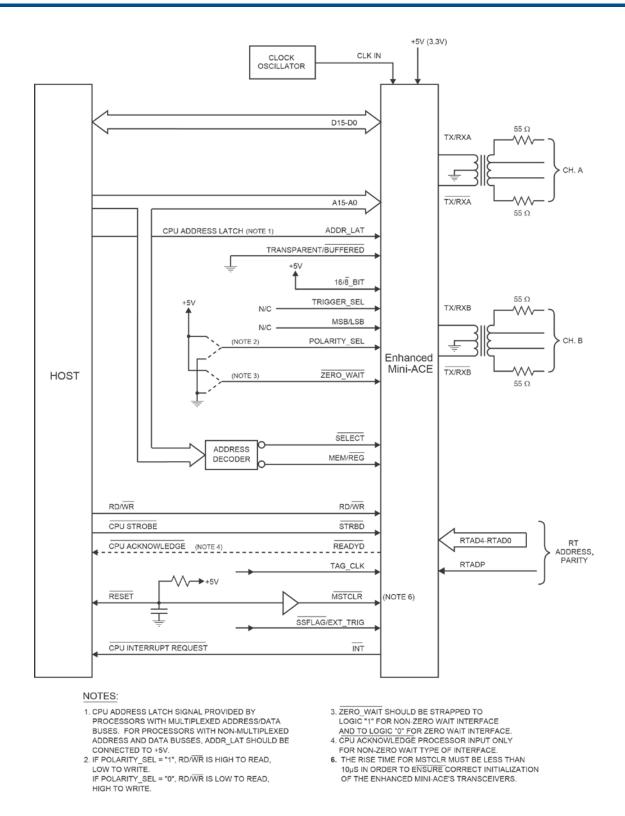


Figure 15. Interconnection Diagram for 16-Bit Buffered Mode

9.4 16-Bit Transparent Mode

Similar to the 16-bit buffered mode, the 16-bit transparent mode (Figure 16) supports a shared RAM interface to a host CPU. The transparent mode offers the advantage of allowing the buffer RAM size to be expanded to up to 64K words, using external RAM. For BU-61864(5), which contain 64K of internal RAM, the user may operate in transparent mode, but the combination of internal and external RAM must not exceed 64K words.

A disadvantage of the transparent mode is that external address and data buffers are required to isolate the processor buses from the Enhanced Mini-ACE buses. In the transparent mode, the host is able to access up to 64K of external RAM. Like the buffered mode, the host is able to use its data/address buses while the Enhanced Mini-ACE **simultaneously** accesses its internal or external shared RAM. Note that in the transparent configuration, external tri-state buffers are required to isolate the CPU's data/address buses from the Enhanced Mini-ACE's RAM buses. Table 1 summarizes the operation of the Enhanced Mini-ACE's tri-state address and data bus buffers for the 16-bit buffered and transparent modes.

Table 1. Operatio	n Of Addre	ess and Data E	Buffers For 1	6-Bit Interfa	aces
TRANSPARENT/BUFFERED MODE	CPU/1553 ACCESS	READ/WRITE	INT/EXT RAM (NOTE 1)	ADDRESS BUFFERS	DATA BUFFERS
Buffered	CPU	WRITE	INT	\longrightarrow	\longrightarrow
Buffered	CPU	READ	INT	\longrightarrow	←
Buffered	1553	WRITE	INT	Hi-Z	Hi-Z
Buffered	1553	READ	INT	Hi-Z	HiZ
Transparent	CPU	WRITE	INT	\longrightarrow	\longrightarrow
Transparent	CPU	WRITE	EXT	\longrightarrow	Hi-Z
Transparent	CPU	READ	INT	\longrightarrow	\longrightarrow
Transparent	CPU	READ	EXT	\longrightarrow	Hi-Z
Transparent	1553	WRITE	INT	←	←
Transparent	1553	WRITE	EXT	<i>~</i>	←
Transparent	1553	READ	INT	←	←
Transparent	1553	READ	EXT	<i>~</i>	←

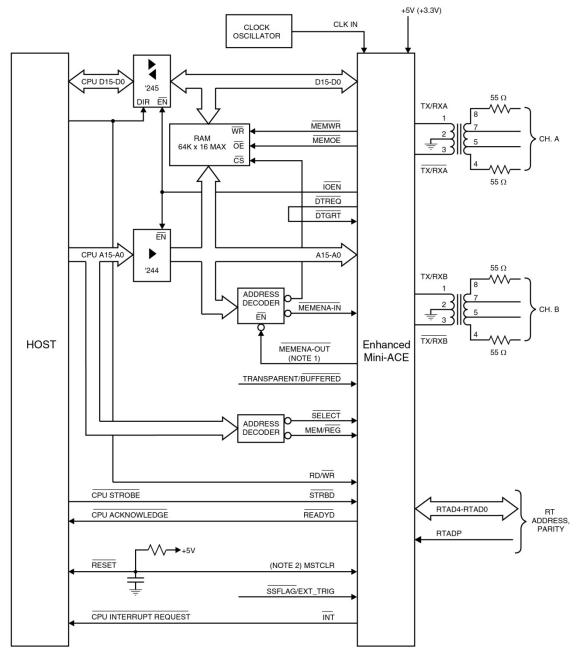
Table 1. Operation Of Address and Data Buffers For 16-Bit Interfaces										
TRANSPARENT/BUFFERED MODE	CPU/1553 ACCESS	READ/WRITE	INT/EXT RAM (NOTE 1)	ADDRESS BUFFERS	DATA BUFFERS					
Table 1 Notes: 1. The Enhanced Mini-AC input signal MEMENA-I										

3. " ----- " indicates buffers enabled in direction from internal memory bus towards external processor bus.

4. "Hi-Z" indicates buffers are in high impedance (tri-state) condition in both directions.

In the transparent mode (reference Figure 16), the memory control signals, MEMWR* and MEMENA-IN* must be connected to the respective control inputs of external RAM.

The external RAM \overline{CS} signal (the external address decoder input) may be derived by logically OR'ing DTACK* and IOEN* {i.e., \overline{CS} (low) = \overline{DTACK} (low) or \overline{IOEN} (low)}. If the Enhanced Mini-ACE's internal RAM is used, the address decoder output to select this RAM must be connected to the Enhanced Mini-ACE's MEMENA-IN* input. If the Enhanced Mini-ACE's internal RAM is not used, MEMENA-IN* must be connected to logic "1." As shown in the figure, the Enhanced Mini-ACE's IOEN* output should be connected to the tri-state enable inputs of the external address and data buffers. In the transparent mode, there is an extra clock cycle (four, instead of the three in buffered mode) between the falling edge of IOEN* and the falling edge of the acknowledge (handshake) output READYD*. This extra time is provided to accommodate the enable times and propagation delays associated with the external tri-state buffers.



NOTES:

- 1. MEMENA-OUT IS NOT AVAILABLE ON THE ENHANCED MINI-ACE SERIES TERMINALS BUT MAY BE REPLACED BY LOGICALLY OR'ING DTACK WITH IOEN.
- 2. THE RISE TIME FOR MSTCLR MUST BE LESS THAN 10 mS IN ORDER TO ENSURE CORRECT INITIALIZATION OF THE ENHANCED MINI-ACE'S TRANSCEIVERS.

Figure 16. Interconnection Diagram for 16-Bit Transparent Mode (Shown with +5V Transceiver)

9.5 16-Bit Dual Port RAM Interface

A modified version of the transparent mode involves the use of external dual port RAM, rather than conventional static RAM (Reference Figure 17). This allows the host to access RAM very quickly (the only limitation is essentially the RAM speed); the Enhanced Mini-ACE arbitration delays are eliminated in this instance. The worst case delay time occurs only during simultaneous access by the host CPU and the Enhanced Mini-ACE to the same memory address; in general, this will occur very rarely and the delay is limited to approximately 250 ns.

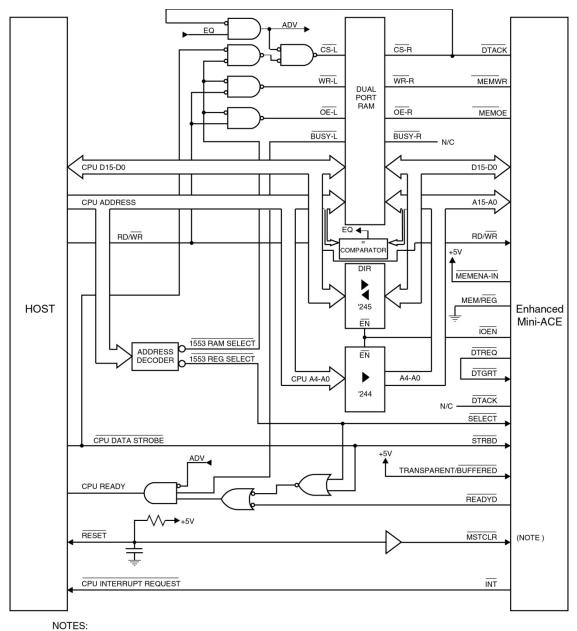
In the dual port RAM interface, one side of the RAM is accessed by the host CPU, while the other side is accessed by the Enhanced Mini-ACE's "1553" logic, by means of the memory control signals. Note that tri-state buffers are required on the address and data buses in order for the CPU to be able to access the Enhanced Mini-ACE's internal registers. Note that the Enhanced Mini-ACE input signal MEM/REG* is hardwired to logic "0," and SELECT* is connected to the address decoder output 1553 REG SELECT* to enable the register accesses. The signal CPU READY is asserted low (indicating "not ready") under either of two conditions:

When the dual port RAM's BUSY-L* output is asserted, indicating that the host tried to access the same location currently being accessed by the 1553 logic. Note that with most dual port RAM chips, a "Busy" condition will only result when both sides are performing an access to the same address location.

CPU READY will be asserted low during the time of a register access, prior to the completion of the Enhanced Mini-ACE's transfer cycle. That is, during the time that the SELECT* and STRBD* inputs are asserted low, but before READYD* is asserted low.

IMPORTANT NOTE:

In this configuration, the dual port RAM's BUSY-R* output is not connected. As a result, it is important to note that the length of the pulse (low) presented on the dual port RAM's CS-L* input (derived from the CPU's CPU DATA STROBE* output) must be less than 100 ns. If CS-L* is asserted low for too long, it may cause the Enhanced Mini-ACE's "1553" logic to miss a transfer cycle. This could have the effect of corrupting a 1553 message (on an Enhanced Mini-ACE read cycle) or causing the Enhanced Mini-ACE to not store a word in the dual port RAM (on an Enhanced Mini-ACE write cycle).



THE RISE TIME FOR $\overline{\text{MSTCLR}}$ MUST BE LESS THAN 10 μ S IN ORDER TO ENSURE CORRECT INITIALIZATION OF THE ENHANCED MINI-ACE'S TRANSCEIVERS.

Figure 17. Interconnection Diagram for 16-Bit Dual Port RAM Mode

9.6 16-Bit DMA Mode

Figure 18 illustrates the connections for the 16-bit Direct Memory Access (DMA) mode. In this configuration, use of the address and data buses is arbitrated by the host processor, rather than by the Enhanced Mini-ACE. The arbitration involves the three DMA control signals Request (DTREQ*), Grant (DTGRT*), and Acknowledge (DTACK*). The DMA interface allows the Enhanced Mini-ACE to interface to large amounts of system RAM. For system address spaces greater than 64K words, it is necessary for the host processor to provide a page register for the upper address bits (above A15) when the Enhanced Mini-ACE accesses the RAM (DTACK* is asserted low).

The internal RAM is accessible through the standard Enhanced Mini-ACE interface (SELECT*, STRBD*, READYD*, etc). The host CPU may access external RAM by means of the Enhanced Mini-ACE's arbitration logic and output control signals, as illustrated in Figure 18. Alternatively, control of the RAM may be multiplexed between the host processor and the Enhanced Mini-ACE, as shown in Figure 19. The latter requires the use of external logic, but allows the processor to access the RAM directly at the full access speed of the RAM, rather than waiting for the Enhanced Mini-ACE handshake acknowledge output (READYD*).

In the DMA configuration, the host processor controls access to the address and data buses by means of a request/grant/acknowledge handshake. Refer to Figure 18. When the 1553 terminal needs to transfer a word or block of words to RAM, it requests use of the buses from the host CPU by asserting its DTREQ* (Data Transfer Request) output low. When the host CPU completes its current instruction cycle, it relinquishes use of the buses by asserting DTGRT* (Data Transfer Grant) low. When the Enhanced Mini-ACE samples DTGRT* low on a rising edge of CLK_IN, it asserts DTACK* (Data Transfer Acknowledge) low to indicate that the Enhanced Mini-ACE has accepted control of the buses.

For the configuration in Figure 18, the ENABLE input to the address decoder is formulated by logically OR'ing DTACK* and IOEN* as shown, that is, ENABLE* (low) = DTACK* (low) or IOEN* (low). For the configuration in Figure 19, DTACK* (**not** gated with IOEN*) is used to enable the Enhanced Mini-ACE's external RAM access. In either case, the resulting signal can be connected to an external address decoder to derive MEMENA-IN* for internal RAM access, or CS* input(s) to external RAM. DTACK* will remain asserted for four clock cycles (200 ns at 20 MHz, 250 ns at 16 MHz, 333 ns at 12 MHz, 400 ns at 10 MHz) to complete a single-word transfer cycle. For a read cycle, the Enhanced Mini-ACE output MEMOE* (Memory Output Enable) is asserted low; for a write cycle, MEMWR* (Memory Write) is asserted low. For a multiword transfer cycle during a Start-of-Message (SOM), End-of-Message (EOM), or BC Retry sequences, DTACK* will remain asserted for an additional [4•(number of words)] clock cycles; either MEMOE* or MEMWR* will be asserted for each word cycle.

In the DMA configuration, the host has two mechanisms for accessing external RAM. As shown in Figure 18, the host can access the RAM by means of the Enhanced Mini-ACE's control signals SELECT*, STRBD*, MEM/REG*. RD/WR*, READYD*, MEMWR* and MEMOE*. While this requires no external control logic, it does entail about 250 ns of processor bandwidth to complete an access. This time allows the Enhanced Mini-ACE to arbitrate between 1553 and CPU accesses, and between internal and external RAM access and to enable internal tri-state buffers. Alternatively, in the configuration of Figure 19, the host processor's access time to read or write the external RAM is reduced by means of the extra logic gates shown. The only limitations are the CPU's strobe width, the access time of the RAM, and the gate delays. Note that in this configuration, the host must still activate the signals SELECT*, STRBD*, etc. in order to access the Enhanced Mini-ACE's internal registers.

9.7 Handshake Timeout

In the DMA or transparent modes, the host processor must allow the Enhanced Mini-ACE's 1553 logic to gain access to the system address and data buses to read and write memory. In order to ensure that words are transferred to/from RAM when required during the processing of 1553 messages, the CPU must provide the Enhanced Mini-ACE access to the system buses within the allotted time. The allotted time is 10.5 μ s when using a 20 MHz clock input, 10 μ s when using a 16 MHz clock input, 9 μ s when using a 12 MHz clock, and 8.5 μ s when using a 10 MHz clock input. If the CPU fails to provide access within the allotted time, the Enhanced Mini-ACE will be unable to transfer a word or burst of words.

A Handshake Timeout can occur on Data Word Transfers in all modes, and during Start-of-Message (SOM) sequences in RT or Message Monitor modes.

Note that a Handshake Timeout condition will **not** occur during the following transfer sequences: BC Start-of-Message (SOM), End-of-Message (EOM), and Retry sequences; Word Monitor start sequence; RT End-of-Message (EOM) sequence; and Message Monitor End-of-Message (EOM) sequence.

The handshake timer will expire in either of two circumstances:

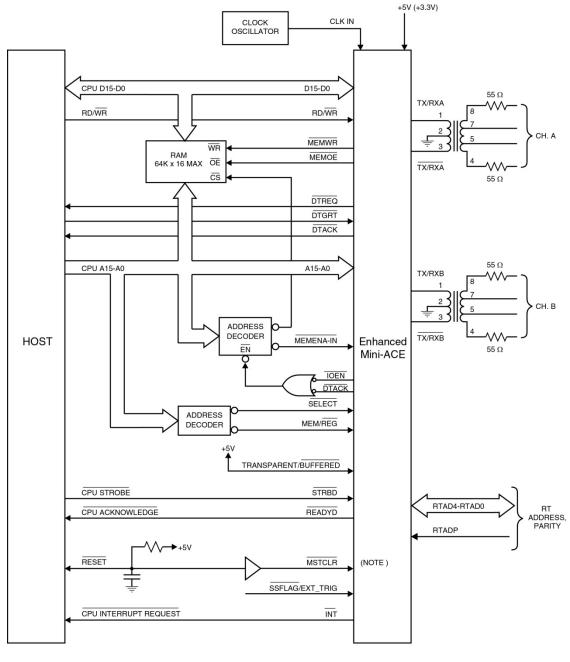
(1) In the DMA configuration, if the host processor did not assert DTGRT* (low) within the allotted time after the Enhanced Mini-ACE asserted its DTREQ* output (low); or

(2) In transparent mode (includes the DMA configuration), if the processor kept STRBD* asserted (low) for longer than the allotted time after the Enhanced Mini-ACE asserted its READYD* acknowledge output low.

The effects of a handshake timeout are as follows:

- In BC, RT, or Selective Monitor modes, the processing of the current message is immediately terminated. In BC or RT modes, if the Enhanced Mini-ACE is transmitting on the 1553 bus in BC or RT modes, the transmission is terminated. The current received Data Word and any subsequent Data Words will not be stored to the Enhanced Mini-ACE shared RAM.
- In RT mode, the Enhanced Mini-ACE **will continue** to monitor received data words for error conditions (encoding, parity, etc.) after a Handshake Timeout condition has occurred. Any detected errors will be flagged in the Block Status Word, Interrupt Status Register, and RT BIT Word Register.
- In BC mode, the processing of a frame of messages is terminated and not re-started.
- In Word Monitor mode, the Enhanced Mini-ACE will not store the current "Word/ID Word" pair, but will continue to store subsequent word pairs.
- In BC, RT, or Selective Monitor modes, the EOM and ERROR FLAG bits will be set in the Block Status Word for the current message.
- If enabled, a HANDSHAKE FAILURE interrupt request will be issued, and the HANDSHAKE FAILURE bit will be set to logic "1" in the Interrupt Status register.
- In RT mode, the HANDSHAKE FAILURE bit will be set in the RT Built-In-Test (BIT) Word.
- If a Handshake Failure occurs during an RT Start-of-Message (SOM) transfer sequence, the entire message will be ignored.

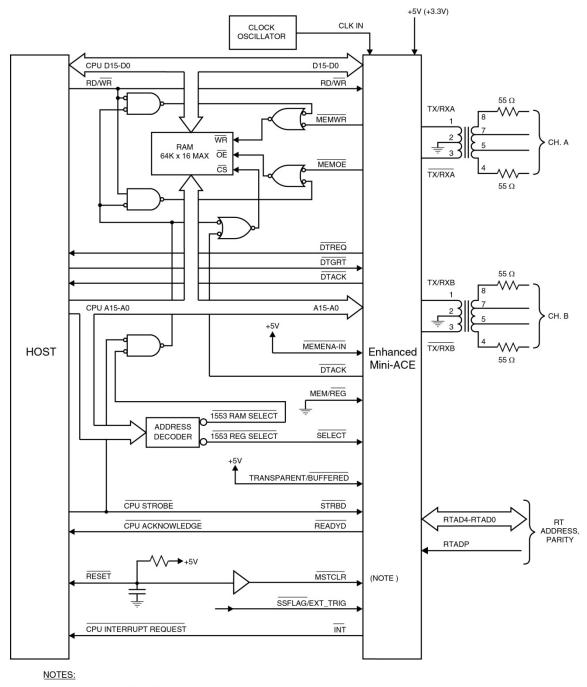
<u>Note</u>: A handshake timeout cannot occur in the buffered mode configuration.



NOTES:

THE RISE TIME FOR MSTCLR MUST BE LESS THAN 10µS IN ORDER TO ENSURE CORRECT INITIALIZATION OF THE ENHANCED MINI-ACE'S TRANSCEIVERS.

Figure 18. Interconnection Diagram for 16-Bit DMA Mode (Shown with +5V Transceiver)



THE RISE TIME FOR $\rm \overline{MSTCLR}$ MUST BE LESS THAN 10 μS IN ORDER TO ENSURE CORRECT INITIALIZATION OF THE ENHANCED MINI-ACE'S TRANSCEIVERS.

Figure 19. 16-Bit DMA with External Logic to Reduce CPU Access Time (Shown with +5V Transceiver)

9.8 8-Bit Buffered Mode

Figure 20 illustrates the 8-bit buffered mode. This interface allows a direct connection to 8-bit microprocessors and 8-bit micro controllers. As in the 16-bit buffered configuration, the buffered RAM is limited to the Enhanced Mini-ACE's internal RAM (4K words on BU-61743(5)/61843(5), and 64K words on BU-61864(5)). In the 8-bit mode, the host CPU accesses the Enhanced Mini-ACE's internal registers and RAM by means of a pair of 8-bit registers embedded in the Enhanced Mini-ACE interface.

The 8-bit interface may be further configured by means of three strappable inputs: ZERO_WAIT*, POLARITY_SEL, and TRIGGER_SEL.In the 8-bit buffered mode, the input 16/8*-BIT must be strapped to logic "0" and the CPU's data bus must be connected to both D15-D8 and D7-D0. The LSB of the processor address bus (processor A0) must be connected to the input MSB/LSB for upper/lower byte selection. The processor's A1 output connects to the Enhanced Mini-ACE's A0 input, processor A2 to Enhanced Mini-ACE A1, etc.

The programmable inputs POLARITY_SEL and TRIGGER_SEL allow the Enhanced Mini-ACE terminals to accommodate the different byte ordering conventions (big/little endian) and "A0" logic sense implemented by different 8-bit processor families. For example, a Motorola 6809 writes upper data first to the lower (usually even) address location, followed by lower data to the next highest (usually odd numbered) location. By contrast, an Intel 8088 will first write lower data to the lower (usually even numbered) address location and then write the upper byte to the next highest (usually odd numbered) address. If the POLARITY_SEL input signal is connected to logic "1" in the 8-bit nonzero wait mode, then the MSB/LSB input signal will select the most significant byte when low and the least significant byte when high.

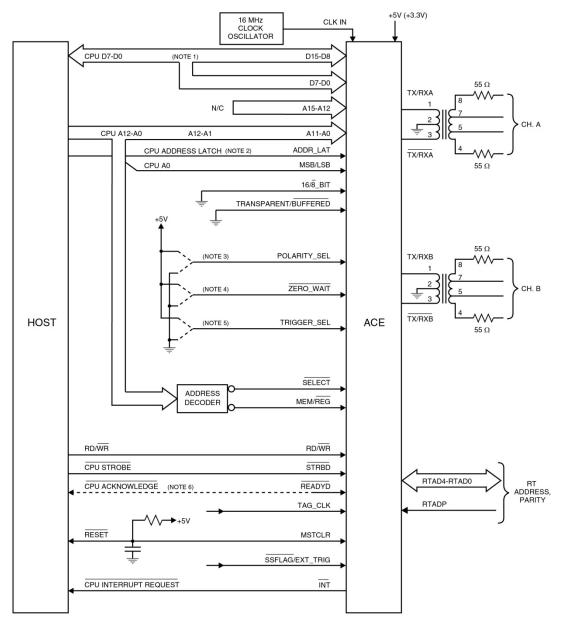
When the POLARITY_SEL input signal is connected to logic "0," the MSB/LSB input signal will select the least significant byte when low and the most significant byte when high. Therefore, a Motorola 6809 would require that the POLARITY_SEL input be connected to logic "1," while an Intel 8088 would require a logic "0" on POLARITY_SEL.The TRIGGER_SEL input will control the order in which bytes are transferred to or from the Enhanced Mini-ACE. This is important because the Enhanced Mini-ACE performs 16-bit internal transfers.

For the case of a write operation, the host processor will write 8 bits of a 16-bit word to the Enhanced Mini-ACE. The Enhanced Mini-ACE will store this byte in an internal data latch. The host processor will then present the other 8 bits of the word. At this point in time, the Enhanced Mini-ACE will "trigger" an internal 16-bit transfer, with half of the data being presented from the CPU data bus, while the other half (written during the previous CPU cycle) is presented to the Enhanced Mini-ACE's RAM or register from the internal latch.

When operating in the nonzero wait mode, a logic "0" on the TRIGGER_SEL input will configure the Enhanced Mini-ACE to trigger an internal 16-bit transfer on the least significant byte transfer for a read access, and by the most significant byte transfer for a write access. A logic "1" on the TRIGGER_SEL input will configure the Enhanced Mini-ACE to trigger an internal 16-bit transfer on the most significant byte transfer for a read access, and by the least significant byte transfer for a write access. Therefore, a 6809 interface would require that the TRIGGER_SEL input be connected to logic "1," while an 8088 interface requires a logic "0."The operation of the ACE's 8-bit nonzero wait buffered mode is essentially the same as the 16-bit mode, with the following exceptions:

For a write cycle, the first byte is written to an internal latch; the second byte is written directly to a register or RAM location. When the second byte is written to register or RAM, the first byte is simultaneously transferred from the buffer register to register or RAM. The address (A15-A0 and MEM/REG*) is "don't care" during the first byte transfer, but must be valid during the second byte transfer. The handshake output READYD* is asserted low after both byte transfers.

For a read cycle in the "nonzero wait" mode, the first byte is read directly from register or RAM. While the first byte is read by the CP, the second byte is being stored in an internal latch. The processor may then read the second byte from the buffer. The address (A15-A0 and MEM/REG*) must be valid during the first byte read, but is "don't care" during the second byte read. The handshake output READYD* is asserted low after both byte transfers.



NOTES:

- 1. CPU D7-D0 CONNECTS TO BOTH D15-D8 AND D7-D0.
- 2. CPU ADDRESS LATCH SIGNAL PROVIDED BY PROCESSORS WITH MULTIPLEXED ADDRESS/DATA BUFFERS.
- IF POLARITY_SEL = "1", THEN MSB/LSB SELECTS THE MOST SIGNIFICANT BYTE WHEN LOW, AND THE LEAST SIGNIFICANT BYTE WHEN HIGH.
- SIGNIFICANT BYTE WHEN HIGH. IF POLARITY_SEL = "0", THEN MSB/LSB SELECTS THE LEAST SIGNIFICANT BYTE WHEN LOW, AND THE MOST SIGNIFICANT BYTE WHEN HIGH.
- ZERO WAIT SHOULD BE STRAPPED TO LOGIC "1" FOR NON-ZERO WAIT INTERFACE AND TO LOGIC "0" FOR ZERO WAIT INTERFACE.
- OPERATION OF TRIGGER_SELECT INPUT IS AS FOLLOWS: FOR NON-ZERO WAIT INTERFACE (ZERO WAIT = "1"): IF TRIGGER_SEL = "1", THEN INTERNAL 16-BIT

TRANSFERS ARE TRIGGERED BY THE MOST SIGNIFICANT BYTE TRANSFER READ ACCESSES AND BY THE LEAST SIGNIFICANT BYTE TRANSFER FOR WRITE ACCESSES. IF TRIGGER_SEL = "0", THEN INTERNAL 16-BIT TRANSFERS ARE TRIGGERED BY THE LEAST SIGNIFICANT BYTE TRANSFER FOR READ ACESSES AND BY THE MOST SIGNIFICANT BYT TRANSFER FOR WRITE ACCESSES. FOR ZERO WAIT INTERFACE (ZERO WAIT = "0"): IF TRICGED SEL = "1" THEN INTERNAL 16 PIT

- IF TRIGGER_SEL = "1", THEN INTERNAL 16-BIT TRANSFERS ARE TRIGGERED BY THE LEAST SIGNIFICANT BYTE TRANSFER, FOR BOTH READ AND WRITE ACCESSES. IF TRIGGER_SEL = "0", THEN INTERNAL 16-BIT TRANSFERS ARE TRIGGERED BY THE MOST SIGNIFICANT
- BYTE TRANSFER, FOR BOTH READ AND WRITE ACCESES. 6. CPU ACKNOWLEDGE PROCESSOR INPUT ONLY FOR NON-ZERO WAIT TYPE OF INTERFACE.

Figure 20. Interconnection Diagram for 8-Bit Buffered Mode (Shown with +5V Transceivers)

21Table 2 provides a summary of the possible transfer sequences in the 8-bit nonzero wait mode.

	٦	Fable 2. S	ummary	of 8-Bit Operation (Non	zero Wait Mode)
ZERO WAIT*	TRIGGER SELECT	POLARIT YSELECT	RD/WR*	FIRST BYTE TRANSFER	SECOND BYTE TRANSFER
1	1	1	1	MSB/LSB = 0; Valid A15-A0, MEM/REG*; CPU ← RAM 15-8; Buffer 7-0 ← RAM 7-0	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care; "CPU ← Buffer 7-0
1	1	1	0	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care; "CPU→ Buffer 15-8	MSB/LSB = 1; Valid A15-A0, MEM/REG*; Buffer 15-8 \longrightarrow RAM 15-8; CPU \longrightarrow RAM 7-0
1	1	0	1	MSB/LSB = 1; Valid A15-A0, MEM/REG*; CPU	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care; "CPU ← Buffer 7-0
1	1	0	0	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care; "CPU→ Buffer 15-8	MSB/LSB = 0; Valid A15-A0, MEM/REG*; Buffer 15-8→ RAM 15-8; CPU→ RAM 7-0
1	0	1	1	MSB/LSB = 1; Valid A15-A0, MEM/REG*; CPU	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care; "CPU ← Buffer 15-8
1	0	1	0	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care; "CPU→ Buffer 7-0	MSB/LSB = 0; Valid A15-A0, MEM/REG*; Buffer 7-0 \longrightarrow RAM 7-0; CPU \longrightarrow RAM 15-8
1	0	0	1	MSB/LSB = 0; Valid A15-A0, MEM/REG*; CPU ← RAM 7-0; Buffer 15-8 ← RAM 15-8	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care; "CPU ← Buffer 15-8
1	0	0	0	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care; "CPU→ Buffer 7-0	MSB/LSB = 1; Valid A15-A0, MEM/REG*; Buffer 7-0 → RAM 7-0; CPU → RAM 15-8

9.9 8-Bit Zero Wait Mode

By connecting ZERO_WAIT* to logic "0" in the 8-bit buffered mode, the Enhanced Mini-ACE may be interfaced with minimal "glue" logic to micro controllers, such as the Intel 8051 series, that do not have an "acknowledge" type of handshake input. When performing a write transfer in the zero wait mode, the Enhanced Mini-ACE will begin the cycle in the same manner as the nonzero wait mode. The difference is that the Enhanced Mini-ACE will latch the data, address and control lines internally if the host processor terminates the transfer cycle (brings STRBD* high) before the Enhanced Mini-ACE has responded with the handshake acknowledge output (high-to-low transition of READYD*). The only constraint is that the host processor must not begin a new transfer to the Enhanced Mini-ACE until the Enhanced Mini-ACE has completed the previous internal transfer.

The operation of the READYD* output signal in the nonzero wait mode is to indicate when a transfer is complete. In the zero wait mode, however, READYD* indicates that a transfer is active. READYD* is normally high and will go low upon the start of the internal transfer, and will remain low until the internal transfer is complete. After the internal RAM or register transfer has been completed, READYD will revert to its high state.

The operation of the TRIGGER_SEL input in the 8-bit zero wait mode is similar to its operation in the 8-bit nonzero wait mode. The Enhanced Mini-ACE must be configured to trigger the internal transfer off of the proper byte transfer. A write operation is the same for both zero wait and nonzero wait, in that the Enhanced Mini-ACE will trigger the internal write when the second of two byte transfers is performed. An internal read transfer will be triggered after the host processor reads the second byte of a 2-byte read. This is in contrast to a nonzero wait read, in which the internal read is triggered on the first of a two byte access.

The write cycle for the 8-bit "zero wait" mode (ZERO_WAIT* = logic "0") is identical to that for the 8-bit "nonzero wait" mode, except for the operation of the READYD* output. In the "zero wait" mode, READYD* stays high during the entire first byte (nontriggering) transfer cycle. During the second byte transfer time (triggering transfer), READYD* stays high until STRBD* is either cleared high (after a minimum pulse width of 20 ns), or has been sampled low for two rising edges of the CLK_IN input. READYD* then goes low (indicating "not ready") and remains high until the internal 16-bit transfer of data between the ACE's internal latches and internal RAM or register has been completed.

When using the 8-bit (or 16-bit) "zero wait" mode, it is assumed there is no "acknowledge" input on the processor to connect the Enhanced Mini-ACE's READYD* output to. However, the CPU may still poll the READYD* output. **It should not initiate another transfer cycle to the ACE while READYD* is logic "0."** Alternatively, the CPU may insert software wait states between successive accesses to the Enhanced Mini-ACE. The required wait time varies with the mode of operation and frequency of the clock input. Refer to Table 3 to determine the required minimum wait time.

Table 3.	Table 3. Minimum Required Delay Times											
MODE	@ 20 MHz	@ 16 MHz	@ 12 MHz	@ 10 MHz								
Bus Controller (BC)	1.9 µs	2.4 µs	3.1 µs	3.8 µs								
Remote Terminal(RT)	3.9 µs	4.9 µs	6.4 µs	7.7 µs								
Word Monitor	900 ns	1.1 µs	1.5 µs	1.8 µs								
Selective Message Monitor	2.1 µs	2.31 µs	3.5 µs	4.2 µs								

For the read cycle for the 8-bit "zero wait" mode: It is important to realize that for a given read cycle, the internal RAM address (including the value of MEM/REG*) is the address that was presented on the Enhanced Mini-ACE's address inputs (A15-A0) during the **second** byte read of the **previous** (word) READ cycle. Therefore, in order to read a word (two bytes) in this mode, the first byte read access is a "dummy cycle" as far as the data bus (D15-8, D7-D0) is concerned; however, the address (A15-A0 and MEM/REG*) for the first word to be read must be presented at this time.

That is, in order to initiate a series of word accesses, the CPU must first perform a "second byte transfer" read access (illustrated in Table 4) with the valid address and value of MEM/REG* for the first word presented. The data read during this transfer should be ignored ("thrown away"). The CPU should then perform the "first byte" and "second byte" read cycles to acquire the data from the address (including MEM/REG*) that was previously presented. As far as the Enhanced Mini-ACE is concerned, the address presented on A15-A0 and MEM/REG* is "Don't Care" during the "first byte" transfer. On the second byte transfer, the valid address for the **next** word to be read may be presented on A15-A0 and MEM/REG*. The CPU may then read the subsequent word by performing a first byte read, followed by a second byte read, etc.

Note that the READYD* output will remain high through the end of the first "zero wait" read cycle, but will transition to logic "0" during (or possibly after) the STRBD* pulse for the second byte read cycle. During the time that READYD* is logic "0", the RAM data for the address presented is transferred from the Enhanced Mini-ACE's internal RAM or register to the two internal 8-bit latches. When READYD* is re-asserted to logic "1" (2.6 µs max later with a 16 MHz clock), the CPU may then proceed to read the first byte, then the second byte.

Table 4 summarizes the possible transfer sequences for the 8-bit zero wait mode.

	Table	4. Summ	ary of 8	-Bit Operation (Zero V	Wait Mode)
ZEROWAIT	TRIGGER SELECT	POLARITY SELECT	RD/WR	FIRST BYTE TRANSFER	SECOND BYTE TRANSFER
0	1	1	1	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care;	MSB/LSB = 1; A15-A0 and MEM/REG* Valid for Next Word;
				"CPU	CPU ←—— Buffer 7-0 (Last A15- A0, MEM/REG*);then,
					Buffer 15-0 ← RAM 15-0
0	1	1	0	MSB/LSB = 0;A15-A0, MEM/REG* = "Don't Care;	MSB/LSB = 1; Valid A15-A0, MEM/REG*;
				"CPU —→ Buffer 15-8	$CPU \longrightarrow Buffer 7-0; then,$
					Buffer —→ RAM 15-0
0	1	0	1	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care;	MSB/LSB = 0; A15-A0 and MEM/REG* Valid for Next Word;
				"CPU ← Buffer 15-8 (Last A15-A0,MEM/REG*)	CPU ← Buffer 7-0 (Last A15- A0, MEM/REG*);then,
					Buffer 15-0
0	1	0	0	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't	MSB/LSB = 0; Valid A15-A0, MEM/REG*;
				Care;	CPU —→ Buffer 7-0;then,
				"CPU —→ Buffer 15-8	Buffer —→ RAM 15-0
0	0	1	1	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't Care;	MSB/LSB = 0; A15-A0 and MEM/REG* Valid for Next Word;
				"CPU ←—— Buffer 7-0(Last A15-A0, MEM/REG*)	CPU ← Buffer 15-8 (Last A15- A0, MEM/REG*);then,
					Buffer 15-0 ← RAM 15-0
0	0	1	0	MSB/LSB = 1; A15-A0, MEM/REG* = "Don't	MSB/LSB = 0; Valid A15-A0, MEM/REG*;
				Care;	CPU —→ Buffer 15-8;then,
				"CPU —→ Buffer 7-0	Buffer —→ RAM 15-0
0	0	0	1	MSB/LSB = 0; A15-A0, MEM/REG* = "Don't Care;	MSB/LSB = 1; A15-A0 and MEM/REG* Valid for Next Word;
				"CPU ← Buffer 7-0 (Last A15-A0,MEM/REG*)	CPU ← Buffer 15-8 (Last A15- A0, MEM/REG*);then,
					Buffer 15-0 ← RAM 15-0

	Table 4. Summary of 8-Bit Operation (Zero Wait Mode)												
ZEROWAIT	TRIGGER SELECT	POLARITY SELECT	RD/WR	FIRST BYTE TRANSFER	SECOND BYTE TRANSFER								
0	0	0		A15-A0, MEM/REG* = "Don't Care:	MSB/LSB = 1; Valid A15-A0, MEM/REG*; CPU —→ Buffer 15-8;then, Buffer —→ RAM 15-0								

9.10 Control Logic

"Glue" control logic is generally required to provide conditioning between the processor's control signals and the Enhanced Mini-ACE's control signals. In many systems, this circuitry may be implemented into a programmable logic device (EPLD/FPGA). It is often possible to combine the address decoding and control logic glue functions in the same EPLD/FPGA device. One typical function of the glue logic is to formulate the Enhanced Mini-ACE's STRBD* input. This is a simple logical OR function for many processors that provides separate WRITE* and READ* strobe outputs. In addition, gating, inverting, and/or tri-state control logic is often needed between the Enhanced Mini-ACE's READYD* output and the processor's acknowledge input.

9.11 Interrupt Logic

In many cases, the interrupt request logic may be implemented in the same EPLD/FPGA with the address decoding and glue logic. The most common functions of this logic include providing tri-state or open collector INTERRUPT REQUEST outputs, clearing the request flip-flop, and providing interrupt vector responses.

9.12 Reset (MSTCLR*) Input

The Enhanced Mini-ACE may be placed in its power turn-on, or initialization state, following either a hardware or software reset. A hardware reset, which generally occurs following power turn-on, is caused by asserting the MSTCLR* input to logic "0" for at least 100ns of the Enhanced Mini-ACE's internal logic following a hardware, software, or "Reset RT" reset is summarized in Volume 1, Table 3, in the "REGISTERS" section of the User's Guide.

Note that in order to ensure the correct initialization at the Enhanced Mini-ACE's transceivers, the rise time for $\overline{\text{MSTCLR}}$ must be less than 10 µs.

9.13 Chip Select (SELECT*) Input

In all modes, a CPU transfer is initiated through the use of the input signals SELECT* and STRBD*. The Enhanced Mini-ACE will begin a CPU transfer upon sampling both SELECT* and STRBD* low on a rising clock edge. A CPU transfer, once started (as indicated by a logic 0 output on the IOEN* output signal), will remain active until the STRBD* input returns to a logic 1 state.

9.14 Bit Buffered, Nonzero Wait Mode Interface Timing

Figure 22 and Figure 23 illustrate the timing for the host processor to access the Enhanced Mini-ACE's internal RAM or registers in the 16_bit, nonzero wait buffered mode. Figure 22 illustrates the 16_bit buffered, nonzero wait state mode read cycle timing, while Figure 23 shows the 16_bit, buffered, nonzero wait state mode write cycle timing.

During a CPU transfer cycle, the signals **STRBD** and **SELECT** must be sampled low on the rising edge of the system clock to request access to the Enhanced Mini-ACE internal shared RAM. The transfer will begin on the first rising system clock edge when (**SELECT and STRBD**) is low **and** the 1553 protocol/memory management unit is not accessing the internal RAM. The start of the transfer is indicated by the falling edge of the output signal **IDEN**. The signals **MEM/REG** and **RD/WR** are latched internally on the first rising clock edge after the signal **IDEN** goes low. Note that the address lines may be latched at any time using the ADDR_LAT input signal.

The output signal \overline{READYD} will be asserted low on the third rising clock edge after \overline{IOEN} goes low for read transfers or the second rising clock edge for write transfers. The assertion of \overline{READYD} low indicates to the host processor that read data is available on the parallel data bus (D15-D0), or that write data has been stored. At this time, the CPU should bring the signal \overline{STRBD} high, completing the transfer cycle.

	Table 5. CPU Reading RAM/Registers							<u> </u>	
REF	DESCRIPTION	NOTES		/ LOGI		3.3V LOGIC			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
t1	SELECT and STRBD low setup time prior to clock rising edge	2, 9	10			15			ns
	SELECT and STRBD low to IOEN low (uncontended access @ 20 MHz)	2, 6			100			105	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	2, 6			3.6			3.6	μs
	(contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	2, 6			515			520	ns
	(uncontended access @ 16 MHz)	2, 6			112			117	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	2, 6			4.6			2.8	μs
t2	(contended access, with ENHANCED CPU ACCESS = "1" s @ 16 MHz)	2, 6			630			635	ns
	(uncontended access @ 12 MHz)	2, 6			133			138	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	2, 6			6.0			6.0	μs
	(contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	2, 6			815			820	ns
	(uncontended access @ 10 MHz)	2, 6			150			155	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	2, 6			7.2			7.2	μs
	(contended access, with ENHANCED CPU ACCESS = "1" $@$ 10 MHz)	2, 6			965			970	ns
	Time for MEM/ $\overline{\text{REG}}$ and RD/ $\overline{\text{WR}}$ to become valid following SELECT and STRBD low (@ 20 MHz)	3,4,5,7			15			10	ns
t3	@ 16 MHz	3,4,5,7			21			16	ns
	@ 12 MHz	3,4,5,7			32			27	ns
	@ 10 MHz	3,4,5,7			40			OGIC MAX 105 3.6 520 117 2.8 635 138 6.0 820 155 7.2 970 10 10	ns
	Time for Address to become valid following $\overline{\text{SELECT}}$ and $\overline{\text{STRBD}}$ low (@ 20 MHz)				17			12	ns
t4	@ 16 MHz				30			25	ns
	@ 12 MHz				50			45	ns
	@ 10 MHz				67			62	ns
t5	CLOCK IN rising edge delay to IOEN falling edge	6			40			40	ns
t6	SELECT hold time following IOEN falling	2	0			0			ns
t7	MEM/ $\overline{\text{REG}}$, RD/ $\overline{\text{WR}}$ setup time prior to CLOCK IN falling edge	3,4,5,7	10			15			ns
t8	MEM/ REG , RD/ WR hold time following CLOCK IN falling edge	3,4,5,7	30			30			ns

	Table 5. CPU Reading RAM/Registers	(16-Bit, E	Buffere	ed, No	n-Zer	o Wai	t Mod	e)	
DEE	DECODIDITION	NOTES	5\	/ LOGI	С	3.3		SIC	
REF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
t9	Address valid setup time prior to CLOCK IN rising edge	7,8	30			35			ns
t10	Address hold time following CLOCK IN rising edge	7,8,9	30			30			ns
	IOEN falling delay to READYD falling (@ 20 MHz)	6,9	135	150	165	135	150	165	ns
t11	@ 16 MHz	6,9	170	187. 5	205	170	187. 5	205	ns
	@ 12 MHz	6,9	235	250	265	235	250	265	ns
	@ 10 MHz	6,9	285	300	315	285	300	300	ns
	Output Data valid prior to READYD falling (@20 MHz)	6	21			11			ns
t12	@ 16 MHz	6	33			23			ns
112	@ 12 MHz	6	54			44			ns
	@ 10 MHz	6	71			61			ns
t13	CLOCK IN rising edge delay to READYD falling	6			40			40	ns
t14	READYD falling to STRBD rising release time				∞			×	ns
t15	STRBD rising edge delay to IOEN rising edge and READYD rising edge	6			30			40	ns
t16	Output Data hold time following STRBD rising edge		0			0			ns
t17	STRBD rising delay to output data tri-state				40			40	ns
t18	STRBD high hold time from READYD rising		0			0			ns
t19	CLOCK IN rising edge delay to output data valid				40			40	ns

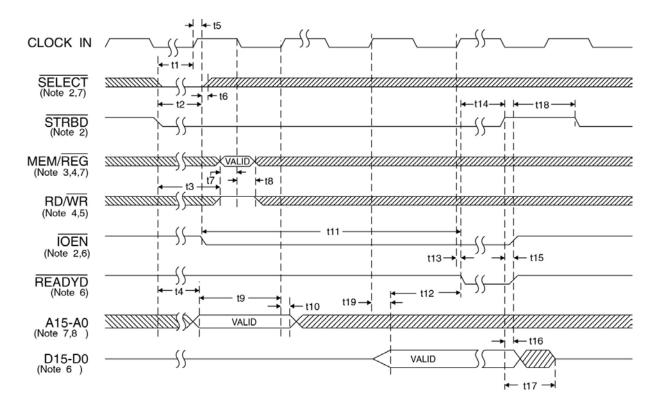


Figure 22. CPU Reading RAM/Registers (16-Bit, Buffered, Nonzero Wait)

Notes: ForTable 5 and Figure 22

- For the 16-bit buffered nonzero wait configuration, TRANSPARENT/BUFFERED must be connected to logic "0".
 ZERO_WAIT and DTREQ / 16/8 must be connected to logic "1". The inputs TRIGGER_SEL and MSB/LSB may be connected to either +5V or ground.
- 2. SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when SELECT STRBD is sampled low (satisfying t1) and the Enhanced Mini-ACE's protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. MEM/REG must be presented high for memory access, low for register access.
- 4. MEM/REG and RD/WR are buffered transparently until the first falling edge of CLK after IOEN goes low. After this CLK edge, MEM/REG and RD/WR become latched internally.
- 5. The logic sense for RD/WR in the diagram assumes that POLARITY_SEL is connected to logic "1." If POLARITY_SEL is connected to logic "0," RD/WR must be asserted low to read.
- 6. The timing for IOEN, READYD and D15-D0 assumes a 50 pf load. For loading above 50 pf, the validity of IOEN, READYD, and D15-D0 is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. The timing for A15-A0, MEM/REG and SELECT assumes that ADDR-LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- 8. The address bus A15-A0 is internally buffered transparently until the first rising edge of CLK after $\overline{\text{IOEN}}$ goes low. After this CLK edge, A15-A0 becomes latched internally.
- 9. Setup time given for use in worst case timing calculations. None of the Enhanced Mini-ACE input signals are required to be synchronized to the system clock. When SELECT and STRBD do not meet the setup time of t1, but occur during the setup window of an internal flip-flop, an additional clock cycle will be inserted between the falling clock edge that latches MEM/REG and RD/WR and the rising clock edge that latches the Address (A15-A0). When this occurs, the delay from IOEN falling to READYD falling (t11) increases by one clock cycle and the address hold time (t10) must be increased be one clock cycle.

	Table 6. CPU Writing RAM/Registers (1			/ LOGI			BV LOG		
REF	DESCRIPTION	NOTES	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
t1	SELECT and STRBD low setup time prior to clock rising edge	2, 10	10			15			ns
	SELECT and STRBD low to IOEN low (uncontended access @ 20 MHz)	2, 6			100			105	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	2, 6			3.6			3.6	μs
	(contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	2, 6			465			470	ns
	(uncontended access @ 16 MHz)	2, 6			112			117	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	2, 6			4.6			2.8	μs
t2	(contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	2, 6			565			570	ns
	(uncontended access @ 12 MHz)	2, 6			133			138	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	2, 6			6.0			6.0	μs
	(contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	2, 6			732			737	ns
	(uncontended access @ 10 MHz)	2, 6			150			155	ns
	(contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	2, 6			7.2			7.2	μs
	(contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	2, 6			865			870	ns
	Time for MEM/ $\overline{\text{REG}}$ and RD/ $\overline{\text{WR}}$ to become valid following SELECT and STRBD low (@ 20 MHz)	3,4,5,7			15			10	ns
t3	@ 16 MHz	3,4,5,7			21			16	ns
	@ 12 MHz	3,4,5,7			32			27	ns
	@ 10 MHz	3,4,5,7			40			35	ns
	Time for Address to become valid following \overline{SELECT} and \overline{STRBD} low (@ 20 MHz)				17			12	ns
t4	@ 16 MHz				30			25	ns
	@ 12 MHz				50			45	ns
	@ 10 MHz				67			62	ns
t5	Time for data to become valid following \overline{SELECT} and \overline{STRBD} low (@ 20 MHz)				37			32	ns
	@ 16 MHz				50			45	ns
	@ 12 MHz				70			65	ns
	@ 10 MHz				87			82	ns

	Table 6. CPU Writing RAM/Registers (1	6-Bit, Bı	uffered	l, Non	zero \	Nait N	/lode)		
REF	DESCRIPTION	NOTES	5\	/ LOGI	С	3.3		SIC	UNITS
REF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNIT5
t6	Clock in rising edge delay to IOEN falling edge	6			40			40	ns
t7	SELECT hold time following IOEN falling	2	0			0			ns
t8	MEM/\overline{REG} , RD/ \overline{WR} setup time prior to CLOCK IN falling edge	3,4,5,7	10			15			ns
t9	MEM/REG, RD/WR setup time following CLOCK IN falling edge	3,4,5,7	30			35			ns
t10	Address valid setup time prior to CLOCK IN rising edge	7,8	30			35			ns
t11	Data valid setup time prior to CLOCK IN rising edge		10			15			ns
t12	Address valid hold time following CLOCK IN rising edge	7,8,9	30			30			ns
t13	Data valid hold time following CLOCK IN rising edge	9	10			15			ns
	IOEN falling delay to READYD falling @ 20 MHz	6,9	85	100	115	85	100	115	ns
t14	@ 16 MHz	6,9	110	125	140	110	125	140	ns
	@ 12 MHz	6,9	152	167	182	152	167	182	ns
	@ 10 MHz	6,9	185	200	215	185	200	215	ns
t15	CLOCK IN rising edge delay to READYD falling	6			40			40	ns
t16	READYD falling to STRBD rising release time				×			×	ns
t17	STRBD rising delay to IOEN rising edge and READYD rising edge	6			30			40	ns
t18	STRBD high hold time from READYD rising		10			10			ns

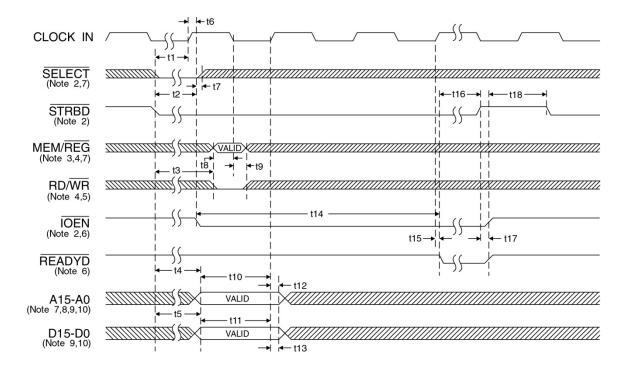


Figure 23. CPU Writing RAM/Registers (16-Bit, Buffered, Nonzero Wait)

Notes: For Table 6 and Figure 23

- 1. For the 16-bit buffered nonzero wait configuration TRANSPARENT/^{BUFFERED} must be connected to logic "0", $\overline{ZERO_WAIT}$ and \overline{DTREG} / 16/ $\overline{8}$ must be connected to logic "1". The inputs TRIGGER_SEL and MSB/LSB may be connected to either +5V or ground.
- SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when
 SELECT STRBD is sampled low (satisfying t1) and the Enhanced Mini-ACE's protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. MEM/ REG must be presented high for memory access, low for register access.
- 4. MEM/\overline{REG} and RD/\overline{WR} are buffered transparently until the first falling edge of CLK after \overline{IOEN} goes low. After this CLK edge, MEM/\overline{REG} and RD/\overline{WR} become latched internally.
- 5. The logic sense for RD/ \overline{WR} in the diagram assumes that POLARITY_SEL is connected to logic "1." If POLARITY SEL is connected to logic "0." RD/ \overline{WR} must be asserted high to write.
- 6. The timing for the IOEN and \overline{READYD} outputs assumes a 50 pf load. For loading above 50 pf, the validity of IOEN and \overline{READYD} is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. The timing for A15-A0, MEM/ REG , and SELECT assumes that ADDR-LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- 9. The address bus A15-A0 and data bus D15-D0 are internally buffered transparently until the first rising edge of CLK after IOEN goes low. After this CLK edge, A15-A0 and D15-D0 become latched internally.

Setup time given for use in worst case timing calculations. None of the Enhanced Mini-ACE input signals are required to be synchronized to the system clock. When SELECT and STRBD do not meet the setup time of t1, but occur during

be synchronized to the system clock. When SELECT and STREE do not meet the setup time of t1, but occur during the setup time of an internal flip-flop, an additional clock cycle may be inserted between the falling clock edge that latches MEM/ $\overline{\text{REG}}$ and RD/ $\overline{\text{WR}}$ and the rising clock edge that latches the address (A15-A0) and data (D15-D0).

When this occurs, the delay from $\overline{\text{IOEN}}$ falling to $\overline{\text{READYD}}$ falling (t14) increases by one clock cycle and the address and data hold time (t12 and t13) must be increased by one clock.

	Table 7. CPU Reading RAM/Registers (16-B	it, Buffe	ered,	, Zer	o Wa	ait Mo	ode)		
			5	/ Log	jic	3.3	3V Lo	gic	
REF	DESCRIPTION	NOTES	MIN	TYP	MAX	MIN	ΤΥΡ	MAX	UNITS
t1	SELECT and STRBD low setup time prior to CLOCK IN rising	10	10			15			ns
t2	SELECT and STRBD low minimum pulse width		20			20			ns
t3	SELECT and STRBD low delay to Data valid	14			35			30	ns
t4	RD/ \overline{WR} setup time prior to \overline{SELECT} and \overline{STRBD} low		10			10			ns
t5	RD/ ^{WR} high delay to Data valid	14			35			30	ns
t6A	Address setup time prior to STRBD rising	11	10			10			ns
t6B	Address setup time prior to CLOCK IN rising	12	10			10			ns
t7A	MEM/REG setup time prior to STRBD rising	11	10			10			ns
t7B	MEM/REG setup time prior to CLOCK IN rising	12	10			10			ns
t8A	SELECT low hold time following STRBD rising	11	0			0			ns
t8B	SELECT low hold time following CLOCK IN rising	12	25			25			ns
t9A,B	STRBD rising setup time prior to CLOCK IN rising	10	15			20			ns
t10A	MEM/ REG and RD/WR* hold time following STRBD rising	11	20			20			ns
t10B	MEM/ REG and RD/WR* hold time following CLOCK IN rising	12	25			25			ns
t11A	STRBD rising delay to READYD low	11			30			30	ns
t11B	CLOCK IN rising delay to READYD low	12			35			30	ns
t12A	Address hold time following STRBD rising	11	20			20			ns
t12B	Address hold time following CLOCK IN rising	12	25			25			ns
t13	Output Data hold time following STRBD rising		0			0			ns
t14	STRBD rising delay to Data tri-state				35			30	ns
	STRBD rising delay to start of next transfer (uncontended access @20 MHz)	13	320			320			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	13	3.9			3.9			us
t15	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	13	650			650			ns
115	STRBD rising delay to start of next transfer (uncontended access @16 MHz)	13	395			395			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	13	4.9			4.9			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	13	800			800			ns

			51	/ Log	ic	2 3	3V Lo	aic	
REF	DESCRIPTION	NOTES					-	MAX	UNITS
	STRBD rising delay to start of next transfer (uncontended access @12 MHz)	13	520			520			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	13	6.5			6.5			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	13	1050			1050			ns
	STRBD rising delay to start of next transfer (uncontended access @10 MHz)	13	620			620			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	13	7.8			7.8			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	13	1250			1250			ns
	STRBD rising delay to IOEN falling (uncontended access @20 MHz)				105			105	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)				3.6			3.6	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)				350			350	ns
	STRBD rising delay to IOEN falling (uncontended access @16 MHz)				130			130	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)				4.5			4.5	us
+4.0	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)				438			438	ns
t16	STRBD rising delay to IOEN falling (uncontended access @12 MHz)				172			172	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)				6.0			6.0	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)				583			583	ns
	STRBD rising delay to IOEN falling (uncontended access @10 MHz)				205			205	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)				7.2			7.2	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)				700			700	ns
t17	CLOCK IN rising to IOEN low	2			40			30	ns
	IOEN low pulse width for RAM read (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for REGISTER read (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for RAM read (@16 MHz)		235	250	265	235	250	265	ns
	IOEN low pulse width for REGISTER read (@16 MHz)		235	250	265	235	250	265	ns
t18	IOEN low pulse width for RAM read (@12 MHz)		315	333	350	315	333	350	ns
	IOEN low pulse width for REGISTER read (@12 MHz)		315	333	350	315	333	350	ns
	IOEN low pulse width for RAM read (@10 MHz)		385	400	415	385	400	415	ns
	IOEN low pulse width for REGISTER read (@10 MHz)		385	400	415	385	400	415	ns
t19	CLOCK IN rising delay to IOEN rising				35			30	ns

Table 7. CPU Reading RAM/Registers (16-Bit, Buffered, Zero Wait Mode)											
REF	DESCRIPTION	NOTES	5V Logic			3.3	UNITS				
REF		NOTES	MIN	ΤΥΡ	MAX	MIN	TYP	MAX			
t20	CLOCK IN falling delay to READYD rising				35			30	ns		
t21	READYD high delay to start of next transfer (STRBD falling)		0			0			ns		

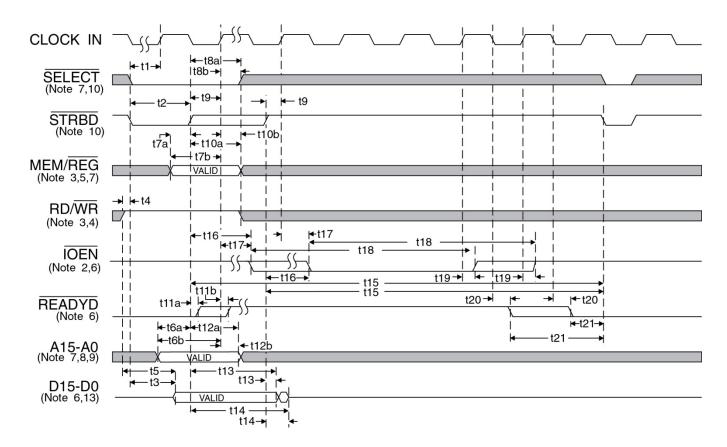


Figure 24. CPU Reading RAM/Registers (16-Bit, Buffered, Zero Wait)

Notes for Table 7 and Figure 24

- For the 16-bit buffered configuration, the inputs TRIGGER_SEL and MSB/LSB may be connected to +5V or GND.
 For the zero wait interface, ZERO_WAIT must be connected to logic "0."
- 2. IOEN goes low on the first rising CLK edge when READYD is low and STRBD is sampled high (satisfying t9 setup time) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, OEN goes low, starting the internal transfer.
- 3. MEM/ $\overline{\text{REG}}$ and RD/ $\overline{\text{WR}}$ are buffered transparently until latched by $\overline{\text{STRBD}}$ rising or second rising clock edge.
- 4. The logic sense for RD/WR in the diagram assumes that POLARITY_SEL is connected to logic "1." If POLARITY_SEL is connected to logic "0," RD/WR must be asserted low to read.
- 5. Data output is ready from register/RAM address referenced by the value of MEM/REG and A15-A0 from the previous read cycle.
- 6. The timing for ^{IOEN}, READYD and D15-D0 assumes a 50 pf load. For loading above 50 pf, the validity of ^{IOEN}, READYD, and D15-D0 is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, and SELECT assumes ADDR-LAT is connected to logic "1." Refer to Address Latch timing for additional details. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 9. The address bus A15-A0 is internally buffered transparently until latched by ^{STRBD} rising or second rising clock edge. To implement a single zero wait read operation, the host processor must perform two read accesses to the Enhanced Mini-ACE. During the first access, the address and transfer type indication (memory or register) of the

location to be read must be asserted on A15-A0 and MEM/^{REG}, respectively. The data read on D15-D0 during this cycle should be ignored ("thrown away"). During the second read access, the Enhanced Mini-ACE presents the data corresponding to the address presented on the first access on D15-D0. If the CPU performs a multi-word read burst, the address for the next word should be presented on A15-A0 on the same cycle that data is read from D15-D0. That is, for a multi-word read transfer, the address presented should always be one location ahead of that of the data being read.

- 10. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock. Removal of SELECT prior to being latched on the second rising clock edge will have the same effect as STRBD rising. For Enhanced Mini-ACE applications, transfer will not start until SELECT and STRBD are both low. SELECT must go low prior to the second rising clock edge after STRBD goes low or transfer will be blocked.
- 11. For the case in which ^{STRBD} goes high before second rising clock edge in which ^{SELECT} is low and ^{STRBD} is low.
- 12. For the case in which STRBD is low and SELECT is low for a minimum of two rising clock edges for the Enhanced Mini-ACE.
- 13. After STRBD is brought high and READYD asserted low, STRBD MUST be kept low until READYD returns high.
- 14. Valid data will be present on D15-D0 only after SELECT, STRBD and RD/WR propagation delays (t3 and t5) are met.

	Table 8. CPU Writing RAM/Registers (16-E		1	/ LOG		3.3	GIC	
REF	DESCRIPTION	NOTES	MIN		MAX		r	UNITS
t1	SELECT and STRBD low setup time prior to CLOCK IN rising	10	10			15		ns
t2	SELECT and STRBD low minimum pulse width		20			20		ns
t3	RD/WR setup time prior to SELECT and STRBD low		10			10		ns
t4A	Address setup time prior to STRBD rising	12	10			10		ns
t4B	Address setup time prior to CLOCK IN rising	13	10			10		ns
t5A	Data setup time prior to STRBD rising	12	10			15		ns
t5B	Data setup time prior to CLOCK IN rising	13	10			10		ns
t6A	MEM/REG setup time prior to STRBD rising	12	10			10		ns
t6B	MEM/REG setup time prior to CLOCK IN rising	13	10			10		ns
t7A	SELECT low hold time following STRBD rising	12	0			0		ns
t7B	SELECT low hold time following CLOCK IN rising	13	25			25		ns
t8	STRBD rising setup time prior to CLOCK IN rising	10	15			20		ns
t9A	MEM/ REG and RD/ WR hold time following STRBD rising	12	20			20		ns
t9B	MEM/ REG and RD/ WR hold time following CLOCK IN rising	13	25			25		ns
t10A	STRBD rising delay to READYD low	12			30		30	ns
t10B	CLOCK IN rising delay to READYD low	13			35		30	ns
t11A	Address hold time following STRBD rising	12	20			20		ns
t11B	Address hold time following CLOCK IN rising	13	25			25		ns
t12A	Input Data hold time following STRBD rising	12	20			20		ns
t12B	Input Data hold time following CLOCK IN rising	13	25			25		ns
	STRBD rising delay to IOEN falling (uncontended access @20 MHz)				105		105	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)				3.6		3.6	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)				350		350	ns
t13	STRBD rising delay to IOEN falling (uncontended access @16 MHz)				130		130	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)				4.5		4.5	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)				438		438	ns
	STRBD rising delay to IOEN falling (uncontended access @12 MHz)				172		172	ns

	DECODUCTION	NOTES	5\	/ LOG	IC	3.3		GIC	
REF	DESCRIPTION	NOTES	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)				6.0			6.0	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)				583			583	ns
	STRBD rising delay to IOEN falling (uncontended access @10 MHz)				205			205	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)				7.2			7.2	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)				700			700	ns
	STRBD rising delay to start of next transfer (uncontended access @20 MHz)	14	320			320			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	14	3.9			3.9			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	14	650			650			ns
	STRBD rising delay to start of next transfer (uncontended access @16 MHz)	14	395			395			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	14	4.9			4.9			us
t14	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	14	800			800			ns
	STRBD rising delay to start of next transfer (uncontended access @12 MHz)	14	520			520			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	14	6.5			6.5			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	14	1050			1050			ns
	STRBD rising delay to start of next transfer (uncontended access @10 MHz)	14	620			620			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	14	7.8			7.8			us
t15	CLOCK IN rising to IOEN low	2			40			30	ns
	IOEN low pulse width for RAM read (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for REGISTER read (@20 MHz)		185	200	215	185	200	215	ns
t16	IOEN low pulse width for RAM read (@16 MHz)		235	250	265	235	250	265	ns
	IOEN low pulse width for REGISTER read (@16 MHz)		235	250	265	235	250	265	ns
	IOEN low pulse width for RAM read (@12 MHz)		315	333	350	315	333	350	ns

	Table 8. CPU Writing RAM/Registers (16-Bit, Buffered, Zero Wait Mode)												
REF	DESCRIPTION	NOTES	5\	/ LOG	IC	3.3	UNITS						
NEF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ΤΥΡ	MAX					
	IOEN low pulse width for REGISTER read (@12 MHz)		315	333	350	315	333	350	ns				
	IOEN low pulse width for RAM read (@10 MHz)		385	400	415	385	400	415	ns				
	IOEN low pulse width for REGISTER read (@10 MHz)		385	400	415	385	400	415	ns				
t17	CLOCK IN rising delay to IOEN rising				35			30	ns				
t18	CLOCK IN falling delay to READYD rising				35			30	ns				
t19	READYD high delay to start of next transfer (STRBD falling)		0			0			ns				

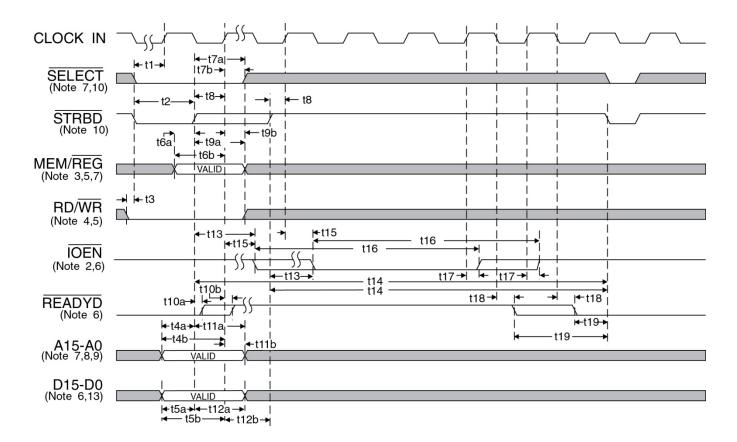


Figure 25. CPU Writing RAM/Registers (16-Bit, Buffered, Zero Wait)

Notes for Table 8 and Figure 25

- 1. For the 16-bit buffered configuration, the inputs TRIGGER_SEL and MSB/LSB may be connected to +5V or GND. For the zero wait interface, ZERO_WAIT must be connected to logic "0."
- 2. IOEN goes low on the first rising CLK edge when READYD is low and STRBD is sampled high (satisfying t9 setup time) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the internal transfer.
- 3. MEM/ REG must be presented high for memory access, low for register access.
- 4. MEM/REG and RD/WR are buffered transparently until latched by STRBD rising or second CLK edge. The logic sense for RD/ WR in the diagram assumes that POLARITY_SEL is connected to logic "1." If POLARITY_SEL is connected to logic "0," RD/WR must be asserted high to write. The timing for IOEN and READYD outputs assumes a 50 pf load. For loading above 50 pf, the validity of IOEN and READYD is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, and SELECT assumes ADDR-LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 9. The address bus A15-A0 is internally buffered transparently until latched by STRBD rising or second rising clock edge. The data bus starts to track when SELECT and STRBD are low until STRBD rises or second rising clock edge. To implement a single zero wait read operation, the host processor must perform two read accesses to the Enhanced Mini-ACE. During the first access, the address and transfer type indication (memory or register) of the location to be read must be asserted on A15-A0 and MEM/REG, respectively. The data read on D15-D0 during this cycle should be ignored ("thrown away"). During the second read access, the Enhanced Mini-ACE presents the data corresponding to the address presented on the first access on D15-D0. If the CPU performs a multi-word read burst, the address for the next word should be presented on A15-A0 on the same cycle that data is read from D15-D0. That is, for a multi-word read transfer, the address presented should always be one location ahead of that of the data being read.
- 10. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock. Removal of SELECT prior to being latched on the second rising clock edge will have the same effect as STRBD* rising. For Enhanced Mini-ACE applications, transfer will not start until SELECT and STRBD are both low. SELECT must go low prior to the second rising clock edge after STRBD goes low or transfer will be blocked.
- 11. Data Bus will be actively driven when SELECT is low, STRBD is low and RD/WR is high. To prevent a bus crash between the host driving the Data Bus and the Enhanced Mini-ACE driving the Data Bus, RD/WR must be setup prior to SELECT low and STRBD low.
- 12. For the case in which STRBD goes high before second rising clock edge in which SELECT is low and STRBD is low. For case in which STRBD is low and SELECT is low for a minimum of two rising clock edges.
- 14. After STRBD is brought high and READYD asserted low, STRBD MUST be kept low until READYD returns high.

	Table 9. CPU Reading RAM/Re	gisters	(Tra	nspar	ent M	ode)	105 105 3.6 117 4.6 138 6.0 155 7.2 40 7.2 40 200 215 200 215 250 265		
REF	DESCRIPTION		5\	/ Logic	;		3.3	/ Logic	;
	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
t1	SELECT and STRBD low setup time prior to CLOCK IN rising	1	10			15			ns
	SELECT and STRBD low delay to IOEN low (uncontended access @20 MHz)				100			105	ns
	SELECT and STRBD low delay to IOEN Iow (Contended access @ 20 MHz) Other Iow delay to IOEN				3.6			3.6	us
	SELECT and STRBD low delay to IOEN low (uncontended access @16 MHz)				112			117	ns
t2	SELECT and STRBD low delay to IOEN low (Contended access @ 16 MHz)				4.6			4.6	us
.2	SELECT and STRBD low delay to IOEN low (uncontended access @12 MHz)				133			138	ns
	SELECT and STRBD low delay to IOEN low (Contended access @ 12 MHz)				6.0			6.0	us
	SELECT and STRBD low delay to IOEN low (uncontended access @10 MHz)				150			155	ns
	SELECT and STRBD low delay to IOEN low (Contended access @ 10 MHz)				7.2			7.2	us
t3	CLOCK IN rising edge delay to IOEN falling				40			40	ns
t4	SELECT low hold time following IOEN falling		0			0			ns
t5	MEM/ \overline{REG} and RD/ \overline{WR} setup time prior to CLOCK IN falling		10			15			ns
t6	MEM/ $\overline{\text{REG}}$ and RD/ $\overline{\text{WR}}$ hold time following CLOCK IN falling		30			30			ns
	IOEN falling delay to READYD falling reading INT. RAM (@20 MHz)		185	200	215	185	200	215	ns
	IOEN falling delay to READYD falling reading REG. or EXT. RAM (@20 MHz)		185	200	215	185	200	215	ns
+7	IOEN falling delay to READYD falling reading INT. RAM (@16 MHz)		235	250	265	235	250	265	ns
t7	IOEN falling delay to READYD falling reading REG. or EXT. RAM (@16 MHz)		235	250	265	235	250	265	ns
	IOEN falling delay to READYD falling reading INT. RAM (@12 MHz)		315	333	350	315	333	350	ns
	IOEN falling delay to READYD falling reading REG. or EXT. RAM (@12 MHz)		315	333	350	315	333	350	ns

	Table 9. CPU Reading RAM/Re	gisters	(Tra	nspar	ent Mo	ode)			
DEE	DESCRIPTION		5\	/ Logic	;		3.3	/ Logic	;
REF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
	IOEN falling delay to READYD falling reading INT. RAM (@10 MHz)		385	400	415	385	400	415	ns
	IOEN falling delay to READYD falling reading REG. or EXT. RAM (@10 MHz)		385	400	415	385	400	415	ns
t8	CLOCK IN rising delay to DTACK low				40			40	ns
t9	MEMENA_IN setup time prior to CLOCK IN rising		10			10			ns
t10	MEMENA_IN hold time following CLOCK IN rising		30			30			ns
t11	CLOCK IN rising delay to MEMOE falling				40			40	ns
t12	Address setup time prior to CLOCK IN rising		30			35			ns
t13	Address hold time following CLOCK IN rising		30			30			ns
t14	CLOCK IN rising to Output Data valid				40			40	ns
t15	CLOCK IN rising delay to READYD falling				40			40	ns
	STRBD release time following READYD falling (Internal RAM @20 MHz)				4.2			4.2	us
	STRBD release time following READYD falling (External RAM @20 MHz)				4.2			4.2	us
	STRBD release time following READYD falling (Internal RAM @16 MHz)				3.6			3.6	us
110	STRBD release time following READYD falling (External RAM @16 MHz)				3.6			3.6	us
t16	STRBD release time following READYD falling (Internal RAM @12 MHz)				3.0			3.0	us
	STRBD release time following READYD falling (External RAM @12 MHz)				3.0			3.0	us
	STRBD release time following READYD falling (Internal RAM @10 MHz)				2.7			2.7	us
	STRBD release time following READYD falling (External RAM @10 MHz)				2.7			2.7	us
t17	STRBD rising dly to IOEN rising, READYD rising, DTACK rising, MEMOE rising rising Image: State				30			40	ns
t18	Output Data hold time following STRBD rising		0			0			ns
t19	STRBD rising delay to Output Data tri-state				40			40	ns

	Table 9. CPU Reading RAM/Registers (Transparent Mode)											
REF DESCRIPTION 5V Logic	5V Logic 3.3V Logi											
NOTES MIN TYP MAX MIN	TYP	MAX U	JNITS									
t20 READYD rising delay to STRBD falling (delay to start of next 0 0			ns									

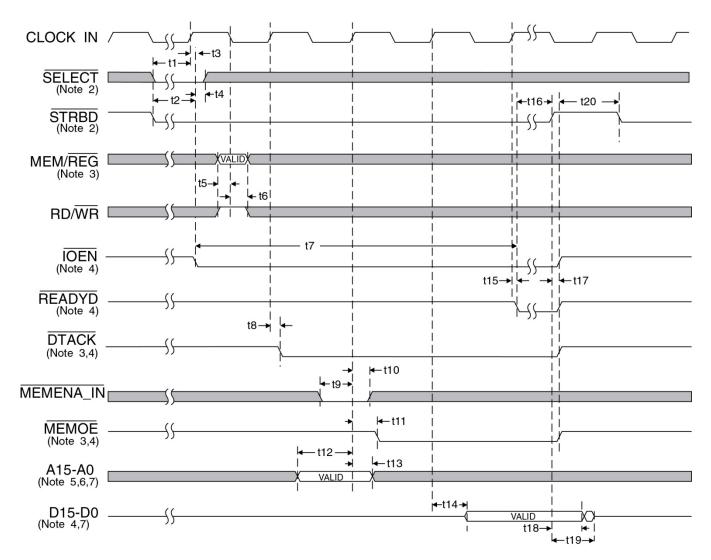


Figure 26. CPU Reading RAM/Registers (Transparent Mode)

Notes for Table 9 and Figure 26

- 1. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock.
- 2. SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when SELECT and STRBD are sampled low (satisfying t1) and the Enhanced Mini-ACE protocol/memory management logic is not actively performing a DMA transfer (i.e., DTACK is logic 1). When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. The timing diagram illustrates the CPU reading RAM. For register reads from the Enhanced Mini-ACE (MEM/REG input = logic 0) the DTACK and MEMOE output signals are not asserted, and therefore maintain a logic "1" level.
- 4. The timing for IOEN, READYD, DTACK, MEMOE, and D15-D0 assumes a 50 pf load. For loading above 50 pf, the validity of IOEN, READYD, DTACK, MEMOE, and D15-D0 is delayed by an additional 0.14 ns/pf typical, 0.28 ns/pf max.
- 5. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 6. The address bus A15-A0 is internally buffered transparently until the second rising edge of CLOCK_IN after IOEN goes low. After this CLOCK_IN edge, A15-A0 become latched internally.
- 7. For read operations from external memory, the address (A15-A0) must be held longer to meet the hold time requirements of the external memory used. The data bus (D15-D0) will remain in tri-state. D15-D0 will only be driven by the external RAM. All data bus timing will now be dependent on the external RAM used.

	Table 10. CPU Writing RAM/Registers (T	ranspa	rent	Mo	de)				
DEE	DESCRIPTION	Nataa	5١	/ Log	gic	3.3	SV Lo	gic	
REF	DESCRIPTION	Notes	MIN	ТҮР	MAX	MIN	TYP	MAX	UNITS
t1	SELECT and STRBD low setup time prior to CLOCK IN rising	1	10			15			ns
	SELECT and STRBD low delay to IOEN low (uncontended access, @ 20 MHz)				100			105	ns
	SELECT and STRBD low delay to IOEN low (Contended access, @ 20 MHz)				3.6			3.6	us
	SELECT and STRBD low delay to IOEN low (Uncontended access, @ 16 MHz)				112			117	ns
	SELECT and STRBD low delay to IOEN low (Contended access,@ 16 MHz)				4.6			4.6	us
t2	SELECT and STRBD low delay to IOEN low (Uncontended access, @12 MHz)				133			138	ns
	SELECT and STRBD low delay to IOEN low (Contended access, @ 12 MHz)				6.0			6.0	us
	SELECT and STRBD low delay to IOEN low (Uncontended access, @ 10 MHz)				150			155	ns
	SELECT and STRBD low delay to IOEN low (Contended access, @ 10 MHz)				7.2			7.2	us
t3	CLOCK IN rising edge delay to IOEN falling				40			40	ns
t4	SELECT low hold time following IOEN falling		0			0			ns
t5	MEM/ REG and RD/ WR setup time prior to CLOCK IN falling		10			15			ns
	MEM/ REG and RD/ WR hold time following CLOCK IN falling		30			30			ns
	IOEN falling delay to READYD falling (@ 20 MHz)		185	200	215	185	200	215	ns
	IOEN falling delay to READYD falling (@ 16 MHz)		235	250	265	235	250	265	ns
t7	IOEN falling delay to READYD falling (@ 12 MHz)		315	333	350	315	333	350	ns
	IOEN falling delay to READYD falling (@ 10 MHz)		385	400	415	385	400	415	ns
t8	CLOCK IN rising delay to DTACK low				35			30	ns
t9	MEMENA_IN setup time prior to CLOCK IN rising		5			10			ns
t10	MEMENA_IN hold time following CLOCK IN rising		30			25			ns
t11	CLOCK IN rising delay to MEMWR falling				40			30	ns
t12	Address setup time prior to CLOCK IN rising		30			10			ns
t13	Address hold time following CLOCK IN rising		30			25			ns
t14	Input Data setup time prior to CLOCK IN rising		10			10			ns
t15	Input Data hold time following CLOCK IN rising		30			25			ns
	MEMWR low pulse width (@20 MHz)		37		62	37		62	ns
	MEMWR low pulse width (@16 MHz)		50		75	50		75	ns
t16	MEMWR low pulse width (@12 MHz)		70		95	70		95	ns
	MEMWR low pulse width (@10 MHz)		87		112	87		112	ns

Table 10. CPU Writing RAM/Registers (Transparent Mode)											
REF	DESCRIPTION	Notes	5V Logic			3.3V Logic					
NEF	DESCRIPTION	NOLES	MIN	ТҮР	MAX	MIN	ТҮР	МАХ			
t17	CLOCK IN rising delay to MEMWR rising				30			30	ns		
t18	CLOCK IN rising delay to READYD falling				35			30	ns		
	STRBD release time following READYD falling (@20 MHz)				4.2			4.2	us		
t19	STRBD release time following READYD falling (@16 MHz)				3.6			3.6	us		
119	STRBD release time following READYD falling (@12 MHz)				3.0			3.0	us		
	STRBD release time following READYD falling (@10 MHz)				2.7			2.7	us		
t20	STRBD rising delay to IOEN rising, READYD rising, and DTACK rising				30			35	ns		
t21	READYD rising delay to STRBD falling (delay to start of next transfer cycle)		0			0			ns		

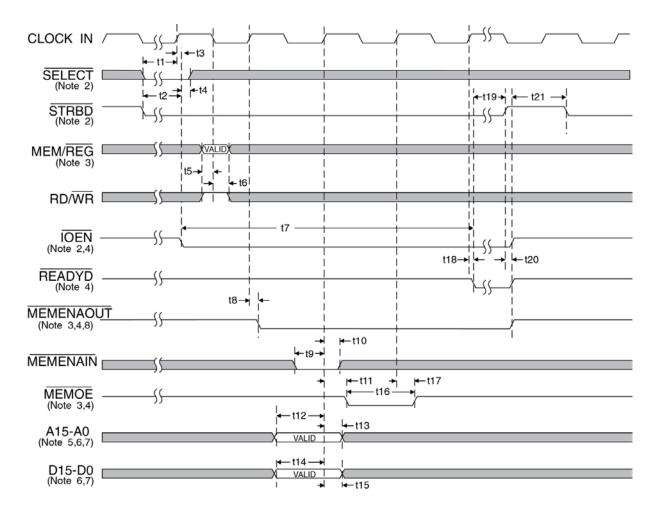


Figure 27. CPU Writing RAM/Registers (Transparent Mode)

Notes for Table 10 and Figure 27

- 1. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock.
- 2. SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when SELECT and STRBD is sampled low (satisfying t1) and the Enhanced Mini-ACE protocol/memory management logic is not active performing a DMA transfer (i.e., DTACK is logic 1). When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. The timing diagram illustrates the CPU writing to RAM. For register writes, the Enhanced Mini-ACE (MEM/ $\overline{\text{REG}}$ input = logic 0) the $\overline{\text{DTACK}}$ and $\overline{\text{MEMWR}}$ output signals are not asserted, and therefore maintain a logic "1" level.
- 4. The timing for IOEN, READYD, DTACK, and MEMWR assumes a 50 pf load. For loading above 50 pf, the validity of IOEN, READYD, DTACK, and MEMWR is delayed by an additional 0.14 ns/pf typical, 0.28 ns/pf max.
- 5. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 6. The address bus A15-A0 and data bus D15-D0 are internally buffered transparently until the second rising edge of CLOCK_IN after IOEN goes low. After this CLOCK_IN edge, A15-A0 and D15-D0 become latched internally.
- 7. For write operation to external memory, the address (A15-A0) and data (D15-D0) must be held longer to meet the hold time requirements of the external memory used.

	Table 11. CPU Reading RAM/Reg		1	V LOG		1	.3V LO		
REF	DESCRIPTION	NOTES			-			r	UNITS
			MIN	TYP	MAX	MIN	ТҮР	MAX	
t1	SELECT and STRBD low setup time prior to clock rising edge	2, 12	10			15			ns
	SELECT and STRBD low to IOEN low (uncontended access @ 20 MHz)	2, 6			100			105	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	2, 6			2.2			2.2	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	2, 6			350			355	ns
	(Uncontended access @ 16 MHz)	2, 6			112			117	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	2, 6			2.8			2.8	μs
t2	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	2, 6			425			430	ns
	(Uncontended access @ 12 MHz)	2, 6			133			138	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	2, 6			3.7			3.7	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	2, 6			550			555	ns
	(Uncontended access @ 10 MHz)	2, 6			150			155	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	2, 6			4.4			4.4	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	2, 6			650			655	ns
t3	Address valid setup time prior to CLOCK IN rising edge		30			35			ns
t4	SELECT hold time following IOEN falling	2	0			0			ns
t5	MEM/REG, RD/WR, MSB/LSB setup time prior to CLOCK IN falling edge	3,4,5,10 ,11	10			15			ns
t6	MEM/REG, RD/WR, MSB/LSB hold time following CLOCK IN falling edge	3,4,5,10 ,11	30			30			ns
t7	Address hold time following CLOCK IN rising edge	9	30			30			ns
	IOEN falling delay to READYD falling (@ 20 MHz)	6	185	200	215	185	200	215	ns
t8	@ 16 MHz	6	235	250	265	235	250	265	ns
ιο	@ 12 MHz	6	318	333	348	318	333	348	ns
	@ 10 MHz	6	385	400	415	385	400	415	ns
	Output Data valid prior to READYD falling (@20 MHz)	6,10,11	22			12			ns
t9	@ 16 MHz	6,10,11	33			23			ns
13	@ 12 MHz	6,10,11	54			44			ns
	@ 10 MHz	6,10,11	72			62			ns

	Table 11. CPU Reading RAM/Reg	gisters (8	B-Bit N	onZe	ro Wa	it Mo	de)		
REF	DESCRIPTION	NOTES	5	V LOG	IC	3	.3V LOO	SIC	
REF	DESCRIPTION	NOTES	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
t10	CLOCK IN rising edge delay to READYD falling	6			40			40	ns
t11	READYD falling to STRBD rising release time	6			8			×	ns
t12	STRBD rising edge delay to IOEN rising edge and READYD rising edge	6			30			40	ns
t13	Output Data hold time following STRBD rising edge		0			0			ns
t14	STRBD rising delay to output data tri-state				40			40	ns
t15	STRBD high hold time from READYD rising		0			0			ns
t16	CLOCK IN rising edge delay to IOEN falling edge				40			40	ns
t17	CLOCK IN rising edge delay to output data valid				40			40	ns

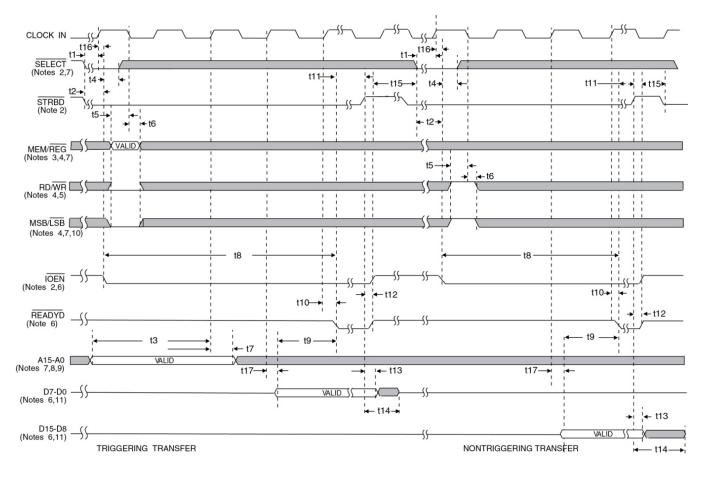


Figure 28. CPU Reading RAM/Registers (8-Bit, Nonzero Wait)

Notes for Table 11 and Figure 24

- 1. For 8-bit nonzero wait interface, TRANSPARENT/BUFFERED and 16/8/DTREQ must be connected to logic "0". must be connected to logic "1".
- 2. SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when SELECT and STRBD are both sampled low (satisfying t₁) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. MEM/REG must be presented high for memory access, low for register access. MEM/REG is a "don't care" for non-triggering transfers.
- 4. MEM/REG, MSB/LSB and RD/WR are buffered transparently until the first falling edge of CLK after IOEN goes low. After CLK edge, MEM/REG, MSB/LSB and RD/WR become latched internally.
- 5. RD/WR must be presented high for read accesses and low for write accesses. The logic sense for RD/WR does not depend the state of the POL_SEL input in the 8-bit mode.
- 6. The timing for IOEN, READYD and D15-D0 assumes a 50 pf load. For loading above 50 pf, the validity of IOEN, READYD, and D15-D0 is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, SELECT and MSB/LSB assumes ADDR_LAT is connected to logic "1." Refer to Address timing for additional details.
- 8. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 9. The address bus A15-A0 is internally buffered transparently until the first rising edge of CLK after IOEN goes low. After this CLK edge, A15-A0 become latched internally.
- 10. The polarity of the MSB/LSB input signal assumes that the POL_SEL input signal is connected to logic "0." If POL_SEL is connected to logic "1," MSB/LSB will be high for LSB transfers and low for MSB transfers.
- 11. The order of the consecutive byte transfers assumes that the TRIG_SEL input signal is connected to logic "0." The actual transfer from the internal RAM or Register takes place during the "triggering transfer" (LSB in this case). If TRIG_SEL is connected to logic "1," the order of the byte transfers would be MSB followed by LSB and the triggering transfer would be the MSB.
- 12. Setup time given for use in worst case timing calculations. None of the Enhanced Mini-ACE input signals are required to be synchronized to the system clock.

	Table 12. CPU Writing RAM/Reg	jisters (8-	Bit, No	onZer	o Wai	t Mod	e)		
REF	DESCRIPTION	NOTES	5\	/ LOGI	C	3.3		SIC	UNITS
REF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	
t1	SELECT and STRBD low setup time prior to clock rising edge	2, 12	10			15			ns
	SELECT and STRBD low to IOEN low (uncontended access @ 20 MHz)	2, 6			100			105	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	2, 6			3.6			3.6	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	2, 6			350			355	ns
	(Uncontended access @ 16 MHz)	2, 6			112			117	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	2, 6			4.6			4.6	μs
t2	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	2, 6			425			430	ns
	(Uncontended access @ 12 MHz)	2, 6			133			138	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	2, 6			6.0			6.0	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	2, 6			550			555	ns
	(Uncontended access @ 10 MHz)	2, 6			150			155	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	2, 6			7.2			7.2	μs
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	2, 6			650			655	ns
t3	Address valid setup time prior to CLOCK IN rising edge	7,8	30			35			ns
t4	SELECT hold time following IOEN falling	2	0			0			ns
t5	MEM/ $\overline{\text{REG}}$, RD/ $\overline{\text{WR}}$, MSB/LSB setup time prior to CLOCK IN falling edge	3,4,5,10,11	10			15			ns
t6	MEM/ $\overline{\text{REG}}$, RD/ $\overline{\text{WR}}$, MSB/LSB setup time following CLOCK IN falling edge	3,4,5,10,11	30			30			ns
t7	Address and Data valid hold time following CLOCK IN rising edge	9	30			30			ns
	IOEN falling delay to READYD falling @ 20 MHz	6	135	150	165	135	150	165	ns
t8	@ 16 MHz	6	172.5	187.5	202.5	172.5	187.5	202.5	ns
.0	@ 12 MHz	6	235	250	265	235	250	265	ns
	@ 10 MHz	6	285	300	315	285	300	315	ns
t9	CLOCK IN rising edge delay to READYD falling				40			40	ns

	Table 12. CPU Writing RAM/Registers (8-Bit, NonZero Wait Mode)									
REF	DESCRIPTION	NOTES	5V LOGIC			3.3		SIC	UNITS	
REF	DESCRIPTION	NOTES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS	
t10	READYD falling to STRBD rising release time				8			8	ns	
t11	STRBD rising edge delay to IOEN rising edge and READYD rising edge				30			40	ns	
t12	STRBD high hold time from READYD rising		10			10			ns	
t13	Input Data valid setup time prior to CLOCK IN rising edge		10			15			ns	
t14	Clock in rising edge delay to IOEN falling edge				40			40	ns	

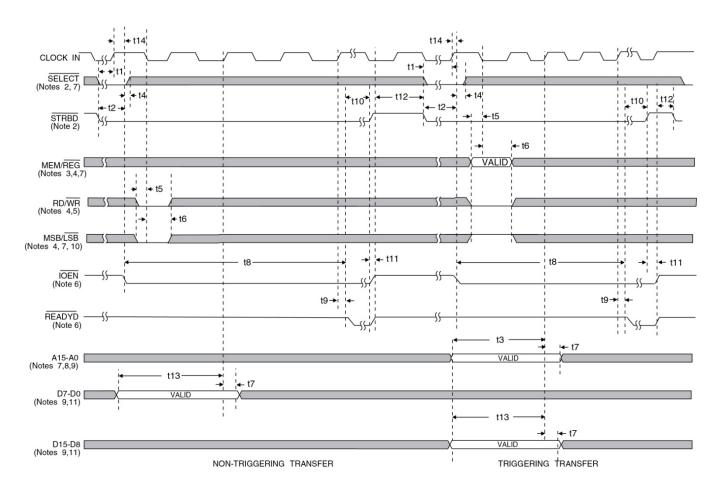


Figure 29. CPU Writing RAM/Registers (8-Bit, Nonzero Wait)

Notes for Table 12 and Figure 29

- 1. For 8-bit nonzero wait interface, TRANSPARENT/BUFFERED and 16/8/DTREQ must be connected to logic "0." ZEROWAIT must be connected to logic "1."
- 2. SELECT and STRBD may be tied together. IOEN goes low on the first rising CLK edge when SELECT and STRBD are both sampled low (satisfying t₂) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the transfer cycle. After IOEN goes low, SELECT may be released high.
- 3. MEM/REG must be presented high for memory access, low for register access. MEM/REG is a "don't care" for non-triggering transfers.
- 4. MEM/REG, MSB/LSB, and RD/WR are buffered transparently until the first falling edge of CLK after IOEN goes low. After this CLK edge, MEM/REG, MSB/LSB, and RD/WR become latched internally.
- 5. RD/WR must be presented high for read accesses and low for write accesses. The logic sense for RD/WR does not depend on the state of the POL_SEL input in the 8-bit mode.
- 6. The timing for \overline{IOEN} and \overline{READY} outputs assumes a 50 pf load. For loading above 50 pf, the validity of \overline{IOEN} and \overline{READY} is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, SELECT and MSB/LSB assumes ADDR_LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- 8. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 9. The address bus A15-A0 and data bus D15-D0 are internally buffered transparently until the first rising edge of CLK after IOEN goes low. After this CLK edge, A15-A0 and D15-D0 become latched internally.
- 10. The polarity of the MSB/LSB input signal assumes that the POL_SEL input signal is connected to logic "0." If POL_SEL is connected to logic "1," MSB/LSB will be high for LSB transfers and low for MSB transfers.
- 11. The order of the consecutive byte transfers assumes that the TRIG_SEL input signal is connected to logic "0." The actual transfer to the internal RAM or Register takes place during the "triggering transfer" (MSB in this case). If TRIG_SEL is connected to logic "1," the order of the byte transfers would be MSB followed by LSB and the triggering transfer would LSB.
- 12. Setup time given for use in worst case timing calculations. None of the Enhanced Mini-ACE input signals are required to synchronized to the system clock.

	Table 13. CPU Reading RAM/Registers	(8-Bit	, Zero	o Wa	it Mo	de)			
DEE	DESCRIPTION	Notoo	5	V Log	ic	3.3	V Lo	gic	
REF	DESCRIPTION	Notes	MIN	ТҮР	MAX	MIN	ТҮР	MAX	UNITS
t1	RD/\overline{WR} and MSB/\overline{LSB} setup time prior to \overline{STRBD} and \overline{SELECT} falling	11	10			15			ns
t2	SELECT and STRBD low setup time prior to CLOCK IN rising	10	10			15			ns
t3	SELECT and STRBD low minimum pulse width		20			25			ns
t4	SELECT and STRBD low delay to Data valid	14			35			40	ns
t5	RD/ WR and MSB/LSB delay to Data valid	14			45			50	ns
t6A	MEM/REG setup time prior to STRBD rising	11	10			10			ns
t6B	MEM/REG setup time prior to CLOCK IN rising	12	10			10			ns
t7A	MEM/ REG , RD/ WR , MSB/ LSB hold time following STRBD rising	11	20			20			ns
t7B	MEM/ $\overline{\text{REG}}$, RD/ $\overline{\text{WR}}$, MSB/ $\overline{\text{LSB}}$ hold time following CLOCK IN rising	12	25			25			ns
t8A	Address setup time prior to STRBD rising	11	10			10			ns
t8B	Address setup time prior to CLOCK IN rising	12	10			10			ns
t9A	Address hold time following STRBD rising	11	20			20			ns
t9B	Address hold time following CLOCK IN rising	12	30			30			ns
t10	Output Data hold time following STRBD rising		0			0			ns
t11	STRBD rising delay to Data tri-state				35			40	ns
	STRBD rising delay to IOEN low (uncontended access @20 MHz)				107			112	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)				3.6			3.6	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)				357			362	ns
	STRBD rising delay to IOEN low (uncontended access @16 MHz)				120			125	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)				4.6			4.6	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)				432			437	ns
t12	STRBD rising delay to IOEN low (uncontended access @12 MHz)				140			145	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)				6.0			6.0	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)				557			562	ns
	STRBD rising delay to IOEN low (uncontended access @10 MHz)				157			162	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)				7.2			7.2	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)				657			662	ns
t13A	STRBD rising delay to READYD low	11			30			30	ns
t13B	CLOCK IN rising delay to READYD low	12			35			35	ns

	Table 13. CPU Reading RAM/Registers	(8-Bit	, Zero	o Wa	it Mo	de)			
	DESCRIPTION	Nataa	5	V Log	ic	3.3V Logic			
REF	DESCRIPTION	Notes	MIN	ТҮР	MAX	MIN	ΤΥΡ	MAX	UNITS
t14	CLOCK IN rising to IOEN low				40			40	ns
t15A	SELECT low hold time following STRBD rising	11	0			0			ns
t15B	SELECT low hold time following CLOCK IN rising	12	25			25			ns
t16	STRBD rising setup time prior to CLOCK IN rising	10	15			15			ns
	IOEN low pulse width for RAM read (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for REGISTER read (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for RAM read (@16 MHz)		235	250	265	235	250	265	ns
	IOEN low pulse width for REGISTER read (@16 MHz)		235	250	265	235	250	265	ns
t17	IOEN low pulse width for RAM read (@12 MHz)		315	333	350	315	333	350	ns
	 IOEN low pulse width for REGISTER read (@12 MHz)		315	333	350	315	333	350	ns
	IOEN low pulse width for RAM read (@10 MHz)		385	400	415	385	400	415	ns
	IOEN low pulse width for REGISTER read (@10 MHz)		385	400	415	385	400	415	ns
	STRBD rising delay to start of next transfer (uncontended access @20 MHz)	13	320			325			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	13	2.5			2.5			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	13	920			925			ns
	STRBD rising delay to start of next transfer (uncontended access @16 MHz)	13	395			400			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	13	3.1			3.1			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	13	1.15			1.15			us
t18	STRBD rising delay to start of next transfer (uncontended access @12 MHz)	13	520			525			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	13	4.1			4.1			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	13	1.52			1.52			us
	STRBD rising delay to start of next transfer (uncontended access @10 MHz)	13	620			625			ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	13	4.9			4.9			us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	13	1.82			1.82			us
t19	CLOCK IN rising delay to IOEN rising				35			35	ns
t20	CLOCK IN falling delay to STRBD rising				35			35	ns
t21	STRBD rising delay to start of next transfer (SELECT and STRBD low)		20			20			ns

	Table 13. CPU Reading RAM/Registers (8-Bit, Zero Wait Mode)									
DEE	DESCRIPTION	Notes	5\	V Log	/ Logic 3.3V Logic					
REF		Notes	MIN	TYP	MAX	MIN	ТҮР	MAX	UNITS	
	trigger									
t22	READYD high to STRBD and SELECT low (Next transfer)		0			0			ns	

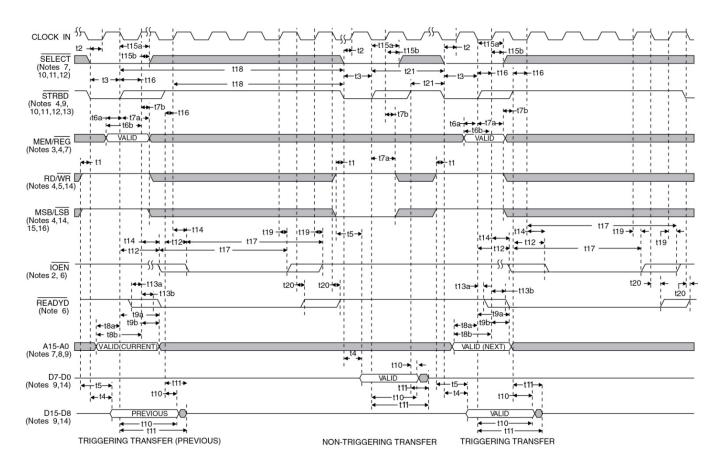


Figure 30. CPU Reading RAM/Registers (8-Bit, Zero Wait)

Notes for Table 13 and Figure 30

- 1. For 8-bit nonzero wait interface, TRANSPARENT/BUFFERED, ZEROWAIT and 16/8/DTREQ must be connected to logic "0."
- 2. IOEN goes low on the first rising CLK edge when READYD is high and STRBD is sampled high (satisfying t16 setup time) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, IOEN goes low, starting the internal transfer.
- 3. MEM/REG must be presented high for memory access, low for register access.
- 4. MEM/REG, MSB/LSB, and RD/WR are buffered transparently until latched by STRBD rising or second rising CLK edge.
- 5. RD/WR must be presented high for read accesses and low for write accesses. The logic sense for RD/WR does not depend on the state of the POL_SEL input in the 8-bit mode.

- 6. The timing for IOEN and READYD outputs assumes a 50 pf load. For loading above 50 pf, the validity of IOEN and READYD is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, MSB/LSB, and SELECT assumes ADDR_LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- 8. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions). Registers are accessed by A4 through A0.
- 9. The address bus A15-A0 and data bus D15-D0 are internally buffered transparently until latched by STRBD rising or second CLK edge.
- 10. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock. Removal of SELECT prior to being latched on the second rising clock edge will have the same effect as STRBD rising. For Enhanced Mini-ACE applications, transfer will not start until SELECT and STRBD are both low. SELECT must go low prior to the second rising clock edge after STRBD* goes low or transfer will be blocked.
- 11. For the case in which STRBD goes high before the second rising clock edge in which SELECT is low and STRBD is low.
- 12. For the case in which STRBD is low and SELECT is low for a minimum of two rising clock edges.
- 13. For 8-Bit Zero Wait triggering transfers. After STRBD is brought high and READYD asserted low, STRBD MUST be kept low until READYD returns high.
- 14. Valid data will be present on the data bus only after SELECT, STRBD, MSB/LSB and RD/WR propagation delays (t3-t5) are met.
- 15. The polarity of the MSB/LSB input signal assumes that the POL_SEL input signal is connected to logic "0." If POL_SEL is connected to logic "1." MSB/LSB will be high for LSB transfers and low for MSB transfers.
- 16. The order of the consecutive byte transfers assumes that the TRIG_SEL input signal is connected to logic "0." The actual transfer to the internal RAM or Register takes place during the "triggering transfer" (MSB in this case). If TRIG_SEL is connected to logic "1," the order of the byte transfers would be MSB followed by LSB and the triggering transfer would be the LSB.

	Table 14. CPU Writing RAM/Registers	6 (8-Bit	, Zer	o Wa	it Mo	de)			
REF	DESCRIPTION	Notes	5	V Log	ic	3.3	3V Log	gic	UNITS
NEF	DESCRIPTION	NOLES	MIN	ТҮР	MAX	MIN	ТҮР	MAX	
t1	RD/\overline{WR} setup prior to \overline{SELECT} low and \overline{STRBD} low	11	10			10			ns
t2	SELECT and STRBD low setup time prior to CLOCK IN rising	10	10			15			ns
t3	SELECT and STRBD low minimum pulse width		20			25			ns
t4A	MSB/LSB setup prior to STRBD rising	12	20			20			ns
t4B	MSB/LSB setup prior to CLOCK IN rising	14	20			20			ns
t5A	MSB/LSB, RD/WR hold timing following STRBD rising	12	20			20			ns
t5B	MSB/ \overline{LSB} , RD/ \overline{WR} hold time following CLOCK IN rising	14	25			25			ns
t6A	Input Data setup prior to STRBD rising	12	10			10			ns
t6B	Input Data setup prior to CLOCK IN rising	14	10			10			ns
t7A	Input Data hold time following STRBD rising	12	20			20			ns
t7B	Input Data hold time following CLOCK IN rising	14	25			25			ns
t8A	SELECT low hold time following STRBD rising	12	0			0			ns
t8B	SELECT low hold time following CLOCK IN rising	14	25			25			ns
t9	STRBD rising delay to start of next transfer (SELECT low and STRBD low)		20			20			ns
t10	MSB/LSB high setup prior to SELECT low and STRBD low	17	10			10			ns
t11A	MEM/ REG setup prior to STRBD rising	12	10			10			ns
t11B	MEM/ REG setup prior to CLOCK IN rising	14	10			10			ns
t12A	MEM/\overline{REG} , RD/ \overline{WR} , MSB/ \overline{LSB} hold time following \overline{STRBD} rising	12	20			20			ns
t12B	MEM/ $\overline{\text{REG}}$, RD/ $\overline{\text{WR}}$, MSB/ $\overline{\text{LSB}}$ hold time following CLOCK IN rising	14	25			25			ns
t13A	Address setup prior to STRBD rising	12	10			10			ns
t13B	Address setup prior to CLOCK IN rising	14	10			10			ns
t14A	Address hold time following STRBD rising	12	20			20			ns
t14B	Address hold time following CLOCK IN rising	14	30			30			ns
	STRBD rising delay to IOEN falling (uncontended access @20 MHz)	13			107			112	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 20 MHz)	13			3.6			3.6	us
t15	(Contended access, with ENHANCED CPU ACCESS = "1" @ 20 MHz)	13			357			362	ns
	STRBD rising delay to IOEN falling (uncontended access @16 MHz)	13			120			125	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 16 MHz)	13			4.6			4.6	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 16 MHz)	13			432			437	ns

	Table 14. CPU Writing RAM/Registers (8-Bit, Zero Wait Mode)								
REF	DESCRIPTION	Notes	5V Logic			3.3	3V Log	gic	
REF	DESCRIPTION	Notes	MIN	TYP	MAX	MIN	TYP	MAX	
	STRBD rising delay to IOEN falling (uncontended access @12 MHz)	13			140			145	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 12 MHz)	13			6.0			6.0	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 12 MHz)	13			557			562	ns
	STRBD rising delay to IOEN falling (uncontended access @10 MHz)	13			157			162	ns
	(Contended access, with ENHANCED CPU ACCESS = "0" @ 10 MHz)	13			7.2			7.2	us
	(Contended access, with ENHANCED CPU ACCESS = "1" @ 10 MHz)	13			657			662	ns
t16A	STRBD rising delay to READYD falling				30			30	ns
t16B	CLOCK IN rising delay to READYD falling				35			35	ns
t17	CLOCK IN rising delay to IOEN falling				40			40	ns
t18	STRBD high setup prior to CLOCK IN rising		15			15			ns
	IOEN low pulse width for RAM write (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for REGISTER write (@20 MHz)		185	200	215	185	200	215	ns
	IOEN low pulse width for RAM write (@16 MHz)		235	250	265	235	250	265	ns
t19	IOEN low pulse width for REGISTER write (@16 MHz)		235	250	265	235	250	265	ns
119	IOEN low pulse width for RAM write (@12 MHz)		315	333	350	315	333	350	ns
	IOEN low pulse width for REGISTER write (@12 MHz)		315	333	350	315	333	350	ns
	IOEN low pulse width for RAM write (@10 MHz)		385	400	415	385	400	415	ns
	IOEN low pulse width for REGISTER write (@10 MHz)		385	400	415	385	400	415	ns
t20	CLOCK IN rising delay to IOEN rising				35			35	ns
t21	CLOCK IN falling delay to READYD rising				35			35	ns
t22	READYD high to STRBD and SELECT low (Next transfer)		0			0			ns

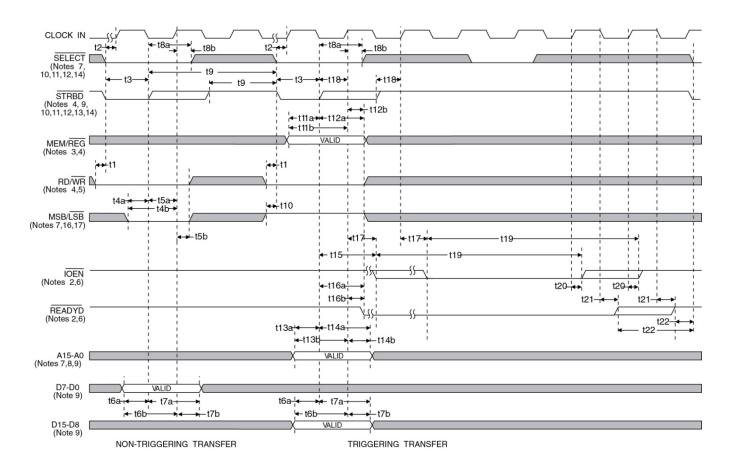


Figure 31. CPU Writing RAM/Registers (8-Bit, Zero Wait)

Notes for Table 14 and Figure 31

- 1. For 8-bit zero wait interface, TRANSPARENT/BUFFERED, ZEROWAIT and 16/8/DTREQ must be connected to logic "0."
- 2. IOEN goes low on the first rising CLK edge when READYD is high and STRBD is sampled high (satisfying t18 setup time) and the Enhanced Mini-ACE protocol/memory management logic is not accessing the internal RAM. When this occurs, OEN goes low, starting the internal transfer.
- 3. MEM/^{REG} must be presented high for memory access, low for register access.
- 4. MEM/^{REG}, MSB/^{LSB}, and RD/^{WR} are buffered transparently until latched by ^{STRBD} rising or second rising CLK edge.
- 5. RD/WR must be presented high for read accesses and low for write accesses. The logic sense for RD/WR does not depend on the state of the POL_SEL input in the 8-bit mode.
- 6. The timing for ^{IOEN} and READYD outputs assumes a 50 pf load. For loading above 50 pf, the validity of ^{IOEN} and READYD is delayed by an additional 0.14 ns/pf typ, 0.28 ns/pf max.
- 7. Timing for A15-A0, MEM/REG, MSB/LSB and SELECT assumes ADDR_LAT is connected to logic "1." Refer to Address Latch timing for additional details.
- 8. Internal RAM is accessed by A15 through A0 (64K RAM Versions) or A11 through A0 (4K RAM Versions).Registers are accessed by A4 through A0.
- 9. The address A15-A0 and data D15-D0 are internally buffered transparently until latched by STRBD rising or the second rising clock edge.

- 10. Setup time given for use in worst case timing calculations. These signals do not have to be synchronized to the system clock. Removal of SELECT effect as STRBD are both low. SELECT must go low prior to the second clock rising edge after STRBD goes low or transfer will be blocked.
- 11. Data Bus will be actively driven when SELECT is low, STRBD is low and RD/WR is high. To prevent a bus crash between the host driving the Data Bus and the Enhanced Mini-ACE driving the Data Bus, RD/WR must be setup prior to SELECT low and STRBD low.
- 12. For the case in which STRBD goes high before second rising clock edge in which SELECT is low and STRBD is low.
- 13. For 8-Bit Zero Wait triggering transfers. After STRBD is brought high and READYD asserted low, STRBD MUST be kept low until READYD returns high.
- 14. For the case in which STRBD is low and SELECT is low for a minimum of two rising clock edges.
- 15. IOEN will be asserted low following the first rising clock edge in which STRBD is high and the internal data bus is available.
- 16. The polarity of the MSB/^{LSB} input signal assumes that the POL_SEL input signal is connected to logic "0." If POL_SEL is connected to logic "1," MSB/^{LSB} will be high for LSB transfers and low for MSB transfers.
- 17. MSB/LSB must be setup prior to SELECT low and STRBD low to prevent an accidental write to the internal non-triggering byte data latch.
- 18. The order of the consecutive byte transfers assumes that the TRIG_SEL input signal is connected to logic "0." The actual transfer to internal RAM or register takes place during the "triggering transfer" (MSB in this case). If TRIG_SEL is connected to logic "1," the order of the byte transfers would be MSB followed by LSB and the triggering transfer would be the LSB.

9.15 Address Latch Timing

Figure 32 and Table 15 illustrate the operation and timing of the address input latches for the buffered interface mode. In the transparent mode, the address buffers, and $\overline{\text{SELECT}}$, MEM/REG inputs are always transparent (MSB/LSB not applicable). Since the transparent mode requires the use of external buffers, external address latches would be required to demultiplex a multiplexed address bus. In the buffered mode however, the Enhanced Mini-ACE's internal address latches is controlled by means of the ADDR_LAT input. When ADDR_LAT is high, the latch outputs, which drive the Enhanced Mini-ACE's internal memory and control bus, transparently track the state of the address inputs A15 through A00, and the input signals $\overline{\text{SELECT}}$, MSB/LSB, and MEM/REG. When ADDR_LAT is low, the internal memory and control bus remain latched at the state of A15-A00, $\overline{\text{SELECT}}$, MSB/LSB, and MEM/REG just prior to the falling edge of ADDR_LAT.

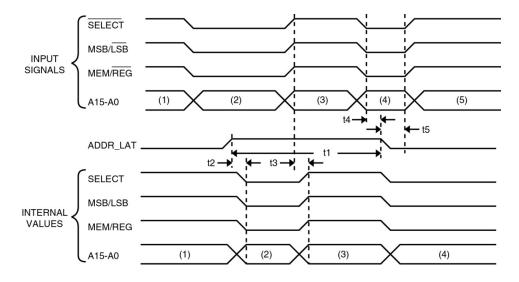
	Table 15. Address Latch Timing									
REF	DESCRIPTION		hanc ni-AC	· -	UNITS					
		MIN	ТҮР	МАХ						
t1	ADDR_LAT pulse width	20			ns					
t2	ADDR_LAT high delay to internal signals valid			10	ns					
	Propagation delay from external input signals to internal signals valid			10	ns					
t4	Input setup time prior to falling edge of ADDR_LAT	10			ns					
t5	Input hold time following falling edge of ADDR_LAT	20			ns					

Table 15 Notes:

1. Applicable to buffered mode only. Address, <u>SELECT</u>, and MEM/<u>REG</u> latches are always transparent in the transparent mode of operation.

2. Latches are transparent when ADDR_LAT is high. Internal values do not update when ADDR_LAT is low.

3. MSB/\overline{LSB} input signal is applicable to 8-bit mode only (16/8 input = logic "0"). MSB/\overline{LSB} input is a "don't care" for 16-bit operation.





9.16 Clock Input Considerations

9.16.1 Input Frequency

The Enhanced Mini-ACE may be operated from a 10MHz, 12MHz, 16MHz, or 20MHz clock input. In the default (power turn-on) state, the Enhanced Mini-ACE assumes a 16MHz clock input. As shown in Volume 1, Table 61 the frequency of CLOCK_IN input may be specified by writing to Configuration Registers 5 and 6. In addition, for 4K RAM versions of Enhanced Mini-ACE. The clock frequency may also be

designated by means of the UPADDREN, A15/CLK_SEL_2, and A14/CLK_SEL_0 input signals.

For compliance to the transmission rate accuracy spec of MIL-STD-1553B. The short term (1 second) frequency accuracy must be within \pm 0.01%, with a long term accuracy of \pm 0.1%. To comply to MIL-STD-1553A, the short term (1 second) accuracy must be to within \pm 0.001%, with a long-term accuracy of \pm 0.01%.

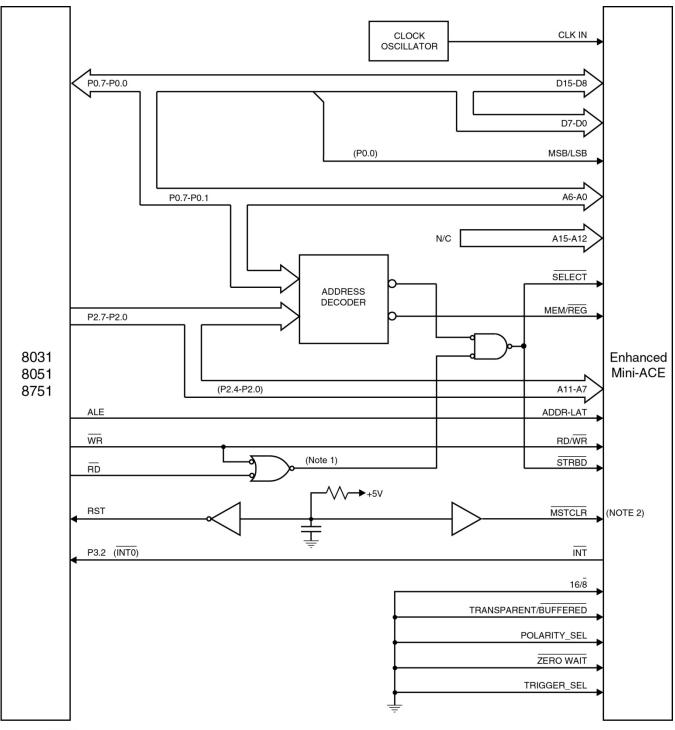
9.16.2 Double EdgeD MANCHESTER DECODER Sampling

The Enhanced Mini-ACE Manchester decoders operate by oversampling the digital input signal from the 1553 double-ended receivers on **every** edge (both rising and falling) of CLOCK_IN. To ensure reliable operation of the Manchester decoder, the duty cycle of the CLOCK_IN input signal must be in the range of 40% to 60%.

9.17 Sample Interfaces

9.17.1 INTEL 8051

Figure 33 illustrates a simplified interface drawing between an Intel 8051 and an Enhanced Mini-ACE. This interface is based on the Enhanced Mini-ACE's 8-bit buffered, zero wait interface. The 4K words (8K bytes) of Enhanced Mini-ACE internal RAM, map to Address range (Base Memory Address) (0000-1FFF). The 16 register locations (32 bytes) of the BU-65170/61580 map to address range (Base Register Address) (0000-001F), where BRA = Base Register Address. SELECT must be asserted low to access either RAM or register. MEM/REG must be asserted high to access RAM, low to access registers.



NOTE:

1. Select a gate such that the RD/WR setup time prior to SELECT and STRBD low is satisfied.

2. The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 33. Intel 8051-to-Enhanced Mini-ACE Interface

Write accesses are performed as follows:

- 1. Write lower data byte, with P0.0 (MSB/ $\overline{\text{LSB}}$) = 0.
- Write upper data byte, with P0.0 (MSB/LSB) = 1.
 If additional write cycles are to be performed, wait the minimum time, then return to step 1. The minimum times are listed in Volume 1, TABLE 94.

Read accesses are performed as follows:

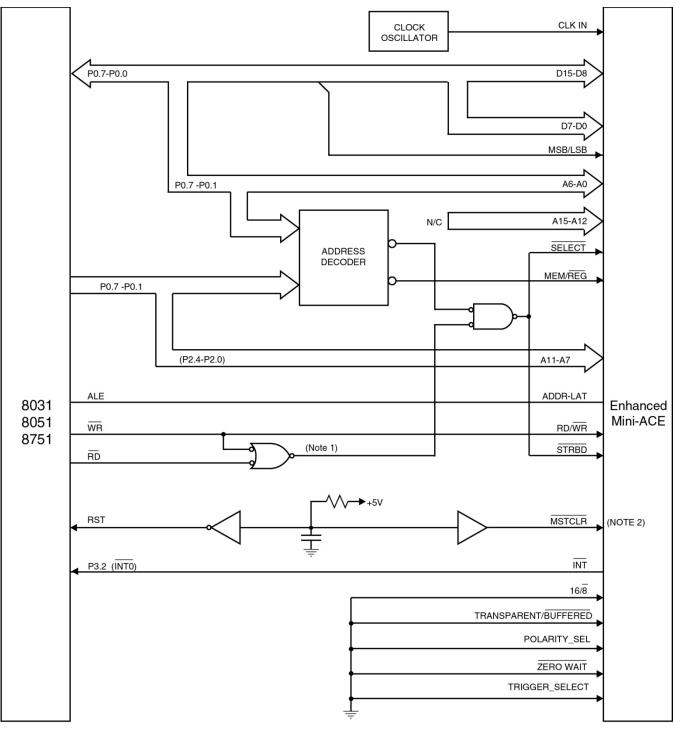
- 1. Perform a "dummy" read access to the upper data byte address (P0.0 (MSB/LSB) = 1). Do not use the data byte accessed from this operation.
- 2. After waiting the minimum time (see Volume 1, TABLE 94), read the lower data byte, with P0.0 (MSB/ \overline{LSB}) = 0.
- While presenting the Address for the next word to be accessed (if any), read the upper byte, with P0.0 (MSB/LSB) = 1.

If there is a subsequent word to be read, repeat steps 2 and 3.

Table 16. Minim	linimum Required Delay Times										
	Enhanced Mini-ACE										
MODE	@20MHz	@16MHz	@12MHz	@10MHz							
Bus Controller (BC)	1.9 µs	2.4 µs	3.1 µs	3.8 µs							
Remote Terminal (RT)	3.9 µs	4.9 µs	6.4 µs	7.7 µs							
Word Monitor	0.9 µs	1.1 µs	1.5 µs	1.8 µs							
Selective Message Monitor	2.1 µs	2.6 µs	3.5 µs	4.2 µs							

9.17.2 ADSP-2101

Figure 34 illustrates a simplified interface drawing between an Analog Devices ADSP-2101 and an Enhanced Mini-ACE. This interface takes advantage of the Enhanced Mini-ACE's 16-bit zero wait mode since the 2101 does not have an acknowledge handshake input. A restriction of the zero wait mode is that the processor may not begin a new transfer until the previous is complete. Therefore, the READYD output may optionally be read by the processor on the LSB of the data bus as a method of polling the Enhanced Mini-ACE to determine when the transfer is complete.



NOTE:

1. Select a gate such that the RD/WR* setup time prior to SELECT* and STRBD* low is satisfied.

2. The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 34. ADSP-2101-to- ACE Interface



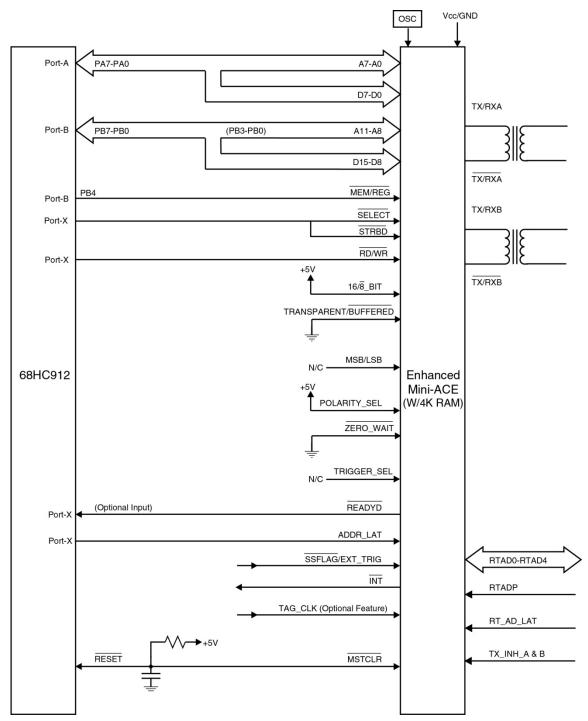
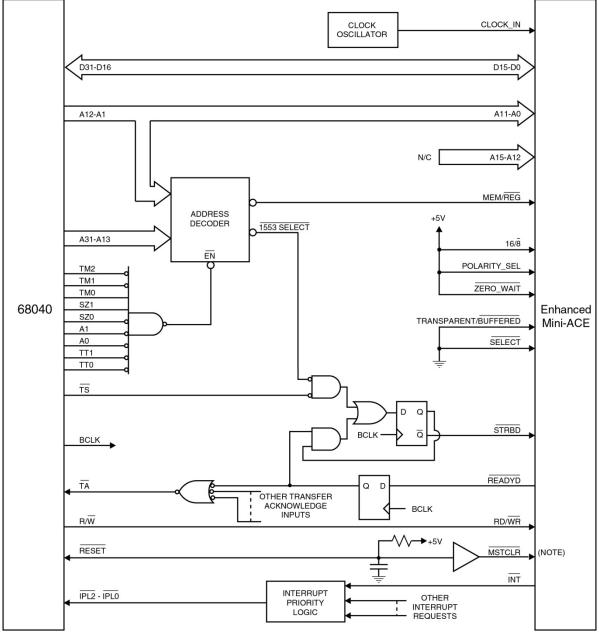


Figure 35. Motorola 68HC912-to-Enhanced Mini-ACE Interface

9.17.4 MOTOROLA 68040

Figure 36 illustrates a simplified interface drawing between a 68040 and an Enhanced Mini-ACE.



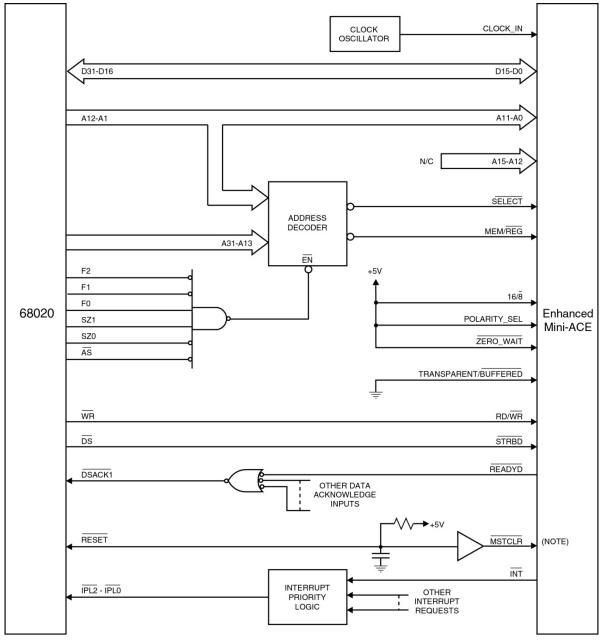
NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 36. Motorola 68040-to-Enhanced Mini-ACE Interface

9.17.5 MOTOROLA 68020

Figure 37 illustrates a simplified interface drawing between a 68020 and an Enhanced Mini-ACE.

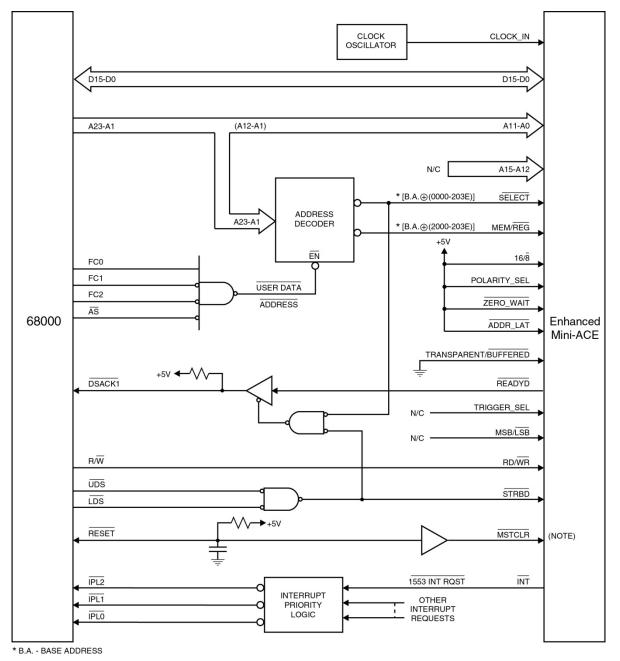


NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 37. Motorola 68020-to-Enhanced Mini-ACE Interface

9.17.6 MOTOROLA 68000

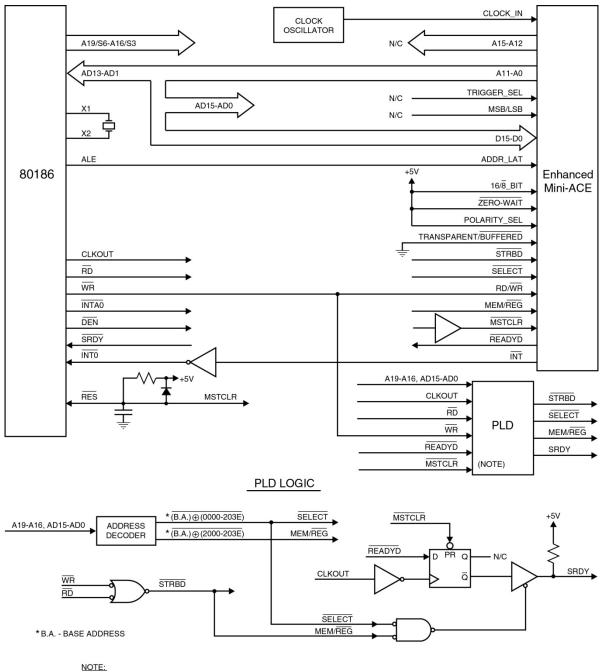


NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 38. Motorola 68000-to-Enhanced Mini-ACE Interface

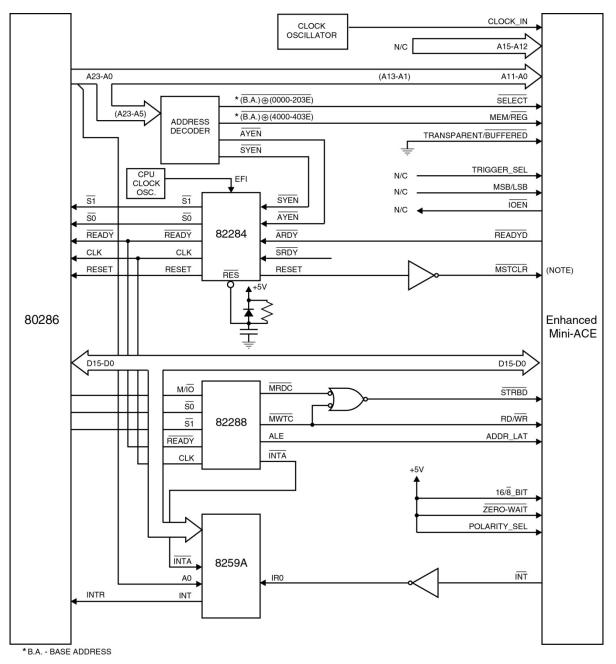
9.17.7 INTEL 80186



The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 39. INTEL 80186-to-Enhanced Mini-ACE Interface

9.17.8 INTEL 80286



NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 40. INTEL 80286-to-Enhanced Mini-ACE Interface

9.17.9 PERFORMANCE (PACE)

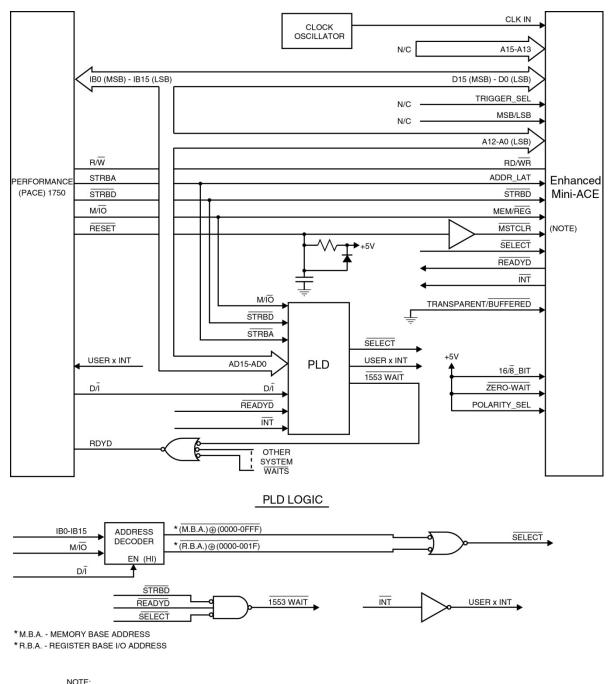
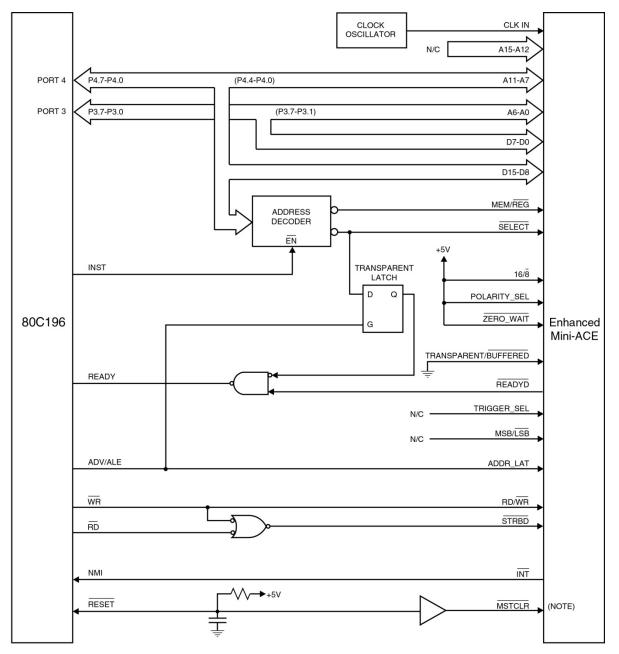


Figure 41. Performance (PACE) 1750-to-Enhanced Mini-ACE Interface

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

9.17.10 INTEL 80C196

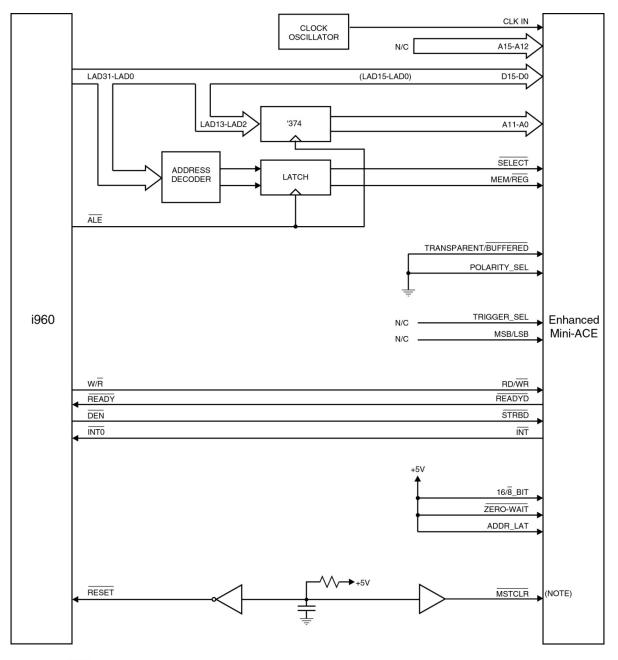


NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 42. INTEL 80C196-to-Enhanced Mini-ACE Interface

9.17.11 INTEL i960



NOTE: The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 43. INTEL i960-to-Enhanced Mini-ACE Interface

9.17.12 INTEL 80486

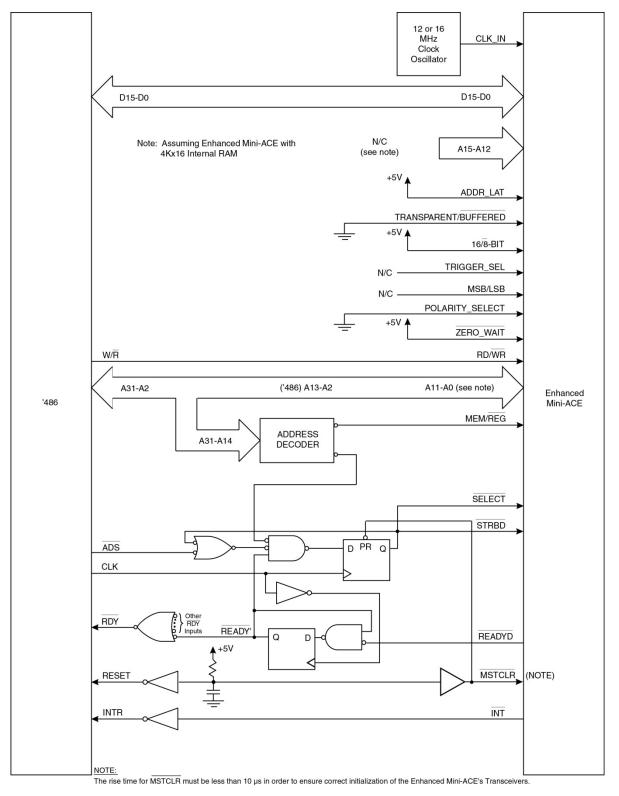
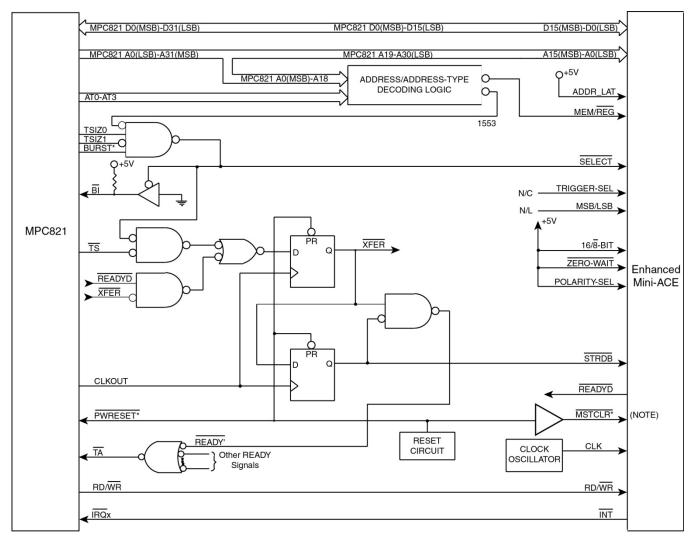


Figure 44. INTEL 80486-to-Enhanced Mini-ACE Interface

9.17.13 MOTOROLA MPC821



NOTE:

The rise time for MSTCLR must be less than 10 µs in order to ensure correct initialization of the Enhanced Mini-ACE's Transceivers.

Figure 45. Motorola MPC821-to-Enhanced Mini-ACE Interface

10.1 General RAM Transfer Timing

This section provides a comprehensive description of the 1553 protocol timing sequences for BC, RT, Message Monitor (MMT), and Word Monitor modes (WMT). This includes RAM transfer timing, and Message Sequence timing. All RAM transfer timing is shown for the transparent mode of operation (transfers are all internal for the buffered mode of operation and hence are not visible). The 1553 message sequence diagrams are shown as a top level summary of timing. These diagrams cross-reference detailed timing diagrams (such as Start Of Message sequence).

10.2 Single Word Read and Write Cycles

These transfer cycles are applicable to BC, RT, and MMT modes for the transfer of Command Words, Status Words, Data words, and Loopback words to the RAM and Data Words from the RAM.

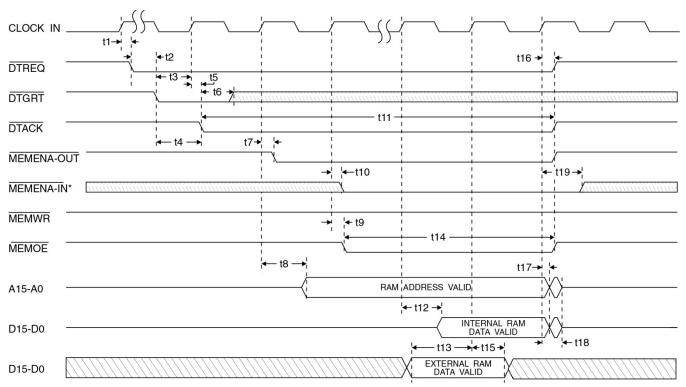
The DMA control signal $\overline{\text{DTREQ}}$ is asserted by the Enhanced Mini-ACE to request access to the host CPU RAM bus. The CPU responds with $\overline{\text{DTGRT}}$ indicating that the interface bus is available for the Enhanced Mini-ACE to read from RAM. The Enhanced Mini-ACE in turn responds with a DMA acknowledge ($\overline{\text{DTACK}}$) and proceeds with the transfer cycle. The $\overline{\text{MEMENA_OUT}}$ along with the Address lines are used to decode between external RAM (if applicable) and internal RAM through the use of the $\overline{\text{MEMENA_IN}}$ input signal. (Note that for Enhanced Mini-ACE series terminals, the $\overline{\text{MEMENA_OUT}}$ signal is not available but can be replaced by logically AND'ing $\overline{\text{DTACK}}$ and $\overline{\text{IOEN}}$).

10.3 SOM/EOM Burst Read/Write Timing

The Start Of Message (SOM) and End Of Message (EOM) timing sequences for BC, RT, and MMT modes consist of a multi-word read/modify/write cycle. Figure 48 illustrates a general multiword burst showing two read transfers followed by 2 write transfers. Note that the actual SOM and EOM transfers may consist of more than 2 read transfers and 2 write transfers. The timing for additional transfers remains the same. Each transfer (both read and write) consists of four clock cycles, with the exception being the first transfer which takes five clock cycles.

Ta	ble 17. Enhanced Mini-ACE Single Word DMA Read (Trans	spare	ent Mo	ode)
REF	DESCRIPTION		nhanco ini-AC		UNITS
		MIN	IIN TYP MA		
t1	CLOCK IN rising delay to DTREQ low			40	ns
	DTREQ falling to DTGRT low (@20 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@20 MHz - 16 Bit Buffered Memory)			4.5	μs
	DTREQ falling to DTGRT low (@16 MHz - 8 Bit Buffered Memory)		N/A		μs
t2	DTREQ falling to DTGRT low (@16 MHz - 16 Bit Buffered Memory)			4	μs
12	DTREQ falling to DTGRT low (@12 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@12 MHz - 16 Bit Buffered Memory)			3.5	μs
	DTREQ falling to DTGRT low (@10 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@10 MHz - 16 Bit Buffered Memory)			3.1	μs
t3	DTGRT low setup prior to CLOCK IN rising	10			ns
	DTGRT falling to DTACK low (@20 MHz)			103	ns
t4	DTGRT falling to DTACK low (@16 MHz)			115	ns
14	DTGRT falling to DTACK low (@12 MHz)			135	ns
	DTGRT falling to DTACK low (@10 MHz)			153	ns
t5	CLOCK IN rising to DTACK low			40	ns
t6	DTGRT hold time following DTACK falling	0			ns
t7	CLOCK IN rising to MEMENA_OUT low			40	ns
t8	CLOCK IN rising to Address outputs valid			40	ns
t9	CLOCK IN rising to MEMOE low			40	ns
	MEMENA_IN setup delay following CLOCK IN rising (@20 MHz)			20	ns
t10	MEMENA_IN setup delay following CLOCK IN rising (@16 MHz)			30	ns
	MEMENA_IN setup delay following CLOCK IN rising (@12 MHz)			50	ns
	MEMENA_IN setup delay following CLOCK IN rising (@10 MHz)			70	ns
	DTACK low pulse width (@20 MHz – 8 Bit Memory Access)		N/A		ns
t11	DTACK low pulse width (@20 MHz – 16 Bit Memory Access)		250		ns
	DTACK low pulse width (@16 MHz – 8 Bit Memory Access)		N/A		ns

Та	ble 17. Enhanced Mini-ACE Single Word DMA Read (Tran	spare	nt M	ode)	
REF	DESCRIPTION	Ei M	UNITS			
		MIN	ТҮР	MAX		
	DTACK low pulse width (@16 MHz – 16 Bit Memory Access)	300	312.5	330	ns	
	DTACK low pulse width (@12 MHz – 8 Bit Memory Access)		N/A		ns	
	DTACK low pulse width (@12 MHz – 16 Bit Memory Access)	400	416.6	430	ns	
	DTACK low pulse width (@10 MHz – 8 Bit Memory Access)		N/A		ns	
	DTACK low pulse width (@120 MHz – 16 Bit Memory Access)		500		ns	
t12	CLOCK IN rising to Output Data valid (Note: Asserted for reads from internal RAM only			60	ns	
t13	Input Data setup time prior to CLOCK IN rising (Note: Valid for reads from external RAM only)	30			ns	
	MEMOE low pulse width (@20 MHz – 8 but Memory)		N/A		ns	
	MEMOE low pulse width (@20 MHz – 16 but Memory)	135	150	165	ns	
	MEMOE low pulse width (@16 MHz – 8 but Memory)		N/A		ns	
t14	MEMOE low pulse width (@16 MHz – 16 but Memory)	170	187.5	200	ns	
114	MEMOE low pulse width (@12 MHz – 8 but Memory)		N/A		ns	
	MEMOE low pulse width (@12 MHz – 16 but Memory)	235	250	265	ns	
	MEMOE low pulse width (@10 MHz – 8 but Memory)		N/A		ns	
	MEMOE low pulse width (@10 MHz – 16 but Memory)	285	300	315	ns	
t15	Input Data hold time following CLOCK IN rising	30			ns	
t16	CLOCK IN rising to DTREQ high, DTACK high, MEMENA_OUT high, MEMOE high			40	ns	
t17	Output Address and Output Data hold time following CLOCK IN rising	0			ns	
t18	CLOCK IN rising to Output Address and Output Data tri-state			45	ns	
t19	MEMENA_IN low hold time following CLOCK IN rising edge	0			ns	



*If only internal RAM is used, connect directly to MEMENA-OUT.

Figure 46. Enhanced Mini-ACE Single Word DMA Read (Transparent Mode)

REF	DESCRIPTION	ESCRIPTION Enhanced Mini-ACE				
		MIN TYP MAX			UNITS	
t1	CLOCK IN rising delay to DTREQ low			40	ns	
	DTREQ falling to DTGRT low (@20 MHz - 8 Bit buffered Memory)		N/A		μs	
	DTREQ falling to DTGRT low (@20 MHz - 16 Bit buffered Memory)			4.5	μs	
	DTREQ falling to DTGRT low (@16 MHz - 8 Bit buffered Memory)		N/A		μs	
t2	DTREQ falling to DTGRT low (@16 MHz - 16 Bit buffered Memory)			4	μs	
τz	DTREQ falling to DTGRT low (@12 MHz - 8 Bit buffered Memory)		N/A		μs	
	DTREQ falling to DTGRT low (@12 MHz - 16 Bit buffered Memory)			3.5	μs	
	DTREQ falling to DTGRT low (@10 MHz - 8 Bit buffered Memory)		N/A		μs	
	DTREQ falling to DTGRT low (@10 MHz - 16 Bit buffered Memory)			3.1	μs	
t3	DTGRT low setup prior to CLOCK IN rising	10			ns	
t4	DTGRT falling to DTACK low (@16 MHz)			115	ns	
t4	DTGRT falling to DTACK low (@12 MHz)			135	ns	
t5	CLOCK IN rising to DTACK low			40	ns	
t6	DTGRT hold time following DTACK falling	0			ns	
t7	CLOCK IN rising to MEMENA_OUT low			40	ns	
t8	CLOCK IN rising to Address outputs valid			40	ns	
t9	CLOCK IN rising to Output Data valid			40	ns	
	DTACK low pulse width (@20 MHz - 8 Bit Memory Access)		N/A		ns	
	DTACK low pulse width (@20 MHz - 16 Bit Memory Access)	235	250	265	ns	
	DTACK low pulse width (@16 MHz - 8 Bit Memory Access)		N/A		ns	
	DTACK low pulse width (@16 MHz - 16 Bit Memory Access)	300	312. 5	330	ns	
t10	DTACK low pulse width (@12 MHz - 8 Bit Memory Access)		N/A	430	ns	
	DTACK low pulse width (@12 MHz - 16 Bit Memory Access)	400	416. 6		ns	
	DTACK low pulse width (@10 MHz - 8 Bit Memory Access)		N/A		ns	
	DTACK low pulse width (@10 MHz - 16 Bit Memory Access)	485	500	515	ns	

Tab	Table 18. Enhanced Mini-ACE Single Word DMA Write (Transparent Mode)						
REF	DESCRIPTION			ced CE	UNITS		
		MIN	TYP	MAX			
t11	MEMENA_IN setup delay following CLOCK IN rising (@16 MHz)			40	ns		
t11	MEMENA_IN setup delay following CLOCK IN rising (@12 MHz)			60	ns		
t12	CLOCK IN rising to MEMWR low			40	ns		
	MEMWR low pulse width (@20 MHz)	35	50	65	ns		
t13	MEMWR low pulse width (@16 MHz)	50	62.5	80	ns		
115	MEMWR low pulse width (@12 MHz)	70	83.3	100	ns		
	MEMWR low pulse width (@10 MHz)	85	100	115	ns		
t14	CLOCK IN rising to MEMWR high			40	ns		
t15	MEMENA_IN hold time following CLOCK IN rising	0			ns		
t16	CLOCK IN rising to DTREQ high, DTACK high, MEMENA_OUT high			40	ns		
t17	Output Address and Output Data hold time following CLOCK IN rising	0			ns		
t18	CLOCK IN rising to Output Address and Output Data tri-state			45	ns		

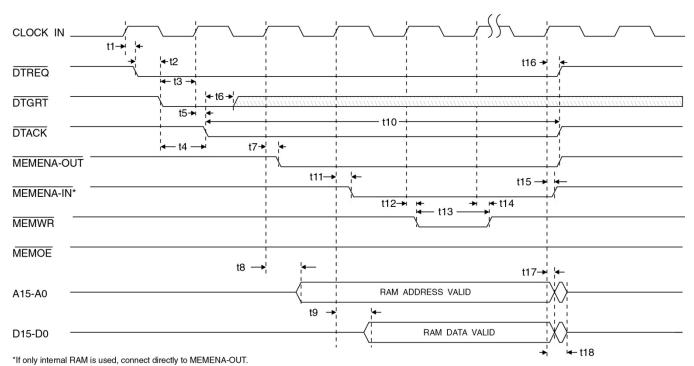


Figure 47. Enhanced Mini-ACE Single Word DMA Write (Transparent Mode)

	Table 19. BC/RT/MT SOM/EOM Burst Read/Write	Timiı	ng		
REF	DESCRIPTION		Enhanced Mini-ACE		
		MIN	TYP	MAX	
t1	CLOCK IN rising delay to DTREQ low			40	ns
	DTREQ falling to DTGRT low (@20 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@20 MHz -16 Bit Buffered Memory)			4.5	μs
	DTREQ falling to DTGRT low (@16 MHz - 8 Bit Buffered Memory)		N/A		μs
t2	DTREQ falling to DTGRT low (@16 MHz -16 Bit Buffered Memory)			4	μs
12	DTREQ falling to DTGRT low (@12 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@12 MHz -16 Bit Buffered Memory)			3.5	μs
	DTREQ falling to DTGRT low (@10 MHz - 8 Bit Buffered Memory)		N/A		μs
	DTREQ falling to DTGRT low (@10 MHz -16 Bit Buffered Memory)			3.1	μs
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			107	ns
t3	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns
13	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			158	ns
t4	DTGRT low hold time following DTACK falling edge.	0			ns
t5	CLOCK IN rising to DTACK low			40	ns
t6	CLOCK IN rising to MEMENA_OUT low			40	ns
t7	CLOCK IN rising to Address outputs valid			40	ns
t8	CLOCK IN rising to MEMOE low			40	ns
t9	MEMENA_IN setup delay following to CLOCK IN rising			30	ns
t10	CLOCK IN rising to Output Data valid (Note: asserted for reads from internal RAM only)			60	ns
t11	Input Data setup time prior to CLOCK IN rising (Note: valid for reads from external RAM only)	30			ns
t12	Input Data hold time following CLOCK IN rising	30			ns
t13	MEMENA_IN valid hold time following CLOCK IN rising edge.	0			ns
t14	CLOCK IN rising edge delay to MEMOE rising edge.			40	ns
t15	Output Address and Output Data valid hold time following CLOCK IN rising edge.	0			ns

Table 19. BC/RT/MT SOM/EOM Burst Read/Write Timing						
REF	EF DESCRIPTION		Enhanced Mini-ACE			
		MIN	ΤΥΡ	MAX		
t16	CLOCK IN rising edge delay to Output Address valid for next address.			50	ns	
t17	CLOCK IN rising edge delay to Output Data tri-state.			45	ns	
t18	CLOCK IN rising edge delay to Output Data valid.			40	ns	
t19	CLOCK IN rising edge delay to MEMWR falling edge.			40	ns	
t20	CLOCK IN rising edge delay to MEMWR rising edge.			40	ns	
t22	CLOCK IN rising edge delay to DTREQ rising edge.			35	ns	
t23	CLOCK IN rising edge delay to DTACK rising edge.			35	ns	
t24	CLOCK IN rising edge delay to MEMENA_OUT rising edge.			40	ns	
t25	CLOCK IN rising edge delay to Output Address tri-state.			45	ns	

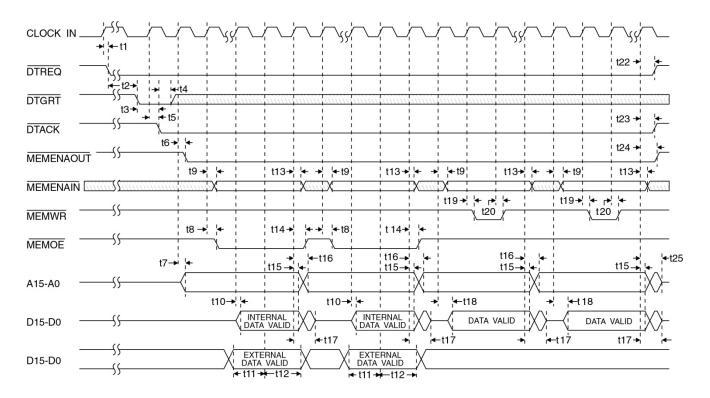


Figure 48. BC/RT/MT SOM/EOM Burst Read/Write Timing

10.4 BC Operation

FIGURES 44 thru 53 illustrate the overall BC message sequence timing for receive, transmit, and broadcast message formats. Each message sequence shows an SOM and EOM sequence as well as single word DMA read cycles and/or DMA write cycles. One of the DMA write cycles shown in the sequence is a command word or data word "looped back." Each word transmitted by the Enhanced Mini-ACE is also decoded by the Enhanced Mini-ACE's receiver section. The transmitter and receiver sections are independent within the Enhanced Mini-ACE and operate independently. Upon completion of the last word transmitted by the Enhanced Mini-ACE (Command word in a transmit message or a data word in a receive message), assuming that there are no errors detected by the receiver, the received copy of the word is written into the Enhanced Mini-ACE's RAM in a location referred to as the loopback word. The loopback word is stored in RAM to provide a simple mechanism for self testing the Enhanced Mini-ACE.

Figure 52 illustrates BC start timing for messages in a frame. The first message in a frame may be started by either an external trigger input, an internal trigger (internal frame timer), or a software start (start bit in start/reset register). Subsequent message in a frame will start based on the minimum intermessage gap time, as illustrated in Figure 52, unless the Message Gap time feature is used to increase this time. Figure 53 and Figure 54 illustrate the BC Start Of Message (SOM) and End Of Message (EOM) sequences. Figure 55 illustrates the timing of automatic retries.

Table 20. BC Mode Receive Message Timing Sequence								
REF	DESCRIPTION		nhanced ini-ACE		UNITS			
		MIN	TYP	MAX				
	Mid-sync crossing of current word delay to $\overline{\text{DTREQ}}$ falling (requesting next data word read access) (@20 MHz)	1.0	1.12	1.2	μs			
t1	Mid-sync crossing of current word delay to $\overline{\text{DTREQ}}$ falling (requesting next data word read access) (@16 MHz)	1.2	1.35	1.45	μs			
LI	Mid-sync crossing of current word delay to $\overline{\text{DTREQ}}$ falling (requesting next data word read access) (@12 MHz)	1.36	1.52	1.6	μs			
	Mid-sync crossing of current word delay to $\overline{\text{DTREQ}}$ falling (requesting next data word read access) (@10 MHz)	1.5	1.65	1.8	μs			
t2	RT Response timeout (note 1).			18.5	μs			
	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting status word write access) (@20 MHz)	1.04	1.32	1.60	μs			
t3	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting status word write access) (@16 MHz)	1.2	1.41	1.77	μs			
ເວ	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting status word write access) (@12 MHz)	1.36	1.6	1.98	μs			
	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting status word write access) (@10 MHz)	1.45	1.75	2.1	μs			
	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting BC end of message access) (@20 MHz)	6.58	6.8	7.16	μs			
	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting BC end of message access) (@16 MHz)	6.70	6.91	7.27	μs			
t4	Mid-parity crossing of status word to $\overline{\text{DTREQ}}$ falling (requesting BC end of message access) (@12 MHz)	6.78	7.02	7.39	μs			
	Mid-parity crossing of status word to DTREQ falling (requesting BC end of message access) (@10 MHz)	6.85	7.1	7.47	μs			
	Mid-parity crossing of last transmitted word to $\overline{\text{DTREQ}}$ falling (requesting loopback word write access) (@20 MHz)	2.92	3.15	3.25	μs			
t5	Mid-parity crossing of last transmitted word to $\overline{\text{DTREQ}}$ falling (requesting loopback word write access) (@16 MHz)	3.06	3.29	3.37	μs			
10	Mid-parity crossing of last transmitted word to $\overline{\text{DTREQ}}$ falling (requesting loopback word write access) (@12 MHz)	3.20	3.43	3.51	μs			
	Mid-parity crossing of last transmitted word to $\overline{\text{DTREQ}}$ falling (requesting loopback word write access) (@10 MHz)	3.50	3.75	3.83	μs			

	MID-SYNC	MID-SYNC	MI	D-PARITY MID-SYNC		
1553 BUS			XX DATA #2		STATUS X	
SOM						
	 	1 1 1			 	/`\
BC_FRAME \	 	1 1 1		 	 	
		⇒t1	t5	→ ←	t3 → t4 —	
						þ. –
DTGRT						
DTACK	SINGLE V DMA RI	VORD SINGLE WOP EAD DMA READ	RD	SINGLE WORD DMA WRITE	SINGLE W DMA WR	
				DATA WORD #2 LOOPED BACK		S BC EOM SEQUENCE
MEMWR	JENCE #1	#2				
MEMOE						
A15-A0						
D15-D0						
INT						
RX_DTA_STR						
TX_DTA_STR						

Figure 49. BC Mode Receive Message Timing Sequence

	Table 21. BC Mode Transmit Message Timing Sequence									
REF	DESCRIPTION		nhano ini-A		UNITS					
		MIN	ТҮР	MAX						
t1	RT Response timeout (note 1).			18.5	μs					
	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting loopback write access) (@20 MHz)	2.92	3.15	3.25	μs					
t2	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting loopback write access) (@16 MHz)	3.06	3.29	3.37	μs					
12	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting loopback write access) (@12 MHz)	3.20	3.43	3.51	μs					
	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting loopback write access) (@10 MHz)	3.50	3.75	3.83	μs					
	Mid-parity crossing delay to $\overline{\rm DTREQ}$ falling (requesting BC end of message access) (@20 MHz)	6.58	6.8	7.16	μs					
t3	Mid-parity crossing delay to $\overline{\rm DTREQ}$ falling (requesting BC end of message access) (@16 MHz)	6.70	6.91	7.27	μs					
1.5	Mid-parity crossing delay to $\overline{\rm DTREQ}$ falling (requesting BC end of message access) (@12 MHz)	6.78	7.02	7.39	μs					
	Mid-parity crossing delay to $\overline{\rm DTREQ}$ falling (requesting BC end of message access) (@10 MHz)	6.85	7.1	7.47	μs					
	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting Status and Data Word write access) (@20 MHz)	1.04	1.32	1.60	μs					
t4	Mid-parity crossing delay to $\overline{\text{DTREQ}}$ falling (requesting Status and Data Word write access) (@16 MHz)	1.20	1.41	1.77	μs					
14	Mid-parity crossing delay to $\overline{\mathrm{DTREQ}}$ falling (requesting Status and Data Word write access) (@12 MHz)	1.36	1.60	1.98	μs					
	Mid-parity crossing delay to $\overline{\mathrm{DTREQ}}$ falling (requesting Status and Data Word write access) (@10 MHz)	1.45	1.75	2.1	μs					

		4	RITY MID-SYNC	MID-PARITY	MID-PA			
1553 BUS	;/	<u>∖</u>		STATUS X	DATA #1		<u>#2_X</u>	
SOM								
INCMD	<u> </u>							/`\
BC_FRAM	Ē \							
		t2 🚽	' ₩—	t4 🚽 🛓	t4 🛶	¦∎ t	4 → t3	
DTREQ			\sim					\
DTGRT								
DTACK			SINGLE WORD DMA WRITE	SINGL DMA	E WORD WRITE	SINGLE WORD	SINGLE WORD DMA WRITE	<u> </u>
MEMENAC		M ICE	COMMAND WORD	STATU	s word	DATA WORD	DATA WORD	BC EOM SEQUENCE
MEMWR								
MEMOE								
A15-A0								
D15-D0								
INT								
RX_DTA_S								
TX_DTA_S	STR							

Figure 50. BC Mode Transmit Message Timing Sequence

NOTES For Table 20 and Table 21 and Figure 49 and Figure 50 Intermessage gap may be extended under software control. The message gap timer is assumed to be disabled. Assumed DTREQ is connected to DTGRT, there is no CPU contention, and all transfers are to memory.

	Table 22. BC Mode Broadcast Message Timing Sequence								
REF	DESCRIPTION	Enhanced Mini-ACE			UNITS				
		MIN	ТҮР	MAX					
	Mid-sync crossing of current word delay to $\overline{^{DTREQ}}$ falling (requesting next data word read access) (@20 MHz)	1.0	1.12	1.2	μs				
t1	Mid-sync crossing of current word delay to $\overline{^{DTREQ}}$ falling (requesting next data word read access) (@16 MHz)	1.20	1.35	1.45	μs				
	Mid-sync crossing of current word delay to $\overline{^{DTREQ}}$ falling (requesting next data word read access) (@12 MHz)	1.36	1.52	1.60	μs				
	Mid-sync crossing of current word delay to $\overline{^{DTREQ}}$ falling (requesting next data word read access) (@10 MHz)	1.5	1.65	1.8	μs				
	Mid-parity crossing of last data word to $\overline{^{DTREQ}}$ falling (loopback word write access request) (@20 MHz)	2.92	3.15	3.25	μs				
t2	Mid-parity crossing of last data word to $\overline{^{DTREQ}}$ falling (loopback word write access request) (@16 MHz)	3.06	3.29	3.37	μs				
12	Mid-parity crossing of last data word to $\overline{^{DTREQ}}$ falling (loopback word write access request) (@12 MHz)	3.20	3.43	3.51	μs				
	Mid-parity crossing of last data word to $\overline{^{DTREQ}}$ falling (loopback word write access request) (@10 MHz)	3.50	3.75	3.83	μs				
	$\overline{\text{DTREQ}}$ rising to $\overline{\text{DTREQ}}$ falling (@20 MHz)	75	100	125	ns				
t3	DTREQ rising to DTREQ falling (@16 MHz)	100	125	150	ns				
	DTREQ rising to DTREQ falling (@12 MHz)	140	166	190	ns				
	\overline{DTREQ} rising to \overline{DTREQ} falling (@10 MHz)	175	200	225	ns				

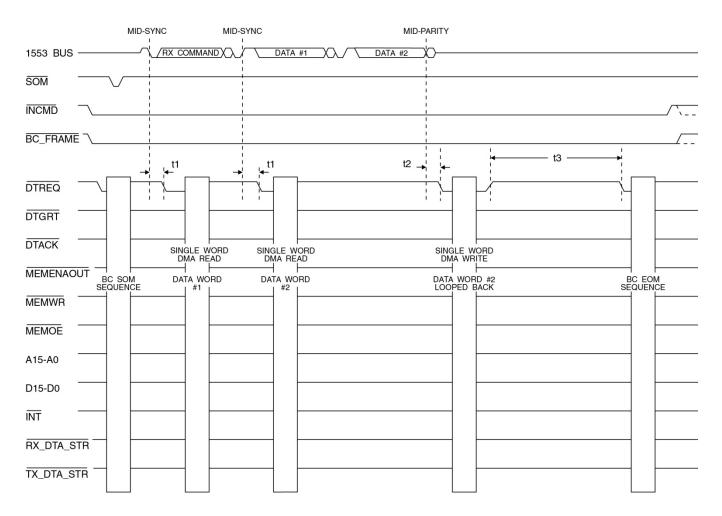


Figure 51. BC Mode Broadcast Message Timing Sequence

	Table 23. BC Mode Start Timing				
REF	DESCRIPTION		HAN(ini-A		UNITS
		MIN	ТҮР	MAX	
	READYD falling (write access to start register bit) delay to DTREQ falling (BC SOM) (@20 MHz)	120	150	180	ns
t1	Error! Objects cannot be created from editing field codes. falling (write access to start register bit) delay to DTREQ falling (BC SOM) (@16 MHz)	160	188	220	ns
	READYD falling (write access to start register bit) delay to DTREQ falling (BC SOM) (@12 MHz)	220	250	280	ns
	$\overrightarrow{\text{READYD}} \text{ falling (write access to start register bit) delay to } \overrightarrow{\text{DTREQ}} \text{ falling (BC SOM)} $ (@10 MHz)	270	300	330	ns
	EXT_TRIG rising delay to DTREQ falling (BC SOM) (@20 MHz)	145	175	225	ns
t2	EXT_TRIG rising delay to DTREQ falling (BC SOM) (@16 MHz)	160	220	280	ns
ιz	EXT_TRIG rising delay to DTREQ falling (BC SOM) (@12 MHz)	220	290	360	ns
	EXT_TRIG rising delay to DTREQ falling (BC SOM) (@10 MHz)	287	350	445	ns
	BC Intermessage GAP (Note 1,2) (@20 MHz - first Broadcast message)	8.4	8.5	8.7	μs
	BC Intermessage GAP (Note 1,2) (@20 MHz - non-Broadcast message)	10.7	10.8	11.0	μs
	BC Intermessage GAP (Note 1,2) (@16 MHz - first Broadcast message)	9.0	9.1	9.2	μs
t3	BC Intermessage GAP (Note 1,2) (@16 MHz - non-Broadcast message)	11.9	12.2	12.7	μs
13	BC Intermessage GAP (Note 1,2) (@12 MHz - first Broadcast message)	10.6	10.7	10.8	μs
	BC Intermessage GAP (Note 1,2) (@12 MHz - non-Broadcast message)	13.2	13.6	14.1	μs
	BC Intermessage GAP (Note 1,2) (@10 MHz - first Broadcast message)	14.6	14.8	15.1	μs
	BC Intermessage GAP (Note 1,2) (@10 MHz - non-Broadcast message)	15.8	16.0	16.3	μs
	INCMD rising delay to INCMD falling (Note 1) (@20 MHz)	35	50	65	ns
t4	INCMD rising delay to INCMD falling (Note 1) (@16 MHz)	40	62.5	85	ns
14	INCMD rising delay to INCMD falling (Note 1) (@12 MHz)	60	83.3	105	ns
	INCMD rising delay to INCMD falling (Note 1) (@10 MHz)	85	100	115	ns
	INCMD falling delay to DTREQ falling (BC SOM) (@20 MHz)	35	50	65	ns
t5	INCMD falling delay to DTREQ falling (BC SOM) (@16 MHz)	40	62.5	85	ns
	INCMD falling delay to DTREQ falling (BC SOM) (@12 MHz)	60	83.3	105	ns

	Table 23. BC Mode Start Timing							
REF	DESCRIPTION		HAN(ini-A		UNITS			
		MIN	ТҮР	MAX				
	INCMD falling delay to DTREQ falling (BC SOM) (@10 MHz)	85	100	115	ns			
t6	DTACK falling delay to DTACK rising (@20 MHz)	1.15	1.20	1.25	μs			
	DTACK falling delay to DTACK rising (@16 MHz)	1.77	1.81	1.85	μs			
	DTACK falling delay to DTACK rising (@12 MHz)	2.37	2.42	2.46	μs			
	DTACK falling delay to DTACK rising (@10 MHz)	2.75	2.85	2.95	μs			
	DTACK rising delay to mid-sync crossing of command word (@20 MHz)	1.70	1.80	2.0	μs			
t7	DTACK rising delay to mid-sync crossing of command word (@16 MHz)	1.82	1.90	2.05	μs			
	DTACK rising delay to mid-sync crossing of command word (@12 MHz)	1.90	1.98	2.14	μs			
	DTACK rising delay to mid-sync crossing of command word (@10 MHz)	1.95	2.05	2.25	μs			

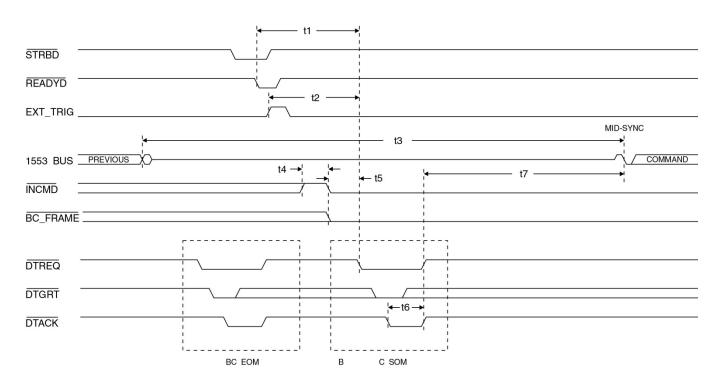




Table 24. BC Start of Message (SOM) Sequence Timing								
REF	DESCRIPTION		Enhanced Mini-ACE					
		MIN	ТҮР	MAX				
t1	DTREQ falling delay DTGRT low.			x	μs			
	DTGRT falling delay to DTACK falling (@20 MHz).			102	ns			
t2	DTGRT falling delay to DTACK falling (@16 MHz).			115	ns			
	DTGRT falling delay to DTACK falling (@12 MHz).			135	ns			
	DTGRT falling delay to DTACK falling (@10 MHz).			152	ns			
t3	DTGRT low hold time following DTACK falling.	0			ns			
	DTACK falling delay to DTREQ rising, DTACK rising, and MEMENAOUT rising (@20 MHz).		1.45		μs			
t4	DTACK falling delay to $\overrightarrow{\text{DTREQ}}$ rising, $\overrightarrow{\text{DTACK}}$ rising, and $\overrightarrow{\text{MEMENAOUT}}$ rising (@16 MHz).		1.82		μs			
	$\overrightarrow{\text{DTACK}}$ falling delay to $\overrightarrow{\text{DTREQ}}$ rising, $\overrightarrow{\text{DTACK}}$ rising, and $\overrightarrow{\text{MEMENAOUT}}$ rising (@12 MHz).		2.42		μs			
	$\overline{\text{DTACK}}$ falling delay to $\overline{\text{DTREQ}}$ rising, $\overline{\text{DTACK}}$ rising, and $\overline{\text{MEMENAOUT}}$ rising (@10 MHz).		2.90		μs			
	SOM active low pulse width (@20 MHz).		50		ns			
t5	SOM active low pulse width (@16 MHz).		62.5		ns			
10	SOM active low pulse width (@12 MHz).		83.3		ns			
	$\overline{\text{SOM}}$ active low pulse width (@10 MHz).		100		ns			
t6	Data Bus (D15-D0) valid setup prior to \overline{SOM} rising.	60			ns			
t7	Data Bus (D15-D0) valid hold time following $\overline{\text{SOM}}$ rising.	60			ns			
	DTACK rising delay to mid-sync crossing of command word (@20 MHz)	1.70	1.80	2.0	μs			
t8	DTACK rising delay to mid-sync crossing of command word (@16 MHz)	1.82	1.9	2.05	μs			
10	DTACK rising delay to mid-sync crossing of command word (@12 MHz)	1.90	1.98	2.14	μs			
	DTACK rising delay to mid-sync crossing of command word (@10 MHz)	1.95	2.05	2.25	μs			

1553 BUS -		COMMAND
SOM		
INCMD	→ i←t5	
BC_FRAME		
DTREQ	\	
DTGRT	t1→ / / ↓ / ↓ t3	
DTACK		/
	··· t4 ···· ··· ··· ··· ··· ··· ··· ··· ···	 /
MEMENAOU		
MEMWR		
MEMOE		
- A15-A0	STACK PTR STACK STACK ADDR + 3 MESS BLK MESS BLK STACK ADDR + 1 ADDR + 1 ADDR + 3	
D15-D0 -	STACK GAP MSG BLC CTRL CMND TIME STS WRD STS WRD	
ĪNT		
RX_DTA_ST	R	
TX_DTA_ST	R	

Figure 53. BC Start of Message (SOM) Sequence Timing

Table 25. BC End of (EOM) Sequence Timing										
DEE	DECODIDITION	Enhan	Enhanced Mini-ACE							
REF	DESCRIPTION	MIN	ТҮР	TYP MAX						
	Mid-parity crossing of last word delay to \overline{DTREQ} falling (@20 MHz)	6.58	6.8	7.16	μs					
t1	Mid-parity crossing of last word delay to $\overline{\text{DTREQ}}$ falling (@16 MHz)	6.70	6.91	7.27	μs					
-	Mid-parity crossing of last word delay to \overline{DTREQ} falling (@12 MHz)	6.78	7.02	7.39	μs					
	Mid-parity crossing of last word delay to \overline{DTREQ} falling (@10 MHz)	6.85	7.1	7.47	μs					
t2	DTREQ falling delay to DTGRT falling				μs					
	DTGRT falling delay to DTACK falling (@20 MHz)			102	ns					
t3	DTGRT falling delay to DTACK falling (@16 MHz)			115	ns					
13	DTGRT falling delay to DTACK falling (@12 MHz)			135	ns					
	DTGRT falling delay to DTACK falling (@10 MHz)			152	ns					
t4	DTGRT low hold time following DTACK falling.	0			ns					
	DTACK falling delay to $\overrightarrow{\text{DTREQ}}$ rising, $\overrightarrow{\text{DTACK}}$ rising, and $\overrightarrow{\text{MEMENAOUT}}$ rising (@20 MHz)		1.05		μs					
t5	DTACK falling delay to $\overrightarrow{\text{DTREQ}}$ rising, $\overrightarrow{\text{DTACK}}$ rising, and $\overrightarrow{\text{MEMENAOUT}}$ rising (@16 MHz)		1.3125		μs					
15	DTACK falling delay to $\overline{\text{DTREQ}}$ rising, $\overline{\text{DTACK}}$ rising, and $\overline{\text{MEMENAOUT}}$ rising (@12 MHz)		1.75		μs					
	DTACK falling delay to DTREQ rising, DTACK rising, and MEMENAOUT rising (@10 MHz)		2.10		μs					
	$\overline{\text{DTACK}}$ falling delay to $\overline{\text{INT}}$ falling (@20 MHz) (Note 1)		1.00		μs					
t6	$\overline{\text{DTACK}}$ falling delay to $\overline{\text{INT}}$ falling (@16 MHz) (Note 1)		1.25		μs					
10	DTACK falling delay to \overline{INT} falling (@12 MHz) (Note 1)		1.66		μs					
	DTACK falling delay to \overline{INT} falling (@10 MHz) (Note 1)		2.00		μs					
t7	INT active low pulse width (Notes 1,2).		500		ns					
	DTACK rising delay to INCMD rising (@20 MHz)		50.0		ns					
	DTACK rising delay to INCMD rising (@16 MHz)		62.5		ns					
t8	DTACK rising delay to INCMD rising (@12 MHz)		83.3		ns					
	DTACK rising delay to INCMD rising (@10 MHz)		100.0		ns					

	Table 25. BC End of (EOM) Sequence Timing								
REF	DESCRIPTION	Enhanced Mini-ACE							
t9	DTACK rising delay to BC_FRAME rising (@20 MHz)		100		ns				
	DTACK rising delay to BC_FRAME rising (@16 MHz)		125		ns				
	DTACK rising delay to BC_FRAME rising (@12 MHz)		166		ns				
	DTACK rising delay to BC_FRAME rising (@10 MHz)		200		ns				

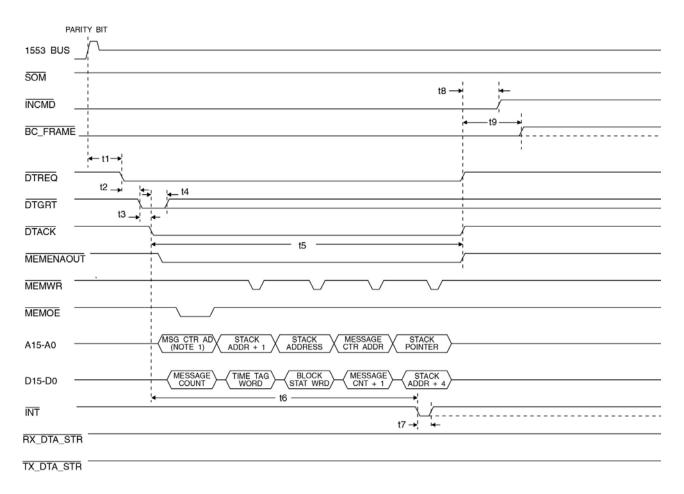


Figure 54. BC End of Message (EOM) Sequence Timing

NOTES For Table 25 and Figure 54

- 1. Assumes that the interrupt is enabled. Applies to all interrupts which occur with the end of a message.
- 2. Interrupt output is software programmable for a pulse or level output. Pulse mode of operation is assumed.

I	Table 26. BC Retry Timing								
REF	DESCRIPTION	Enhanced Mini-ACE			UNITS				
		MIN	ТҮР	MAX					
t1a	Mid-parity crossing delay to DTREQ falling (Retry due to invalid word, incorrect sync, high word count or status address mismatch)	6.7	6.9	7.5	μs				
t1b	Mid-parity crossing delay to DTREQ falling (Retry due to no response or low word count) (programmable)	23		23.7	μs				
t1c	DTREQ rising to DTREQ falling (Retry due to loop test fail on broadcast command)		2		clk				
t2	DTREQ falling delay to DTGRT falling.			8	ns				
	DTGRT falling delay to DTACK falling (@20 MHz)			102	ns				
t3	DTGRT falling delay to DTACK falling (@16 MHz)			115	ns				
	DTGRT falling delay to DTACK falling (@12 MHz)			135	ns				
	DTGRT falling delay to DTACK falling (@10 MHz)			152	ns				
t4	DTGRT low hold time following DTACK falling.	0			ns				
	DTACK falling delay to $\overline{\text{DTREQ}}$ rising, $\overline{\text{DTACK}}$ rising, and $\overline{\text{MEMENAOUT}}$ rising (@20 MHz)		0.650		μs				
t5	DTACK falling delay to $\overline{\text{DTREQ}}$ rising, $\overline{\text{DTACK}}$ rising, and $\overline{\text{MEMENAOUT}}$ rising (@16 MHz)		0.812		μs				
15	$\overrightarrow{\text{DTACK}}$ falling delay to $\overrightarrow{\text{DTREQ}}$ rising, $\overrightarrow{\text{DTACK}}$ rising, and $\overrightarrow{\text{MEMENAOUT}}$ rising (@12 MHz)		1.083		μs				
	DTACK falling delay to DTREQ rising, DTACK rising, and MEMENAOUT rising (@10 MHz)		1.300		μs				
	DTACK rising delay to mid-sync crossing of command word (@20 MHz)	1.70	1.80	2.0	μs				
te	DTACK rising delay to mid-sync crossing of command word (@16 MHz)	1.82	1.9	2.05	μs				
t6	DTACK rising delay to mid-sync crossing of command word (@12 MHz)	1.90	1.98	2.14	μs				
	DTACK rising delay to mid-sync crossing of command word (@10 MHz)	1.95	2.05	2.25	μs				

MID-PARITY	MID-SYNC
1553 BUS LAST WORD	· COMMAND └ COMMAND
SOM	t6 → 1
BC_FRAME	
	l← t1a, t1b l← t1c
DTGRT	
DTACK	
MEMENAOUT LAST WORE RECEIVED_DM	
MEMWR OR	
A15-A0	STACK MESSAGE MSG BLK ADDR + 3 BLK PTR PTR + 1
D15-D0	MESSAGE BC CTRL COMMAND WORD
INT	
RX_DTA_STR	
TX_DTA_STR	

Figure 55. BC Retry Timing

NOTES for Table 26 and Figure 55

- 1. Time based on default no response timeout program (18.5 µs typ.). For Enhanced Mini-ACE products, add 5.3 µs to typical value.
- 2. Last word received applicable to t1A timings and loop back write applicable to t1B and t1C timings.

10.5 RT Operation

Figure 56 thru Figure 60 illustrate the overall RT message sequence timing for receive, transmit, and broadcast message formats. Figure 59 and Figure 60 illustrate the RT Start Of Message Sequence and the End Of Message Sequence. The Start Of Message output signal ($\overline{\text{som}}$) is driven low during the SOM sequence at the time when the received command word is driven onto the data bus (D15-D0). The timing of the $\overline{\text{som}}$ signal matches the timing of the write strobe ($\overline{\text{MEMWR}}$) and such can be used to externally latch the command word. Note also the that 1553 status bits are latched internally on the rising edge of the $\overline{\text{som}}$ pulse ($\overline{\text{SSFLAG}}$ is the only status bit which is driven from an external source).

During the RT SOM sequence several optional transfers are shown as dashed lines. The illegalization table is only accessed if command illegalization is enabled (bit 7 in configuration register #3 set to logic 0). A read of the busy bit table (transfer #3 in the SOM) only occurs if the busy bit lookup feature is enabled (bit 13 in configuration register #2 set to logic 1). The subaddress control word (SOM transfer #4) will only occur if enhanced RT memory management is enabled (bit 1 in configuration register #2 is set to logic 1) and the command is not a mode code or enhanced mode code handling is not enabled (bit 0 of configuration register #3 set to logic 0). The data block pointer is read (SOM transfer #5) for all commands except any mode code if enhanced mode code handling is enabled (bit 0 of configuration register #3 set to logic 1). If such is the case, the mode code interrupt look-up table will be read.

The RT EOM sequence also contains several optional transfers. The subaddress control word is re-read if enhanced RT memory management is enabled (bit 1 in configuration register #2 is set to logic 1) and the command is to receive data to a block address and the double buffering feature is enabled (bit 12 of configuration register #2 is set to logic 1). The data block address is re-read from the lookup table (EOM transfer #2) if subaddress double buffering is enabled and the command is to receive data to a block address. A write of a single data word to the third location on the descriptor stack (EOM transfer #2) will occur if the current message is a mode code with data and enhanced mode code handling is enabled (bit 0 of configuration register #3 set to logic 1). A write to the subaddress data pointer will occur if the data pointer has to be updated either because double-buffering was enabled or the stack address must be updated.

	Table 27. RT Receive Message Timing								
REF	DESCRIPTION	Enhanced Mini-ACE			UNITS				
		MIN							
t1	Mid-parity crossing of received command word to RT Address and RT Address Parity sampled.	500	800	1100	ns				
t2	RT Address and RT Address Parity setup prior to sampling.	500			ns				
t3	RT Address and RT Address Parity hold time following sampling.	500			ns				
	Mid-parity crossing of received command word to $\overline{\text{DTREQ}}$ falling edge (requesting RT Start Of Message transfer) (@20 MHz) (Note 1)	1.10	1.39	1.75	μs				
t4	Mid-parity crossing of received command word to $\overline{\text{DTREQ}}$ falling edge (requesting RT Start Of Message transfer) (@16 MHz) (Note 1)	1.26	1.49	1.83	μs				
14	Mid-parity crossing of received command word to $\overline{\text{DTREQ}}$ falling edge (requesting RT Start Of Message transfer) (@12 MHz) (Note 1)	1.44	1.60	2.06	μs				
	Mid-parity crossing of received command word to $\overline{\text{DTREQ}}$ falling edge (requesting RT Start Of Message transfer) (@10 MHz) (Note 1)	1.49	1.69	2.15	μs				
	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer) (@20 MHz)	1.12	1.35	1.68	μs				
t5	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer) (@16 MHz)	1.20	1.43	1.77	μs				
15	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer) (@12 MHz)	1.36	1.52	1.98	μs				
	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer) (@10 MHz)	1.42	1.60	2.05	μs				
t6	RT response time (6.9 μs max if buffered or $\overline{\text{DTGRT}}$ applied with 2 μsec for Enhanced Mini-ACE)	5.9	6.3	9.4	μs				
t7	Mid-parity crossing of RT status word to DTREQ falling edge (requesting RT End Of Message transfer).	2.8		3.2	μs				

	MID-PARITY	MID-PARITY		MID-SYNC	MID-PARITY	
1553 BUS	← t1 →	DATA #1	DATA #2 X	\ <u>/s</u>	STATUS X	
RTAD4-RTAD0,RTADP		X				
SOM						
INCMD		1				/
	t4 → +	t5 → ' 	t5 → +		t7 → +	
DTREQ	,	, ,	, ,		\	
DTGRT						
DTACK		SINGLE W DMA WR	IORD SINGLE	E WORD WRITE		
MEMENAOUT	RT SC SEQUE	DM DATA WO NCE #1	DRD DATA	WORD #2	RT EON SEQUENC	1 CE
MEMWR						
MEMOE						
A15-A0						
D15-D0						
INT						
RX_DTA_STR						
TX_DTA_STR						

Figure 56. RT Receive Message Timing

NOTES For Table 27 and Figure 56

1. If superseding command, max time can increase by 5 clk cycles.

	Table 28. RT Transit Message Timing							
REF	DESCRIPTION		hanc ini-A		UNITS			
		MIN	TYP	MAX				
t1	RT Response time (6.9 s max if buffered or $\overrightarrow{\text{DTGRT}}$ applied within 2 sec for Enhanced Mini-ACE)	5.9	6.3	9.4	μs			
t2	Mid-parity crossing of received command word to RT Address and RT Address Parity sampled.	500	800	1100	ns			
t3	RT Address and RT Address Parity setup prior to sampling.	500			ns			
t4	RT Address and RT Address Parity hold time following sampling.	500			ns			
t5	Mid-parity crossing of received command word to DTREQ falling edge (requesting RT Start Of Message transfer).	1.25		2.1	μs			
t6	Mid-sync crossing of current transmitting word to DTREQ falling edge (requesting data word read transfer of next word to be transmitted).	1.2		1.6	μs			
t7	Mid-parity crossing of last transmitted word to DTREQ falling edge (requesting RT End Of Message transfer).	2.8		3.2	μs			

DETAILED DESCRIPTION OF 1553 MESSAGE SEQUENCES

1553 BUS	MID-PARITY			
	i ← t2 →¦ → i← t3 → i← t4			
RTAD4-RTAD0,RTADP	XX			
SOM				
				//
	t5 → ' <	t6 → 🖌	t6 → +	t7 → +
DTREQ		`_	,,,,,,,	,,,,,,, _
DTGRT				
DTACK		SINGLE WORD	SINGLE WORD DMA READ	
MEMENAOUT	RT SOM SEQUENCE	DATA WORD	DATA WORD	RT EOM SEQUENCE
MEMWR				
MEMOE				
A15-A0				
D15-D0				
INT				
RX_DTA_STR				
TX_DTA_STR				

Figure 57. RT Transmit Message Timing

NOTES For Table 28 and Figure 57

1. In the event SOM sequence stretches into first DMA read cycle, DTREQ will fall 1 clk cycle after DTREQ rises.

	Table 29. RT Broadcast Receive Message Timing						
REF	DESCRIPTION			Enhanced Mini-ACE			
			TYP	MAX			
t1	Mid-parity crossing of received command word to RT Address and RT Address Parity sampled.	500	800	1100	ns		
t2	RT Address and RT Address Parity setup prior to sampling.				ns		
t3	RT Address and RT Address Parity hold time following sampling.				ns		
t4	Mid-parity crossing of received command word to DTREQ falling edge (requesting RT Start Of Message transfer).			2.1	μs		
t5	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer).	1.2		2.0	μs		
t6	Mid-parity crossing of last received data word to DTREQ falling edge (requesting RT End Of Message transfer).	6.7		7.4	μs		

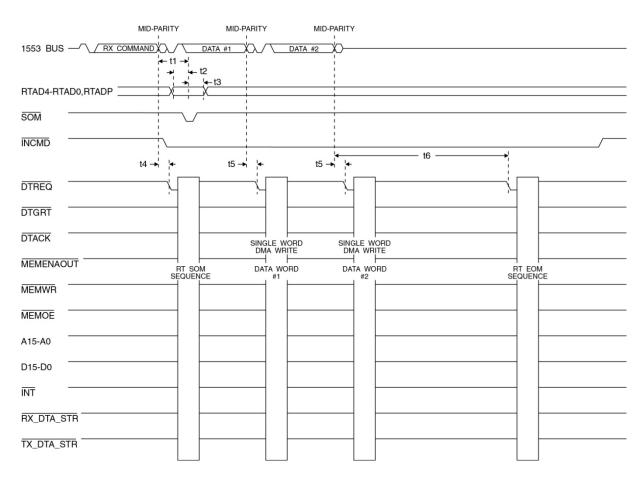


Figure 58. RT Broadcast Receive Message Timing

	Table 30. RT Start of Message Timing							
REF	DESCRIPTION	Enhanced Mini-ACE			UNITS			
		MIN	TYP	MAX				
t1	Mid-parity crossing of received command word delay to INCMD falling edge.	1.2		2.0	μs			
t2	Mid-parity crossing of received command word delay to DTREQ falling edge (requesting RT Start Of Message transfer sequence).	1.25		2.1	μs			
	DTREQ falling edge delay to DTGRT falling edge (@20 MHz) (Note 1)			4.5	μs			
t3	DTREQ falling edge delay to DTGRT falling edge (@16 MHz) (Note 1)			4.0	μs			
10	DTREQ falling edge delay to DTGRT falling edge (@12 MHz) (Note 1)			3.5	μs			
	DTREQ falling edge delay to DTGRT falling edge (@10 MHz) (Note 1)			3.1	μs			
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns			
t4	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns			
14	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns			
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns			
t5	DTGRT low hold time following DTACK falling edge.	0			ns			
	DTACK falling edge delay to $\overline{\text{MEMENAOUT}}$ rising edge, $\overline{\text{DTREQ}}$ rising edge, and $\overline{\text{DTACK}}$ rising edge (@20 MHz)	1.42		2.08	μs			
+6	DTACK falling edge delay to $\overline{\text{MEMENAOUT}}$ rising edge, $\overline{\text{DTREQ}}$ rising edge, and $\overline{\text{DTACK}}$ rising edge (@16 MHz)	1.78		2.59	μs			
t6	DTACK falling edge delay to $\overline{\text{MEMENAOUT}}$ rising edge, $\overline{\text{DTREQ}}$ rising edge, and $\overline{\text{DTACK}}$ rising edge (@12 MHz)	2.38		3.45	μs			
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{MEMENAOUT}}$ rising edge, $\overrightarrow{\text{DTREQ}}$ rising edge, and $\overrightarrow{\text{DTACK}}$ rising edge (@10 MHz)	2.85		4.15	μs			
t7	Status word inputs ($\overline{\text{SSFLAG}}$) valid setup time prior to $\overline{\text{SOM}}$ rising edge.	40			ns			
t8	Status word inputs ($\overline{\text{SSFLAG}}$) valid hold time following $\overline{\text{SOM}}$ rising edge.	10			ns			

P	ARITY BIT
1553 BUS	-J ₁
SOM	
INCMD	→ ' ' - t1
STATUS	
	→
DTREQ	
DTGRT	
DTACK	
MEMENA	
MEMWR	
MEMOE	
A15-A0	/ILLEGALIZEV STACK / BUSY / SA CTRL / LOOKUP STACK STACK STACK / STACK
D15-D0	(ILLEGAL), STACK, BUSY, SA CTRL, DATA BLK, CMND, DATA BLK, TIME TAG, BLOCK, STACK, MORD, WORD, ADDR, STS WRD, ADDR + 4'
INT	
RX_DTA_S	STR
TX_DTA_S	STR

Figure 59. RT Start of Message (SOM) Timing

NOTES for Table 30 and Figure 59

- 1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the RT Start of Message sequence will cause the Enhanced Mini-ACE to not respond to the current command.
- 2. The stack pointer is only written during the sum sequence if command stack pointer increment on EOM, bit 13 of configuration register #6, is logic '0.'

1	Table 31. RT End of Message Timing								
REF	DESCRIPTION	En Mi	UNITS						
		MIN	ТҮР	MAX					
t1	Mid-parity crossing of last transmitted word delay to $\overline{\text{DTREQ}}$ falling edge (requesting RT End Of Message transfer sequence).	2.8		3.2	μs				
t2	$\overline{\text{DTREQ}}$ falling edge delay to $\overline{\text{DTGRT}}$ falling edge (Note 1).				ns				
t3	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns				
	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns				
	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns				
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns				
t4	$\overrightarrow{\text{DTGRT}}$ low hold time following $\overrightarrow{\text{DTACK}}$ falling edge.	0			ns				
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{MEMENAOUT}}$ rising edge, $\overrightarrow{\text{DTREQ}}$ rising edge, and $\overrightarrow{\text{DTACK}}$ rising edge (@20 MHz)	0.43		1.07	μs				
t5	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{MEMENAOUT}}$ rising edge, $\overrightarrow{\text{DTREQ}}$ rising edge, and $\overrightarrow{\text{DTACK}}$ rising edge (@16 MHz)	0.53		1.34	μs				
15	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{MEMENAOUT}}$ rising edge, $\overrightarrow{\text{DTREQ}}$ rising edge, and $\overrightarrow{\text{DTACK}}$ rising edge (@12 MHz)	0.72		1.78	μs				
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{MEMENAOUT}}$ rising edge, $\overrightarrow{\text{DTREQ}}$ rising edge, and $\overrightarrow{\text{DTACK}}$ rising edge (@10 MHz)	0.96		2.03	μs				
t6	INT falling prior to DTACK rising		1		clk				
t7	INT low pulse width (note 2).		500		ns				
t8	MEMENAOUT rising edge, DTREQ rising edge, and DTACK rising edge delay to INCMD rising edge.		2		clk				

Р	ARITY BIT
1553 BUS	
SOM	
INCMD	
	¦← t1→¦
DTREQ	$t^2 \rightarrow t^{\prime} \leftarrow t^4$
DTGRT	
DTACK	
MEMENAC	
MEMWR	
MEMOE	
	VSA CONTROLY ADDR X Y LOOKUP X STACK STACK ADDR + 1 STACK POINTER /
A15-A0	WORD ADDR,^ (SEE NOTE),^ TBL ADDR _/ ADDR + 1 ADDRESS / POINTER _/ Note 3
D15-D0	
INT	
	t7→¦
RX_DTA_S	TR
TX_DTA_S	

Figure 60. RT End of Message (EOM) Timing

NOTES For Table 31 and Figure 60

- 1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the RT End of Message sequence will have no effect on 1553 message transfers.
- 2. Assumes that the interrupt request mode is set to pulse mode (bit 3 of configuration register #2 is set to logic "1").
- 3. The stack pointer is only written during the EOM sequence if command stack pointer increment on EOM, bit 13 of configuration register #6, is logic '1.'

10.6 Message MT Operation

Figure 61 thru Figure 66 illustrate the overall MT message sequence timing for receive, transmit, and broadcast message formats. Figure 63 illustrates the timing sequence for a message in which the command word is not enabled in the Enhanced Mini-ACE's monitor selection lookup table. The Enhanced Mini-ACE will begin a normal Start Of Message, beginning with a read of the monitor lookup table, if the command is not selected in the lookup table, the Enhanced Mini-ACE will abort the SOM sequence. By the time the Enhanced Mini-ACE aborts the sequence, a read of the monitor command stack pointer has begun, so the Enhanced Mini-ACE will finish the read cycle and abort immediately there after.

Figure 65 illustrates the Message Monitor Start Of Message (SOM) sequence. Figure 66 illustrates the Message Monitor End Of Message (EOM) sequence.

	Table 32. Message MT Receive Message Timing							
REF	DESCRIPTION		Enhanced Mini-ACE					
				MAX				
t1	Mid-parity crossing of received command word to DTREQ* falling edge (requesting Message MT Start Of Message transfer).	1.25		2.10	μs			
t2	Mid-parity crossing of received data word to DTREQ* falling edge (requesting data word write transfer).	1.2		2.0	μs			
t3	RT no response timeout (note 1).			18.5	μs			
t4	Mid-parity crossing of received status word to DTREQ* falling edge (requesting status word write transfer).	1.2		2.0	μs			
t5	Mid-parity crossing of RT status word to DTREQ* falling edge (requesting Message MT End Of Message transfer).	6.7		7.4	μs			

DETAILED DESCRIPTION OF 1553 MESSAGE SEQUENCES

	MID-PA	RITY	MID-PARITY	L.	t3	MID-SYNC	MID-PARITY	
1553 BUS							rus X	
SOM		/						
SMM_ACT	VE			 			1 1 1	/
INCMD			\	 			 	
	t1 →¦	₩	_ t2→ + +-,	t2 →	⊬		'← t5 - t4 →¦ '←	
DTREQ	I 	_ <u>`</u>		1			· /_	
DTGRT								
DTACK			SING	LE WORD	SINGLE WORD)	SINGLE WO DMA WRI	
MEMENAO	UT	MESSAG SOM_SEQ		ГА WORD #1 ц				S MESSAGE MT
MEMWR								
MEMOE					\neg			
A15-A0								
D15-D0								
ĪNT					-			
RX_DTA_S					\dashv			
TX_DTA_S	TR							

Figure 61. Message MT Receive Message Timing

NOTES For Table 32 and Figure 61

1. Response timeout is programmable. Assumes default response timeout value is programmed. If a status response is not received with the response time period, a response timeout condition will be flagged and the Enhanced Mini-ACE will begin looking for new command words.

1	Table 33. Message MT Transmit Message Timing							
REF	DESCRIPTION	E	UNITS					
			ΤΥΡ	MAX				
t1	RT no response timeout (Note 1).			18.5	μs			
t2	Mid-parity crossing of transmit command word to $\overline{\text{DTREQ}}$ falling edge (requesting Message MT Start Of Message transfer).	1.25		2.10	μs			
t3	Mid-parity crossing of received status word to DTREQ falling edge (requesting status word write transfer).	1.2		2.0	μs			
t4	Mid-parity crossing of received data word to $\overline{\text{DTREQ}}$ falling edge (requesting data word write transfer).	1.2		2.0	μs			
t5	Mid-parity crossing of last transmitted data word to $\overline{\text{DTREQ}}$ falling edge (requesting Message MT End Of Message transfer).	6.7		7.4	μs			

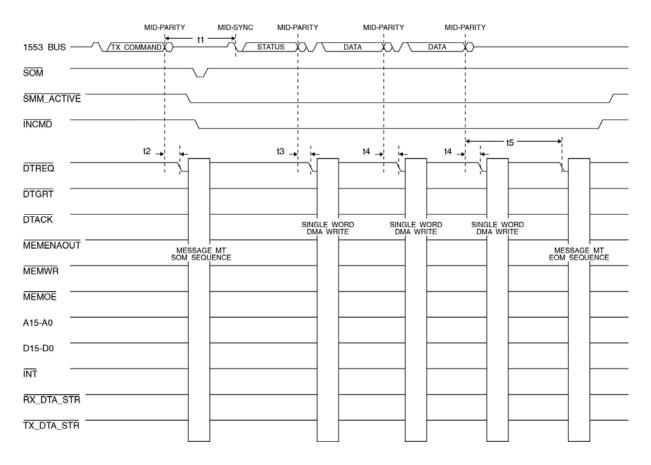


Figure 62. Message MT Transmit Message Timing

	Table 34. Message MT Broadcast Receive Message Timing							
REF	DESCRIPTION	Ei M	UNITS					
		MIN	ΤΥΡ	MAX				
	Mid-parity crossing of received command word to DTREQ falling edge (requesting Message MT Start Of Message transfer).	1.25		2.10	μs			
t2	Mid-parity crossing of received data word to DTREQ falling edge (requesting data word write transfer).	1.2		2.0	μs			
t3	Mid-parity crossing of last data word to DTREQ falling edge (requesting Message MT End Of Message transfer).	6.7		7.4	μs			

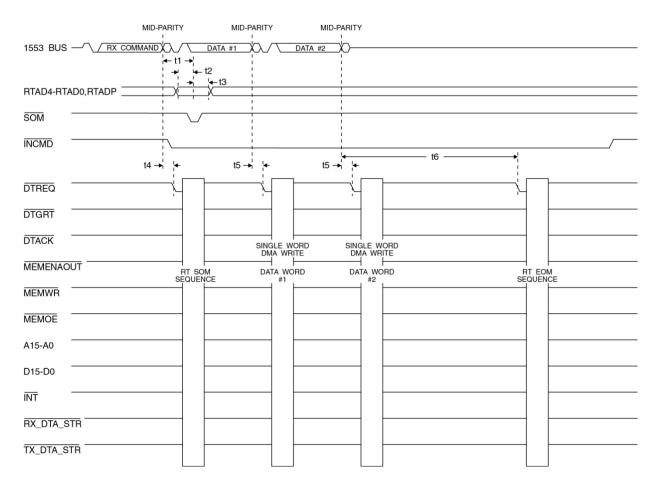


Figure 63. Message MT Broadcast Receive Message Timing

Notes for Table 34 and Figure 63

1. Response timeout is programmable. Assumes default response timeout value is programmed. If a status response is not received with the response time period, a response timeout condition will be flagged and the Enhanced Mini-ACE will begin looking for new command words.

	Table 35. Message MT Command Not Selected Timing									
		Enhan	ced Mi	ni-ACE						
REF	DESCRIPTION	MIN	ТҮР	MAX	UNITS					
t1	Mid-parity crossing of received command word delay to DTREQ falling edge (requesting Message MT Start Of Message transfer sequence).	1.25		2.10	μs					
	DTREQ falling edge delay to DTGRT falling edge (@20 MHz) (Note 1)			4.5	μs					
t2	DTREQ falling edge delay to DTGRT falling edge (@16 MHz) (Note 1)			4.0	μs					
.2	DTREQ falling edge delay to DTGRT falling edge (@12 MHz) (Note 1)			3.5	μs					
	DTREQ falling edge delay to DTGRT falling edge (@10 MHz) (Note 1)			3.1	μs					
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns					
t3	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns					
	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns					
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns					
t4	DTGRT low hold time following DTACK falling edge.	0			ns					
	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@20 MHz)	0.42	0.45	0.48	μs					
t5	DTACK falling edge delay to $DTREQ$ rising edge, $DTACK$ rising edge, and $\overline{MEMENAOUT}$ rising edge (@16 MHz)	0.53	0.56	0.59	μs					
15	$\overline{\text{DTACK}}$ falling edge delay to $\overline{\text{DTREQ}}$ rising edge, $\overline{\text{DTACK}}$ rising edge, and $\overline{\text{MEMENAOUT}}$ rising edge (@12 MHz)	0.72	0.75	0.78	μs					
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{DTREQ}}$ rising edge, $\overrightarrow{\text{DTACK}}$ rising edge, and $\overrightarrow{\text{MEMENAOUT}}$ rising edge (@10 MHz)	0.87	0.90	0.93	μs					
	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@20 MHz)	0.82	1.000	1.450	μs					
t6	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@16 MHz)	1.01	1.140	1.580	μs					
	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@12 MHz)	1.11	1.370	1.720	μs					
	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@10 MHz)	1.27	1.550	1.830	μs					

	Table 35. Message MT Command Not Selected Timing								
REF	DESCRIPTION Enhanced Mini-ACE								
t7	DTACK rising edge delay to SMM_ACTIVE rising edge		2		clk				

	MID-PARITY	
1553 BUS		
SOM		
INCMD		
SMM_ACT	! t7 →! \- ! t7 →! \-	
DTREQ	$t_2 \rightarrow t_4$ $t_2 \rightarrow t_4$	
DTGRT		
DTACK	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	
MEMENAC		
MEMWR		
MEMOE		
A15-A0	MT LOOKUP COMMAND STK MT LOOKUP COMMAND STK ENBL ADDR PNTR ADDR	
D15-D0	MT LOOKUP CMND STK MT LOOKUP CMND STK POINTER	

Figure 64. Message MT Command Not Selected Timing

NOTES For Table 35 and Figure 64

1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the MT Start of Message sequence will cause the Enhanced Mini-ACE to ignore the current command.

	Table 36. Message MT Start of Message Timing				
DEE	DESCRIPTION	Enhanced Mini-ACE			
REF	DESCRIPTION	MIN	ТҮР	MAX	UNITS
t1	Mid-parity crossing of received command word delay to \overline{DTREQ} falling edge (requesting Message MT Start Of Message transfer sequence).	1.25		2.10	μs
	DTREQ falling edge delay to DTGRT falling edge (@20 MHz) (Note 1)			4.5	μs
10	DTREQ falling edge delay to DTGRT falling edge (@16 MHz) (Note 1)			4.0	μs
t2	DTREQ falling edge delay to DTGRT falling edge (@12 MHz) (Note 1)			3.5	μs
	DTREQ falling edge delay to DTGRT falling edge (@10 MHz) (Note 1)			3.1	μs
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns
t3	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns
13	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns
t4	DTGRT low hold time following DTACK falling edge.	0			ns
	DTACK falling edge delay to SOM falling edge (@20 MHz)	720	750	780	ns
t5	DTACK falling edge delay to SOM falling edge (@16 MHz)	910	940	970	ns
15	DTACK falling edge delay to SOM falling edge (@12 MHz)	1220	1250	1280	ns
	$\overline{\text{DTACK}}$ falling edge delay to $\overline{\text{SOM}}$ falling edge (@10 MHz)	1470	1500	1530	ns
	SOM low pulse width (@20 MHz)	35	50	65	ns
	SOM low pulse width (@16 MHz)	45	62.5	80	ns
t6	SOM low pulse width (@12 MHz)	65	83.3	100	ns
	SOM low pulse width (@10 MHz)	80	100	120	ns
	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@20 MHz)	0.82	1.000	1.450	μs
	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@16 MHz)	1.01	1.140	1.580	μs
t7	Mid-parity crossing of receive command word to SMM_ACTIVE falling edge (@12 MHz)	1.11	1.370	1.720	μs
	Mid-parity crossing of receive command word to $\overline{_{SMM_ACTIVE}}$ falling edge (@10 MHz)	1.270	1.550	1.830	μs
	DTACK falling edge delay to INCMD falling edge (@20 MHz)	370	400	430	ns
t8	DTACK falling edge delay to INCMD falling edge (@16 MHz)	470	500	530	ns
	DTACK falling edge delay to INCMD falling edge (@12 MHz)	635	666	695	ns

	Table 36. Message MT Start of Message Timing					
REF	DESCRIPTION	Enhanced Mini-ACE				
REF		MIN	ТҮР	MAX	UNITS	
	DTACK falling edge delay to INCMD falling edge (@10 MHz)	770	800	830	ns	
	DTACK falling edge delay to DTREQ rising edge and DTACK rising edge (@20 MHz)	1.62	1.65	1.68	μs	
t9	DTACK falling edge delay to DTREQ rising edge and DTACK rising edge (@16 MHz)	2.03	2.06	2.09	μs	
10	DTACK falling edge delay to DTREQ rising edge and DTACK rising edge (@12 MHz)	2.72	2.75	2.78	μs	
	$\overline{\text{DTACK}}$ falling edge delay to $\overline{\text{DTREQ}}$ rising edge and $\overline{\text{DTACK}}$ rising edge (@10 MHz)	3.27	3.30	3.33	μs	

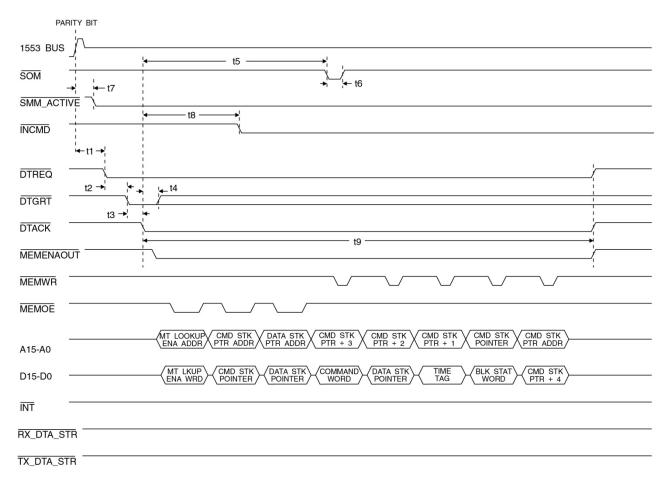


Figure 65. Message MT Start of Message (SOM) Timing

NOTES For Table 36 and Figure 65

1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the MT Start of Message sequence will cause the Enhanced Mini-ACE to ignore the current command.

	Table 37. Message MT End of Message Timing				
REF	DECODIDITION	Enhanced Mini-ACE			UNITS
NEF	DESCRIPTION	MIN	ТҮР	MAX	UNITS
t1	Mid-parity crossing of last word in message delay to DTREQ falling edge (requesting Message MT End Of Message transfer sequence).	6.7		7.4	μs
t2	DTREQ falling edge delay to DTGRT falling edge (Note 1).				ns
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns
t3	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns
15	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns
t4	DTGRT low hold time following DTACK falling edge.	0			ns
	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@20 MHz)	0.62	0.650	0.68	μs
ŧE	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@16 MHz)	0.78	0.812	0.84	μs
t5	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@12 MHz)	1.05	1.083	1.11	μs
	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@10 MHz)	1.27	1.300	1.33	μs
	DTACK falling edge delay to INT falling edge (@20 MHz)	0.57	0.60	0.63	μs
	DTACK falling edge delay to INT falling edge (@16 MHz)	0.72	0.75	0.78	μs
t6	DTACK falling edge delay to INT falling edge (@12 MHz)	0.97	1.00	1.03	μs
	DTACK falling edge delay to INT falling edge (@10 MHz)	1.17	1.20	1.23	μs
t7	INT active low pulse width (note 2).		500		ns
t8	DTACK rising edge delay to SMM_ACTIVE rising edge.		3		clk
t9	DTACK rising edge delay to INCMD rising edge.		2		clk

PARITY BIT		
1553 BUS		
SOM	t8 →	
SMM_ACTIVE		
INCMD	t9 →	
⊷ t1 →		
	/ ← t4	
DTGRT	4	
DTACK	t5	
MEMENAOUT	\\	
MEMWR		
MEMOE		
A15-A0	CMD STK CMD STK CMD STK PTR ADDR PTR + 1 POINTER	
D15-D0	DATA STK POINTER TAG BLK STAT	
INT	t6'	
RX_DTA_STR	t7 →¦ –	
TX_DTA_STR		

Figure 66. Message MT End of Message (EOM) Timing

NOTES For Table 37 and Figure 66

- 1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the MT End of Message sequence will cause the Enhanced Mini-ACE to abort processing the message. This message will appear on the communication stack as a message with the SOM bit set in the block status word.
- 2. Assumes that the interrupt request mode is set to pulse mode (bit 3 of configuration register #2 is set to logic "1").

10.7 Word MT Operation

Figure 67 illustrates the start timing for the Word Monitor mode. The word monitor may be started by either a software command (writing a start command to the start/reset register) or by an external trigger input (EXT_TRIG) if the external trigger is enabled (bit 7 of configuration register #1 set to logic 1). Upon either of the start conditions, the Enhanced Mini-ACE will perform a read operation from the stack pointer memory location (100 or 104). Once read, the stack pointer memory location (100 or 104). Once read, the stack pointer memory location by the Enhanced Mini-ACE monitor and may be overwritten by either the monitor stack without effecting the operation of the Enhanced Mini-ACE.

Figure 68 illustrates a word monitor received word write cycle. Once started, the Enhanced Mini-ACE Word Monitor will store all 1553 words (command, status, and data) into the RAM. Each 1553 word will be stored with a corresponding tag word.

	Table 38. Word MT Start Timing				
REF		Enhanced Mini-ACE			UNITS
REF	DESCRIPTION	MIN	ТҮР	MAX	
	READYD falling edge (end of CPU MT start write cycle) delay to $\overline{\text{DTREQ}}$ falling edge (requesting MT start sequence) (@20 MHz)	120	150	180	ns
t1	READYD falling edge (end of CPU MT start write cycle) delay to $\overline{\text{DTREQ}}$ falling edge (requesting MT start sequence) (@16 MHz)	160	188	220	ns
	READYD falling edge (end of CPU MT start write cycle) delay to $\overline{\text{DTREQ}}$ falling edge (requesting MT start sequence) (@12 MHz)	220	250	280	ns
	READYD falling edge (end of CPU MT start write cycle) delay to $\overline{\text{DTREQ}}$ falling edge (requesting MT start sequence) (@10 MHz)	270	300	330	ns
	EXT_TRIG rising edge delay to DTREQ falling edge (requesting MT start sequence) (@20 MHz) (Note 1)	100	170	240	ns
t2	EXT_TRIG rising edge delay to DTREQ falling edge (requesting MT start sequence) (@16 MHz) (Note 1)	160	210	280	ns
12	EXT_TRIG rising edge delay to DTREQ falling edge (requesting MT start sequence) (@12 MHz) (Note 1)	220	290	360	ns
	EXT_TRIG rising edge delay to DTREQ falling edge (requesting MT start sequence) (@10 MHz) (Note 1)	300	370	440	ns
t3	DTREQ falling edge delay to DTGRT falling edge (Note 2)				ns
t4	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns
14	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns

	Table 38. Word MT Start Timing					
REF	DESCRIPTION	Enhanced Mini-ACE			UNITS	
NEF		MIN	ТҮР	MAX	UNITS	
	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns	
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns	
t5	DTGRT low hold time following DTACK falling edge.	0			ns	
	DTACK falling edge delay to $\overline{\text{DTREQ}}$ rising edge, $\overline{\text{DTACK}}$ rising edge, and $\overline{\text{MEMENAOUT}}$ rising edge (@20 MHz)	220	250	280	ns	
t6	$\overline{\text{DTACK}}$ falling edge delay to $\overline{\text{DTREQ}}$ rising edge, $\overline{\text{DTACK}}$ rising edge, and $\overline{\text{MEMENAOUT}}$ rising edge (@16 MHz)	280	312	340	ns	
10	DTACK falling edge delay to $\overline{\text{DTREQ}}$ rising edge, $\overline{\text{DTACK}}$ rising edge, and $\overline{\text{MEMENAOUT}}$ rising edge (@12 MHz)	390	417	450	ns	
	DTACK falling edge delay to $\overline{\text{DTREQ}}$ rising edge, $\overline{\text{DTACK}}$ rising edge, and $\overline{\text{MEMENAOUT}}$ rising edge (@10 MHz)	470	500	530	ns	

STRBD	
READYD	
EXT_TRIG	
SOM	
INCMD	,
SMM_FR	
SMM_ACTIVE	
	/← t5
DTGRT	
	t6
MEMENAOUT	
MEMWR	
MEMOE	
A15-A0 REG 03	ADDRESS
D15-D0	(NOTE 1)
RX_DTA_STR	
TX_DTA_STR	

Figure 67. Word MT Start Timing

NOTES For Table 38 and Figure 67

- 1. Assumes that the external trigger is enabled in Configuration Register #1.
- 2. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on the MT start sequence will cause the Enhanced Mini-ACE monitor to not start (i.e., the Enhanced Mini-ACE will remain in the Idle mode).

	Table 39. Word MT Received Word Write Cycle Timing					
REF	DECODIDITION	Enhanced Mini-ACE			UNITS	
KEF	DESCRIPTION	MIN	ТҮР	MAX	UNITS	
	Mid-parity crossing of last word in message delay to DTREQ falling edge (requesting received word write cycle) (@ 20 MHz)	1.04	1.32	1.60	μs	
t1	Mid-parity crossing of last word in message delay to DTREQ falling edge (requesting received word write cycle) (@16 MHz)	1.2	1.41	1.73	μs	
	Mid-parity crossing of last word in message delay to DTREQ falling edge (requesting received word write cycle) (@12 MHz)	1.36	1.6	1.94	μs	
	Mid-parity crossing of last word in message delay to DTREQ falling edge (requesting received word write cycle) (@10 MHz)	1.45	1.75	2.1	μs	
	DTREQ falling edge delay to DTGRT falling edge (@20 MHz) (Note 1)			4.5	μs	
t2	DTREQ falling edge delay to DTGRT falling edge (@16 MHz) (Note 1)			4.0	μs	
12	DTREQ falling edge delay to DTGRT falling edge (@12 MHz) (Note 1)			3.5	μs	
	DTREQ falling edge delay to DTGRT falling edge (@10 MHz) (Note 1)			3.1	μs	
	DTGRT falling edge delay to DTACK falling edge (@20 MHz)			102	ns	
t3	DTGRT falling edge delay to DTACK falling edge (@16 MHz)			115	ns	
13	DTGRT falling edge delay to DTACK falling edge (@12 MHz)			135	ns	
	DTGRT falling edge delay to DTACK falling edge (@10 MHz)			152	ns	
t4	DTGRT low hold time following DTACK falling edge.	0			ns	
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{DTREQ}}$ rising edge, $\overrightarrow{\text{DTACK}}$ rising edge, and $\overrightarrow{\text{MEMENAOUT}}$ rising edge (@20 MHz)	0.42	0.450	0.48	μs	
	$\overrightarrow{\text{DTACK}}$ falling edge delay to $\overrightarrow{\text{DTREQ}}$ rising edge, $\overrightarrow{\text{DTACK}}$ rising edge, and $\overrightarrow{\text{MEMENAOUT}}$ rising edge (@16 MHz)	0.53	0.560	0.59	μs	
t5	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@12 MHz)	0.72	0.750	0.78	μs	
	DTACK falling edge delay to DTREQ rising edge, DTACK rising edge, and MEMENAOUT rising edge (@10 MHz)	0.87	0.900	0.93	μs	

DETAILED DESCRIPTION OF 1553 MESSAGE SEQUENCES

	PARITY BIT
1553 BUS	
DTREQ	t2 ↓ → ↓ ↓ ↓ ↓ ↓ ↓ ↓
DTGRT	t3 -> -
DTACK	t5
MEMENAO	
MEMWR	
MEMOE	
A15-A0	STACK STACK POINTER PTR + 1
D15-D0	RECEIVED 1553 WORD
RX_DTA_S	
TX_DTA_ST	TR

Figure 68. Word MT Received Word Write Cycle Timing

NOTES For Table 39 and Figure 68

1. If maximum allowable request to grant time is exceeded, a handshake fail condition will occur. A handshake fail on an MT received word write sequence will cause the Enhanced Mini-ACE monitor to ignore the received word (i.e., the word will be lost).

11 APPENDIX A: ISOLATION TRANSFORMERS

11.1 ISOLATION TRANSFORMERS FOR USE WITH DDC +5.0 VOLT MIL-STD-1553 TERMINALS

11.1.1 INTRODUCTION

Voltage source transmitters, such as those used in DDC's +3.3 volt terminals, are sensitive to transformer parasitic leakage inductance. Transformers with large leakage inductances (in effect, large series inductances) may result in excessively long transmitter rise and fall times which can result in a reduction in output amplitude if the slowdown becomes excessive. The higher the leakage inductance, the greater the problem.

Note: Isolation Transformer selection is not required for the Total-ACE as Isolation Transformers are an integral part of the Total-ACE plastic BGA component.

11.1.2 DESIGN CONSIDERATIONS

Our voltage source design provides superior line driving capability, especially when driving a healthily loaded bus (i.e., high capacitance). This transceiver has been exhaustively tested and characterized for compliance to our published data sheets as well as to MIL-STD-1553, and has successfully passed the RT Validation Test Plan per MIL-HDBK-1553A, Section 100. In addition, for specific products, DDC has verified that it meets the transmitter amplitude requirement for MIL-STD-1760.

As mentioned, reflected leakage inductance is a parameter that must be considered when selecting isolation transformers to be used with any of these products. For transformer-coupled (stub-coupled) terminals or transceivers, the maximum allowable reflected leakage inductance is 6.0μ H and a maximum reflected leakage inductance imbalance must be less than 1.0μ H. For direct-coupled (stub-coupled) terminals or transceivers, the maximum allowable reflected leakage inductance is 12.0μ H and the maximum reflected leakage inductance imbalance must be less than 2.0μ H.

If these limits are exceeded, the transmitter rise and fall times may increase, possibly causing the bus amplitude to fall below the minimum level required by MIL-STD-1553. In addition, an excessive leakage imbalance may result in a dynamic offset (output symmetry) that exceeds 1553 specifications.

11.1.3 TEST METHOD

Reflected leakage inductance should be measured as follows: the side of the transformer that connects to the terminal or transceiver hybrid is defined as the

"primary" winding. If one side of the primary is shorted to the primary center-tap, the primary-to-secondary reflected inductance should be measured across the "secondary" (stub-side) winding. This inductance must be less than 6.0 μ H for stub-coupled and 12.0 μ H for direct coupled. Similarly, if the other side of the primary is shorted to the primary center-tap, the reflected inductance measured across the "secondary" (stub-side) winding must also be less than 6.0 μ H for stub-coupled and 12.0 μ H for direct coupled. The difference between these two measurements is the "differential" leakage inductance. This value must be less than 1.0 μ H for stub-coupled terminals and 2.0 μ H for direct-coupled terminals.

11.1.4 SUITABLE TRANSFORMERS FROM BETA TRANSFORMER TECHNOLOGY CORPORATION:

Beta Transformer Technology Corporation (BTTC) manufactures transformers in a variety of mechanical configurations with the required turns ratios of 1.0:2.5 direct coupled, and 1.0:1.79 transformer coupled. The table below provides a listing of many of these transformers. Except where noted, all transformers in this table meet the leakage inductance requirements described in this section and therefore may be used with DDC +5.0 Volt terminal products.

Table 40. BTTC +5.0 Volt Transformers for use with Enhanced Mini-ACE					
Transformer Configuration	BTTC Part No.				
Single epoxy transformer, through-hole, 0.625 X 0.625, 0.250" max height	B-3067 B-3226				
Single epoxy transformer, through-hole with stand-offs, 0.625" X 0.625", 0.275" max height	B-3225				
Single epoxy transformer, surface mount, 0.625" X 0.625", 0.275" max height	B-3227				
Single epoxy transformer, through-hole, 0.350 X 0.500, 0.250" max height	B-3229 B-3230				
Single epoxy transformer, flat pack, 0.625" X 0.625", 0.275" max height	B-3231				
Single epoxy transformer, through-hole, 0.625" X 0.625", 0.220" max height.	B-3818 (see NOTE 1)				
Single epoxy transformer, surface mount, 0.625" X 0.625", 0.220" max height	B-3819 (see NOTE 1)				
Single epoxy transformer, flat pack, 0.625" X 0.625", 0.220" max height	B-3820 (see NOTE 1)				
Single epoxy transformer, flat pack, 0.625" X 0.625", 0.150" max height	LPB-5014				
Single epoxy transformer, surface mount, 0.625" X 0.625", 0.150" max height	LPB-5015				
Dual epoxy transformer, twin stacked, through hole, 0.625" X 0.625", 0.320" max height	TST-9107				
Dual epoxy transformer, twin stacked, surface mount, 0.625" X 0.625", 0.320" max height	TST-9117				

For further information, contact BTTC at 631-244-7393 or at <u>www.bttc-beta.com</u>.

Table 40. BTTC +5.0 Volt Transformers for use with Enhanced Mini-ACE				
Transformer Configuration	BTTC Part No.			
Dual epoxy transformer, twin stacked, flat pack, 0.625" X 0.625", 0.320" max height	TST-9127			
Dual epoxy transformer, twin stacked, through hole, 0.625" X 0.625", 0.280" max height	TST-9007			
Dual epoxy transformer, twin stacked, surface mount, 0.625" X 0.625", 0.280" max height	TST-9017			
Dual epoxy transformer, twin stacked, flat pack, 0.625" X 0.625", 0.280" max height	TST-9027			
Dual epoxy transformer, side-by-side, through-hole, 0.930" X 0.630", 0.155" max height.	TLP-1205/B-3300			
Dual epoxy transformer, side-by-side, flat pack, 0.930" X 0.630", 0.155" max height.	TLP-1105/B-3261			
Dual epoxy transformer, side-by-side, surface mount, 0.930" X 0.630", 0.155" max height.	TLP-1005/B-3310			
Single epoxy transformer, flat pack, 0.750" X 0.750", 0.130" max height	SLP-8124 (see NOTE 2)			
Single epoxy transformer, surface mount, 0.750" X 0.750", 0.130" max height	SLP-8107 (see NOTE 2)			
Dual epoxy transformer, side-by-side, flat pack, 1.410" X 0.750", 0.130" max height.	DLP-7114 (see NOTE 2)			
Dual epoxy transformer, side-by-side, surface mount, 1.410" X 0.750", 0.130" max height.	DLP-7115 (see NOTE 2)			
Single nickel-plated kovar transformer, flat pack, 0.630" X 0.630", 0.175" max height	HLP-6014			
Single nickel-plated kovar transformer, surface mount, 0.630" X 0.630", 0.175" max Height	HLP-6015			
Single epoxy transformer, surface mount, 0.400" X 0.400", 0.185" max height	MLP-2005 (see NOTE 2)			
Single epoxy transformer, surface mount, 0.400" X 0.400", 0.185" max height	MLP-2205 (see NOTE 2)			
Single epoxy transformer, surface mount, 0.400" X 0.400", 0.260" max height	MMT-3005			
Single epoxy transformer, surface mount, 0.400" X 0.400", 0.260" max height	MMT-3205			
NOT RECOMMENDED	DLP-7014 DLP-7015 SLP-8007 SLP-8024			

NOTES

1. Only the B-3818, B-3819 and B-3820 can be used with McAir-compatible transceivers (i.e., products with a last digit suffix of "4" rather than "3"). All others, except for the 4 non-recommended transformers (DLP-7014, DLP-7015, SLP-8007, and SLP-8024) can be used with +5.0 Volt MIL-STD-1553 transceivers (i.e., products with a last digit suffix of "3").

2. Operates to +105° C max. All other transformers operate to +125° C max.

11.2 ISOLATION TRANSFORMERS FOR USE WITH DDC +3.3 VOLT MIL-STD-1553 TERMINALS

11.2.1 INTRODUCTION

Voltage source transmitters, such as those used in DDC's +3.3 volt terminals, are sensitive to transformer parasitic leakage inductance. Transformers with large leakage inductances (in effect, large series inductances) may result in excessively long transmitter rise and fall times which can result in a reduction in output amplitude if the slowdown becomes excessive. The higher the leakage inductance, the greater the problem.

Note: Isolation Transformer selection is not required for the Total-ACE as Isolation Transformers are an integral part of the Total-ACE plastic BGA component.

11.2.2 DESIGN CONSIDERATIONS

Our voltage source design provides superior line driving capability, especially when driving a healthily loaded bus (i.e., high capacitance). This transceiver has been exhaustively tested and characterized for compliance to our published data sheets as well as to MIL-STD-1553, and has successfully passed the RT Validation Test Plan per MIL-HDBK-1553A, Section 100. In addition, for specific products, DDC has verified that it meets the transmitter amplitude requirement for MIL-STD-1760.

As mentioned, reflected leakage inductance is a parameter that must be considered when selecting isolation transformers to be used with any of these products. For transformer-coupled (stub-coupled) terminals or transceivers, the maximum allowable reflected leakage inductance is 5.0μ H and the maximum reflection leakage inductance imbalance must be less than 1.0μ H. For direct-coupled (stub-coupled) terminals or transceivers, the maximum allowable reflected leakage inductance is 10.0μ H and the maximum reflected leakage inductance is 2.0μ H.

If these limits are exceeded, the transmitter rise and fall times may increase, possibly causing the bus amplitude to fall below the minimum level required by MIL-STD-1553. In addition, an excessive leakage imbalance may result in a dynamic offset (output symmetry) that exceeds 1553 specifications.

11.2.3 TEST METHOD

Reflected leakage inductance should be measured as follows: the side of the transformer that connects to the terminal or transceiver hybrid is defined as the "primary" winding. If one side of the primary is shorted to the primary center-tap, the primary-to-secondary reflected inductance should be measured across the "secondary" (stub-side) winding. This inductance must be less than 5.0 µH for stub-

coupled and 10.0 μ H for direct coupled. Similarly, if the other side of the primary is shorted to the primary center-tap, the reflected inductance measured across the "secondary" (stub-side) winding must also be less than 5.0 μ H for stub-coupled and 10.0 μ H for direct coupled. The difference between these two measurements is the "differential" leakage inductance. This value must be less than 1.0 μ H for stub-coupled terminals and 2.0 μ H for direct-coupled terminals.

11.2.4 SUITABLE TRANSFORMERS FROM BETA TRANSFORMER TECHNOLOGY CORPORATION:

Beta Transformer Technology Corporation (BTTC) manufactures transformers in a variety of mechanical configurations with the required turns ratios of 1.0:3.75 direct coupled, and 1.0:2.7 transformer coupled for the X8/9 transceiver options and 1.0:2.65 direct coupled, and 1.0:2.038 transformer coupled for the XC/D transceiver options. The table below provides a listing of many of these transformers. Except where noted, all transformers in this table meet the leakage inductance requirements described in this section and therefore may be used with DDC +3.3 Volt terminal products.

Table 41. BTTC +3.3 Volt Transformers for use with Enhanced Mini-ACE X8/9 Transceiver Options			
Transceiver Option	Transformer Configuration	(BTTC Legacy Part No.)	BTTC Part No.
X8/9	Single epoxy transformer, through-hole, transformer coupled, 0.625 X 0.630, 0.300" max height, +130° C max	(B-3372)	LVB-4203
X8/9	Single epoxy transformer, through-hole, direct coupled, 0.625" X 0.630", 0.300" max height, +130° C max	(B-3383)	LVB-4103
X8/9	Single epoxy transformer, surface mount, 0.625" X 0.625", 0.130" max height, +85° C max	(B-3389)	LVB-4213
X8/9	Single epoxy transformer, surface mount, direct coupled, 0.625 X 0.625, 0.130" max height, +85° C max	(B-3390)	LVB-4113
X8/9	Single epoxy transformer, surface mount, transformer coupled, 0.625" X 0.630", 0.300" max height, +130° C max	(B-3391)	LVB-4223
X8/9	Single epoxy transformer, surface mount, direct coupled 0.625" X 0.630", 0.300" max height, +130° C max	(B-3392)	LVB-4123
X8/9	Dual epoxy transformer, surface mount, transformer coupled, 0.960" X 0.575", 0.185" max height, +130° C max	-	DLVB-4233
X8/9	Dual epoxy transformer, surface mount, direct coupled, 0.960" X 0.575", 0.185" max height, +130° C max	-	DLVB-4133
X8/9	Dual epoxy transformer, surface mount, transformer coupled , 0.960" X 0.575", 0.155" max height, +85° C max	-	DLVB-4213
X8/9	Dual epoxy transformer, surface mount, direct coupled, 0.960" X 0.575", 0.155" max height, +85° C max	-	DLVB-4113

For further information, contact BTTC at 631-244-7393 or at <u>www.bttc-beta.com</u>.

Table 41. BTTC +3.3 Volt Transformers for use with Enhanced Mini-ACE X8/9Transceiver Options			
Transceiver Option	Transformer Configuration	(BTTC Legacy Part No.)	BTTC Part No.
XC/D	Single epoxy transformer, surface mount, direct coupled, 0.4" X 0.52", 0.185" max height.	-	MLP-2030
XC/D	Single epoxy transformer, surface mount, transformer coupled, 0.4" X 0.52", 0.185" max height.	-	MLP-2230
XC/D	Dual epoxy transformer, surface mount, direct and transformer coupled, 0.52" X 0.675", 0.185" max height.	-	DSS-3330
XC/D	Dual epoxy transformer, surface mount, transformer coupled, 0.4" X 0.53", 0.32" max height.	-	TSM-2230

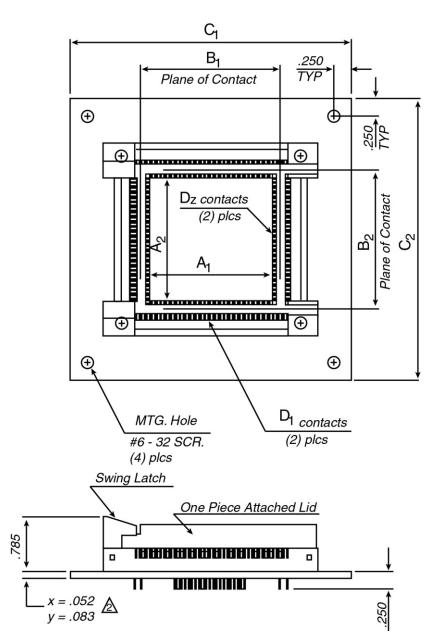
NOTES

1.

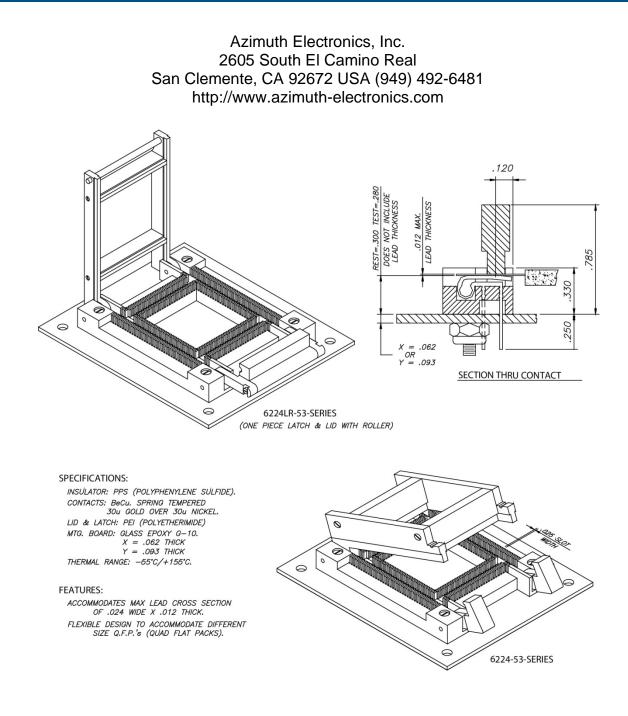
SMT (Surface Mount) body package size (a" x b") does not include leads. The list of approved transformers for use with +3.3V transceivers is constantly being updated. Please contact 2. Beta Transformer Technology Corporation for the latest transformer configuration information.

12 APPENDIX B: BREADBOARDING SOCKETS

Bread Boarding Sockets Azimuth Electronics, Inc. 2605 South El Camino Real San Clemente, CA 92672 USA (949) 492-6481 http://www.azimuth-electronics.com



Azimuth 72-Lead CQFP Socket Test, Flat Pack, 6224-53-21X



APPENDIX C: DESC DRAWING PART NUMBERS 13

Table 42. Enhanced Mini-ACE BU-61743/61745 RT, and BU-61843/61845/61864/61865 BC/RT/MT DESC Drawing Part Numbers				
Logic/RAM	SMD P/N	SMD Suffix		
Voltage		72-Lead [Flat Pack]	72-Lead [Gull Wing]	
+5V	5962-0151401HMC		BU-61865G3-110	
+5V	5962-0151401HMC		BU-61865G3-130	
+5V	5962-0151401HMA		BU-61865G3-140	
+5V	5962-0151401HMA		BU-61865G3-150	
+5V	5962-0151401HTC	BU-61865F3-110		
+5V	5962-0151401HTC	BU-61865F3-130		
+5V	5962-0151401HTA	BU-61865F3-140		
+5V	5962-0151401HTA	BU-61865F3-150		
+5V	5962-0151402HMC		BU-61865G4-110	
+5V	5962-0151402HMC		BU-61865G4-130	
+5V	5962-0151402HMA		BU-61865G4-140	
+5V	5962-0151402HMA		BU-61865G4-150	
+5V	5962-0151402HTC	BU-61865F4-110		
+5V	5962-0151402HTC	BU-61865F4-130		
+5V	5962-0151402HTA	BU-61865F4-140		
+5V	5962-0151402HTA	BU-61865F4-150		
+3.3V, +5V	5962-0151403HMC		BU-61864G3-110	
+3.3V, +5V	5962-0151403HMC		BU-61864G3-130	
+3.3V, +5V	5962-0151403HMA		BU-61864G3-140	
+3.3V, +5V	5962-0151403HMA		BU-61864G3-150	
+3.3V, +5V	5962-0151403HTC	BU-61864F3-110		
+3.3V, +5V	5962-0151403HTC	BU-61864F3-130		
+3.3V, +5V	5962-0151403HTA	BU-61864F3-140		
+3.3V, +5V	5962-0151403HTA	BU-61864F3-150		
+3.3V, +5V	5962-0151404HMC		BU-61864G4-110	
+3.3V, +5V	5962-0151404HMC		BU-61864G4-130	
+3.3V, +5V	5962-0151404HMA		BU-61864G4-140	
+3.3V, +5V	5962-0151404HMA		BU-61864G4-150	
+5V	5962-0151404HTC	BU-61745F4-110		
+5V	5962-0151404HTC	BU-61745F4-130		
+5V	5962-0151404HTA	BU-61864F4-140		

Table 42.Enhanced Mini-ACE BU-61743/61745 RT, andBU-61843/61845/61864/61865 BC/RT/MT DESC Drawing Part Numbers

Logic/RAM	SMD P/N	SMD Suffix	
Voltage		72-Lead [Flat Pack]	72-Lead [Gull Wing]
+5V	5962-0151404HTA	BU-61864F4-150	
+5V	5962-0151405HMC		BU-61745G3-110
+5V	5962-0151405HMC		BU-61745G3-130
+5V	5962-0151405HMA		BU-61745G3-140
+5V	5962-0151405HMA		BU-61745G3-150
+5V	5962-0151405HTC	BU-61745F3-110	
+5V	5962-0151405HTC	BU-61745F3-130	
+5V	5962-0151405HTA	BU-61745F3-140	
+5V	5962-0151405HTA	BU-61745F3-150	
+5V	5962-0151406HMC		BU-61745G4-110
+5V	5962-0151406HMC		BU-61745G4-130
+5V	5962-0151406HMA		BU-61745G4-140
+5V	5962-0151406HMA		BU-61745G4-150
+5V	5962-0151406HTC	BU-61745F4-110	
+5V	5962-0151406HTC	BU-61745F4-130	
+5V	5962-0151406HTA	BU-61745F4-140	
+5V	5962-0151406HTA	BU-61745F4-150	
+3.3V	5962-0151407HMC		BU-61743G3-110
+3.3V	5962-0151407HMC		BU-61743G3-130
+3.3V	5962-0151407HMA		BU-61743G3-140
+3.3V	5962-0151407HMA		BU-61743G3-150
+3.3V	5962-0151407HTC	BU-61743F3-110	
+3.3V	5962-0151407HTC	BU-61743F3-130	
+3.3V	5962-0151407HTA	BU-61743F3-140	
+3.3V	5962-0151407HTA	BU-61743F3-150	
+3.3V	5962-0151408HMC		BU-61743G4-110
+3.3V	5962-0151408HMC		BU-61743G4-130
+3.3V	5962-0151408HMA		BU-61743G4-140
+3.3V	5962-0151408HMA		BU-61743G4-150
+3.3V	5962-0151408HTC	BU-61743F4-110	
+3.3V	5962-0151408HTC	BU-61743F4-130	
+3.3V	5962-0151408HTA	BU-61743F4-140	
+3.3V	5962-0151408HTA	BU-61743F4-150	

Table 42.Enhanced Mini-ACE BU-61743/61745 RT, andBU-61843/61845/61864/61865 BC/RT/MT DESC Drawing Part Numbers

Logic/RAM		SMD Suffix	
Voltage	SMD P/N	72-Lead [Flat Pack]	72-Lead [Gull Wing]
+5V	5962-0151409HMC		BU-61705G3-110
+5V	5962-0151409HMC		BU-61705G3-130
+5V	5962-0151409HMA		BU-61705G3-140
+5V	5962-0151409HMA		BU-61705G3-150
+5V	5962-0151409HTC	BU-61705F3-110	
+5V	5962-0151409HTC	BU-61705F3-130	
+5V	5962-0151409HTA	BU-61705F3-140	
+5V	5962-0151409HTA	BU-61705F3-150	
+5V	5962-0151410HMC		BU-61705G4-110
+5V	5962-0151410HMC		BU-61705G4-130
+5V	5962-0151410HMA		BU-61705G4-140
+5V	5962-0151410HMA		BU-61705G4-150
+5V	5962-0151410HTC	BU-61705F4-110	
+5V	5962-0151410HTC	BU-61705F4-130	
+5V	5962-0151410HTA	BU-61705F4-140	
+5V	5962-0151410HTA	BU-61705F4-150	
+3.3V	5962-0151411HMC		BU-61703G3-110
+3.3V	5962-0151411HMC		BU-61703G3-130
+3.3V	5962-0151411HMA		BU-61703G3-140
+3.3V	5962-0151411HMA		BU-61703G3-150
+3.3V	5962-0151411HTC	BU-61703F3-110	
+3.3V	5962-0151411HTC	BU-61703F3-130	
+3.3V	5962-0151411HTA	BU-61703F3-140	
+3.3V	5962-0151411HTA	BU-61703F3-150	
+3.3V	5962-0151412HMC		BU-61703G4-110
+3.3V	5962-0151412HMC		BU-61703G4-130
+3.3V	5962-0151412HMA		BU-61703G4-140
+3.3V	5962-0151412HMA		BU-61703G4-150
+3.3V	5962-0151412HTC	BU-61703F4-110	
+3.3V	5962-0151412HTC	BU-61703F4-130	
+3.3V	5962-0151412HTA	BU-61703F4-140	
+3.3V	5962-0151412HTA	BU-61703F4-150	
+5V	5962-0151413HTC	BU-61845F3-110	

Table 42. Enhanced Mini-ACE BU-61743/61745 RT, andBU-61843/61845/61864/61865 BC/RT/MT DESC Drawing Part Numbers

Logic/RAM	SMD P/N	SMD Suffix	
Voltage		72-Lead [Flat Pack]	72-Lead [Gull Wing]
+5V	5962-0151413HTC	BU-61845F3-130	
+5V	5962-0151413HTA	BU-61845F3-140	
+5V	5962-0151413HTA	BU-61845F3-150	
+5V	5962-0151413HMC		BU-61845G3-110
+5V	5962-0151413HMC		BU-61845G3-130
+5V	5962-0151413HMA		BU-61845G3-140
+5V	5962-0151413HMA		BU-61845G3-150
+5V	5962-0151414HTC	BU-61845F4-110	
+5V	5962-0151414HTC	BU-61845F4-130	
+5V	5962-0151414HTA	BU-61845F4-140	
+5V	5962-0151414HTA	BU-61845F4-150	
+5V	5962-0151414HMC		BU-61845G4-110
+5V	5962-0151414HMC		BU-61845G4-130
+5V	5962-0151414HMA		BU-61845G4-140
+5V	5962-0151414HMA		BU-61845G4-150
+3.3V	5962-0151415HTC	BU-61843F3-110	
+3.3V	5962-0151415HTC	BU-61843F3-130	
+3.3V	5962-0151415HTA	BU-61843F3-140	
+3.3V	5962-0151415HTA	BU-61843F3-150	
+3.3V	5962-0151415HMC		BU-61843G3-110
+3.3V	5962-0151415HMC		BU-61843G3-130
+3.3V	5962-0151415HMA		BU-61843G3-140
+3.3V	5962-0151415HMA		BU-61843G3-150
+3.3V	5962-0151416HTC	BU-61843F4-110	
+3.3V	5962-0151416HTC	BU-61843F4-130	
+3.3V	5962-0151416HTA	BU-61843F4-140	
+3.3V	5962-0151416HTA	BU-61843F4-150	
+3.3V	5962-0151416HMC		BU-61843G4-110
+3.3V	5962-0151416HMC		BU-61843G4-130
+3.3V	5962-0151416HMA		BU-61843G4-140
+3.3V	5962-0151416HMA		BU-61843G4-150

14 APPENDIX D : ISSUE INVOLVING USE OF EXECUTE AND FLIP "XGF " BC INSTRUCTION

This information pertains only to devices operating in enhanced BC mode. It does not affect devices operating as an RT, combined RT/Monitor, Monitor, or the nonenhanced BC mode, and does not affect units operating in the transparent interface configuration (this interface configuration is **Not Applicable** to PCI Enhanced Mini-ACE). The problem will only occur in a very limited set of applications even on devices operating in Enhanced BC Mode. Errors caused by this issue are very rare and can only occur if all of a series of configurations and conditions are in effect.

The error that can occur is:

• The possibility of momentarily reading erroneous data from Enhanced Mini-ACE registers under a very limited set of circumstances. The data is only momentarily corrupted.

This error is applicable to the following products:

- BU-61743/5, BU-61843/5 and BU-61864/5 Enhanced Mini-ACE terminals
- BU-61740, BU-61840 and BU-61860 Micro-ACE
- BU-64743, BU-64843 and BU-64863 Mini-ACE Mark3
- BU-6474x, BU-6484X, BU-6486X Micro-ACE-TE
- BU-64843T Total-ACE
- BU-62743, BU-62843 and BU-62864 PCI Enhanced Mini-ACE
- BU-65743, BU-65843 and BU-65863 PCI Mini-ACE Mark3
- BU-6584X, BU-6586X PCI Micro-ACE-TE

This error can only occur if **ALL** of the following configurations and conditions are in effect:

• The 1553 terminal is in BC mode, with enhanced BC mode enabled; i.e., bit 15 of Configuration Register #7 = '1'.

AND

• The Enhanced Mini-ACE is in its buffered processor interface configuration (this interface configuration is **Not Applicable** to PCI Enhanced Mini-ACE).

AND

ENHANCED CPU ACCESS is enabled; (i.e., bit 14 of Config Register #7 = '1'). Note that on Enhanced Mini-ACE & Micro-ACE the default condition is disabled and for PCI Enhanced Mini-ACE the default is enabled.

AND

• The host CPU is performing a register read operation during a particular four-clock cycle time window near the end of the BC EOM (end-of-message) sequence. Register write operations, as well as memory read and write operations, are **not** affected.

AND

 The Enhanced BC Controller performs an XQF (Execute and Flip) operation, and a "flip" of the instruction's parameter word, which is the pointer to the message's control/status block, occurs as a result of the executed message.

If and only if **ALL** these conditions/events occur simultaneously, then it is possible to momentarily read erroneous data from the Enhanced Mini-ACE registers.

The issue described in the following paragraph comes into play only if the host performs a register read access during a particular four-clock cycle time window near the end of the BC EOM (end-of-message) sequence. The specific time window is four clock cycles wide, and occurs just prior to the BC's internal write transfer to update the value of the XQF instruction's parameter field in the BC instruction list. This write operation, which occurs only for an XQF instruction in which a "flip" occurs, is the last word transfer of the BC EOM sequence.

Under the circumstances described above, a corrupted register read operation can occur. For an affected register read operation, the data read by the host processor will be equal to the *correct value of the register being read* **OR'd** with the value of the updated control/status block pointer.

Note that this erroneous register read access is only a temporary condition. That is, the actual value of the register is **not** affected, and that in general, for subsequent register read accesses, correct values will be read. Also, note that the operation of the XQF instruction, including processing of the specified 1553 message and the updating of the value of the instruction parameter, is **not** affected. In addition, no memory locations are corrupted as the result of this problem.

Also note that if the host reads a register (e.g., Interrupt Status Register #1 or #2) *immediately* following the occurrence of an interrupt request resulting from the end of a BC message, that the problem will **not** occur. If INTERRUPT STATUS AUTO-

CLEAR is enabled (bit 4 of Configuration Register #2 = '1'), the value of the Interrupt Status Register #1 or #2 **will** clear (internally) to '0000' following a corrupted read access of the interrupt status registers.

There are several possible workarounds to this problem:

- Disable the ENHANCED CPU ACCESS feature; i.e., program bit 14 of Configuration Register #7 to logic '0'. As a compromise to minimize overall access time, disable this feature only during register read accesses. Note that for the Enhanced Mini-ACE, the power-up default condition for ENHANCED CPU ACCESS is disabled.
- 2. Eliminate use of the BC XQF (Execute and Flip) instruction. This may be done by emulating its use through other instructions, and possibly host intervention.
- 3. The host can avoid the complications of having to read the interrupt status registers by making use of the enhanced BC's user-defined interrupts (bits 5-2 of Interrupt Mask Register #2 and Interrupt Status Register #2) and general purpose queue features, and disabling the issuance of interrupts for other conditions defined by the two interrupt mask and status registers.

Just prior to issuing a user-defined interrupt, the BC should post one or more words to the general purpose queue, using the PTT, PBS, PSI, and/or PSM instructions. Then, the host can issue a user-defined interrupt by means of an IRQ instruction. When an interrupt occurs, it is suggested that the host first clear the interrupt by writing logic '1' to INTERRUPT RESET, bit 2 of the Start/Reset Register, and then proceed to read all previously unread words from the general purpose queue.

4. This last method is only applicable for applications in which Interrupt Status Register #1 and Interrupt Status Register #2 are **not** read. For the case of registers other than the two interrupt status registers, reliable values may be obtained by reading the registers multiple times, until the same value is returned for two consecutive accesses.

However, for the two interrupt status registers, this method cannot be made to work with 100% reliability. Because of the problem described above, it's not possible to eliminate the possibility of erroneous error indications, missed interrupts, and/or "ghost" interrupts.

15 APPENDIX E :

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16 APPENDIX F : SPECIAL NOTES (FOR DEVICES OPERATING ONLY IN RT AND RT/MONITOR MODE)

This information pertains only to devices that are operating in RT and RT/Monitor mode. Devices operating in either BC or MT (only) modes are not affected. Even on devices operating in RT mode, the errors caused by this issue are very rare and probabilistic in nature, and can only occur if all of a series of configurations and conditions are in effect.

The errors that can occur are:

For some of the products, it is possible for the value of the first data word transmitted by the RT to be equal to the RT status word, rather than the word read from memory. The second and subsequent data words transmitted by the RT will all have the correct values, as read from RAM.

The RT's Service Request status word bit may fail to automatically clear following receipt of a Transmit vector word mode command.

The RT's time tag register may fail to automatically clear following receipt of a Synchronize mode command (without data).

Although these issues are related, the consequences and DDC's recommended workarounds vary according to the product. Consequently Appendix "F" contains two parts describing the issue and the recommended workarounds for each of the specific products affected. As such it is only necessary that you read the section applicable to products you're using.

The remainder of this appendix is divided into two parts.

- Appendix "F" Part 1: Enhanced Mini-ACE
 - Covers the BU-61743/5, BU-61843/5 and BU-61864/5 Enhanced Mini-ACE; BU-61740, BU-61840 and BU-61860 Micro-ACE, all Mini-ACE Mark3, Micro-ACE TE, and Total-ACE products.
- Appendix "F" Part 2: PCI Enhanced Mini-ACE
 - Covers the BU-62743, BU-62843 and BU-62864 PCI Enhanced Mini-ACE, and all PCI Mini-ACE Mark3, PCI Micro-ACE TE products.

APPENDIX "F" Part 1:

This section applies only to the following products:

- BU-61743/5, BU-61843/5 and BU-61864/5 Enhances Mini-ACE terminals
- BU-61740, BU-61840 and BU-61860 Micro-ACE
- BU-64743/64745, and BU-64843/64845/64863 Mini-ACE Mark3
- BU-64743B/64840B/64860B/64863B Micro-ACE-TE
- BU-64843T Total-ACE

The issues described in this appendix affect only devices that are operating in RT and RT/Monitor modes. Devices operating in either BC or Monitor (only) modes are not affected. Moreover, the errors caused by this issue are very rare and probabilistic in nature.

The first issue affects the first data word transmitted by the RT. An error can only occur if all of the following configurations and conditions are in effect: The 1553 terminal is operating in RT mode.

AND

One or more of specific non-message interrupts are enabled by their respective Interrupt Mask Register bits. The Enhanced Mini-ACE's non-message interrupts that are applicable are TIME TAG ROLLOVER, RT ADDRESS PARITY ERROR, and RAM PARITY ERROR. These interrupts are enabled by bits 6, 7, and 14 respectively of Interrupt Mask Register #1.

AND

The interrupt status queue is enabled (i.e., bit 6 of Configuration Register #6 is set to a logic "1").

AND

The RT receives a non-mode code transmit command, or mode code transmit command involving a memory read operation for the transmitted data word. Receive commands to the RT are not affected.

AND

The internal write transfer to the interrupt status queue resulting from a non-message interrupt begins on a particular single clock cycle relative to the first data word read cycle; i.e., the read transfer from shared RAM and ensuing write to the internal manchester encoder register.

If and only if all of these conditions/events occur simultaneously, then it is possible for the value of the first data word transmitted by the RT to be equal to the RT status word, rather than the word read from memory. The second and subsequent data words transmitted by the RT will all have the correct values, as read from memory.

Note that given the conditions above, occurrences of this error condition will be probabilistic in nature, with a mean time between occurrences that's a function of clock input frequency, time tag counter resolution, and the rate of transmit messages processed. The mean time between errors is given by the following equation:

 $T_{ERR} = \frac{65,536 \bullet f_{CLK} \bullet R}{N}$, where:

 T_{ERR} = average time between errors, in seconds

 f_{CLK} = input clock frequency, in Megahertz

R = time tag resolution, in μ S/LSB

N = number of *transmit* messages per second processed by the RT

For example, for an input clock frequency of 16 MHz, and a programmed time tag resolution of 64 μ S/LSB, this error will occur once in every 2²⁶ = 67,108,864 transmit messages. For an RT responding to 100 transmit messages per second, this equates to (on average) one error every 671,089 seconds, or one error every 186 hours (7.8 days).

In addition to TIME TAG ROLLOVER, the other non-message interrupts are RT ADDRESS PARITY ERROR, PROTOCOL SELF-TEST COMPLETE, and RAM PARITY ERROR. A PROTOCOL SELF-TEST COMPLETE interrupt will not result in the error described, since the Enhanced Mini-ACE will not be responding as an RT on the 1553 bus at the time that a protocol self-test completes. The occurrence of an RT ADDRESS PARITY ERROR could theoretically result in the error. However, the occurrence of this interrupt tends to be extremely rare and in any event would point to a significantly more disruptive issue for the RT than a single corrupted data word. The occurrence of a RAM PARITY ERROR at this time would point to a likely error in the data word being read from memory and transmitted on the 1553 bus, regardless of the occurrence or non-occurrence of the issue described above. As stated, errors will not occur if either the interrupt status queue feature is disabled or non-message interrupts (principally, the TIME TAG ROLLOVER interrupt) are disabled. However, if the interrupt status queue is being used and there's a need to use the TIME TAG ROLLOVER function, we recommend using the ENHANCED INTERRUPTS feature (i.e., set bit 15 of Configuration Register #2 to logic "1"). Then, to completely eliminate the described errors and still make use of the interrupt status queue feature for interrupt events other than TIME TAG ROLLOVER, we recommend that the TIME TAG ROLLOVER interrupt be disabled (set bit 6 of Interrupt Mask Register #1, to logic "0").

In this configuration, the user can then poll the value of TIME TAG ROLLOVER bit 6 of Interrupt Status Register #1 to monitor time tag rollovers. This must be done sufficiently often such that the polling periodicity is less than the period between time tag rollover events to ensure that no time tag rollovers are missed.

There are two other issues that can affect the RT's internal operation following receipt of two specific mode code messages: Synchronize (without data) and Transmit vector word. This error will only occur if all of the following configurations and conditions are in effect:

• The 1553 terminal is operating in RT mode.

AND

 One or more of specific non-message interrupts are enabled by the respective Interrupt Mask Register bit. The Enhanced Mini-ACE's nonmessage interrupts that are applicable are TIME TAG ROLLOVER, RT ADDRESS PARITY ERROR, or RAM PARITY ERROR. These interrupts are enabled by bits 6, 7, and 14 respectively of Interrupt Mask Register #1.

AND

• The interrupt status queue is enabled (i.e., bit 6 of Configuration Register #6 is logic "1").

AND

• For the case of a Transmit vector word mode command, CLEAR SERVICE REQUEST, bit 2 of Configuration Register #2, is programmed to logic "1". For the case of a Synchronize (without data) mode command, CLEAR TIME TAG ON SYNCHRONIZE, bit 6 of Configuration Register #2, is logic"1".

AND

 The RT receives a Transmit vector word mode command (with CLEAR SERVICE REQUEST = logic "1") or Synchronize (without data) mode command (with CLEAR TIME TAG ON SYNCHRONIZE = logic "1". All other mode code commands are not affected.

AND

• The internal write transfer to the interrupt status queue resulting from a non-message interrupt begins within a particular five clock cycle window just prior to the start of the Enhanced Mini-ACE's RT EOM (end of message) sequence.

If and only if all of these conditions/events occur simultaneously, then it is possible for either of the following errors to occur:

- For the case of a Transmit vector word mode command, the RT's Service request status word bit will not clear (with CLEAR SERVICE REQUEST = "1", it normally will clear).
- For the case of a Synchronize (without data) mode command, the RT's internal time tag counter will not clear to 0000h (with CLEAR TIME TAG ON SYNCHRONIZE = "1", it normally will clear to 0000h).

Note that given the conditions above, occurrences of these error conditions will be probabilistic in nature, with a mean time between occurrences that's a function of clock input frequency, time tag counter resolution, and the frequency at which the respective mode code messages are received. The mean time between such errors is given by the following equation:

 $T_{ERR} = \frac{13107.2 \bullet f_{CLK} \bullet R}{N}$, where:

 T_{ERR} = average time between errors, in seconds

 f_{CLK} = input clock frequency, in Megahertz

- R = time tag resolution, in μ S/LSB
- N = the number of Transmit vector word or Synchronize (without data) mode code messages per second received by the RT

For example, for an input clock frequency of 16 MHz, and a programmed time tag resolution of 64 μ S/LSB, this error will occur once in every 2²⁶ = 67,108,864 Transmit vector word or Synchronize (without data) mode code messages. For an RT

responding to 1 Transmit vector word or Synchronize (without data) mode code messages per second, this equates to (on average) one error every 13,421,770 seconds, or one error every 3730 hours (155 days). Note that in either case, the error is highly likely to be corrected following the RT's next reception of a Transmit vector word or Synchronize (without data) mode command.

As stated, errors will not occur if either the interrupt status queue feature is disabled or non-message interrupts (principally, the TIME TAG ROLLOVER interrupt) are disabled. Thus, the recommended workaround for this issue is the same as previously described for the issue where the first data word is equal to the status word.

APPENDIX "F" Part 2:

This section applies only to the following products:

- BU-62743, BU-62843 and BU-62864 PCI Enhanced Mini-ACE
- BU-65743, BU-65843 and BU-65863 PCI-Mini-ACE Mark3
- BU-65843B, BU-65864B, BU-65863B and BU-65864B PCI Micro-ACE-TE

The issues described below affect only RT and RT/Monitor modes. BC and Monitor (only) modes are not affected. Occurrences of the errors relating to this issue are very rare and are probabilistic in nature.

There are two issues that can affect the RT's internal operation following receipt of two specific mode code messages: Synchronize (without data) and Transmit vector word. This error can only occur if all of the following configurations and conditions are in effect:

The 1553 terminal is operating in RT mode.

AND

One or more of certain specific non-message interrupts are enabled by the respective Interrupt Mask Register bit. The Enhanced Mini-ACE's non-message interrupts that are applicable are TIME TAG ROLLOVER, RT ADDRESS PARITY ERROR, or RAM PARITY ERROR. These interrupts are enabled by bits 6, 7, and 14 respectively of Interrupt Mask Register #1.

AND

The interrupt status queue is enabled (i.e., bit 6 of Configuration Register #6 is logic "1").

AND

For the case of a Transmit vector word mode command, CLEAR SERVICE REQUEST, bit 2 of Configuration Register #2, is programmed to logic "1". For the case of a Synchronize (without data) mode command, CLEAR TIME TAG ON SYNCHRONIZE, bit 6 of Configuration Register #2, is logic "1".

AND

The RT receives a Transmit vector word mode command (with CLEAR SERVICE REQUEST = logic "1") or Synchronize (without data) mode command (with CLEAR TIME TAG ON SYNCHRONIZE = logic "1". All other mode code commands are not affected.

AND

The internal write transfer to the interrupt status queue resulting from a non-message interrupt begins within a particular five clock cycle window just prior to the start of the Enhanced Mini-ACE's RT EOM (end of message) sequence.

If and only if **all** of these conditions/events occur simultaneously, then it is possible for either of the following errors to occur:

For the case of a Transmit vector word mode command, the RT's Service request status word bit will *not* clear (with CLEAR SERVICE REQUEST = "1", it normally will clear).

For the case of a Synchronize (without data) mode command, the RT's internal time tag counter will *not* clear to 0000h (with CLEAR TIME TAG ON SYNCHRONIZE = "1", it normally will clear to 0000h).

Note that given the conditions above, occurrences of these error conditions will be probabilistic in nature, with a mean time between occurrences that's a function of clock input frequency, time tag counter resolution, and the frequency at which the respective mode code messages are received. The mean time between such errors is given by the following equation:

 $T_{ERR} = \frac{13107.2 \bullet f_{CLK} \bullet}{R}$, where:

 T_{ERR} = average time between errors, in seconds

 f_{CLK} = input clock frequency, in Megahertz

- R = time tag resolution, in μ S/LSB
- N = the number of Transmit vector word or Synchronize (without data) mode code messages per second received by the RT

For example, for an input clock frequency of 16 MHz, and a programmed time tag resolution of 64 μ S/LSB, this error will occur once in every 2²⁶ = 67,108,864 Transmit vector word or Synchronize (without data) mode code messages. For an RT

responding to 1 Transmit vector word or Synchronize (without data) mode code messages per second, this equates to (on average) one error every 13,421,770 seconds, or one error every 3730 hours (155 days). Note that in either case, the error is *highly likely* to be corrected following the RT's next reception of a Transmit vector word or Synchronize (without data) mode command.

As stated, this problem will **not** occur if **either** the interrupt status queues feature or non-message interrupts (principally, the TIME TAG ROLLOVER interrupt) are not used. However, if the interrupt status queue is used and there's a need to use the TIME TAG ROLLOVER function, we recommend using the ENHANCED INTERRUPTS feature (i.e., set bit 15 of Configuration Register #2 to logic "1"). Then, to completely eliminate the probability of encountering the described problems and still make use of the interrupt status queue feature for interrupt events other than TIME TAG ROLLOVER, we recommend that the TIME TAG ROLLOVER interrupt be disabled (set bit 6 of Interrupt Mask Register #1, to logic "0").

In this configuration, time tag rollovers may be monitored by polling the value of TIME TAG ROLLOVER bit 6 of Interrupt Status Register #1, sufficiently often such that the polling periodicity is less than the period between time tag rollover events.

In addition to TIME TAG ROLLOVER, the other non-message interrupts are RT ADDRESS PARITY ERROR, and RAM PARITY ERROR. The occurrence of an RT ADDRESS PARITY ERROR could theoretically result in the problems. However, the occurrence of this interrupt tends to be extremely rare and in any event would point to a significantly more disruptive problem for the RT than the failure of the Service request bit or time tag counter to clear. The occurrence of a RAM PARITY ERROR at this time would point to an error in a word being read from memory by the PCI Enhanced Mini-ACE's host processor. However, occurrences of RAM parity errors are extremely rare.

As stated, errors will **not** occur if *either* the interrupt status queue feature is disabled or non-message interrupts (principally, the TIME TAG ROLLOVER interrupt) are disabled. However, if the interrupt status queue is being used and there's a need to use the TIME TAG ROLLOVER function, we recommend using the ENHANCED INTERRUPTS feature (i.e., set bit 15 of Configuration Register #2 to logic "1"). Then, to completely eliminate the described errors and still make use of the interrupt status queue feature for interrupt events other than TIME TAG ROLLOVER, we recommend that the TIME TAG ROLLOVER interrupt be disabled (set bit 6 of Interrupt Mask Register #1, to logic "0").

In this configuration, the user can then poll the value of TIME TAG ROLLOVER bit 6 of Interrupt Status Register #1 to monitor time tag rollovers. This must be done sufficiently often such that the polling periodicity is less than the period between time tag rollover events to ensure that no time tag rollovers are missed.

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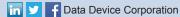
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